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A MULTIPLE DELAY SWITCH-LEVEL SIMULATOR FOR MOS/LSI CIRCUITS

by

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A thesis submitted to
the School of Graduate Studies and Research
in partial fulfillment of the requirements
for the degree of
Master of Applied Science
in the
Department of Electrical Engineering
University of Ottawa

Ottawa, Ontario, 1985



Kia Lian Chuah, Ottawa, Canada, 1985.



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ABSTRACT

In this thesis a new multiple delay switch-level simulator for MOS LSI circuits is presented with the following features : table-driven, time queue with macro event list for simulation with multiple rise and fall delays, selective tracing of active paths, and event scheduling and rescheduling on time queue including spike detection. The delay model used is organized around subnetworks, instead of logic gates. The use of subnetworks permits both logic gates and pass transistors to be handled in a uniform fashion. The delay model takes into account the effects of not only the output loading capacitances but also the input waveforms. An improved algorithm is described and implemented for computing the states and delays of a subnetwork.

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Chapter I

INTRODUCTION

The rapid progress of LSI technologies enables a designer to produce denser and more complex integrated circuits, especially in the MOS area. Design verification in each design step of logic systems has particularly become an important technology in the LSI design process. Hardware prototyping and software simulation are effective means for design verification. The latter has been extensively used because of the following reasons:-

1. A logic simulator can be used to check if the present design can perform the intended function before committing it to hardware.
2. A timing simulator can be used to predict the timing relations among signals closely by taking the actual device parameters and loading conditions into account.
3. A circuit simulator can be used to evaluate the electrical characteristics with variations in device parameters and operating conditions.

A variety of software simulators for MOS LSI circuits is currently available : they include circuit simulators [15] [20], timing simulators [10] [11] [19], logic simulators [8] [9] [18] [21] and combinations of these [1] [12], each providing a certain degree of accuracy.

The primary concern of circuit simulators is accuracy : the ability to simulate exactly the real-world behavior of devices. A circuit is modeled by a collection of differential equations, and the equations are solved to predict the circuit's behavior. This approach produces highly accurate results, and has resulted in widespread use of circuit simulators as a design tool. Unfortunately, the accuracy of the circuit models comes at a high price in execution time : circuit simulators typically require several seconds of CPU time per transistor. As a result, it is impractical for today's state-of-the-art VLSI circuits, which contain tens or hundreds of thousands of transistors.

In timing simulator, circuits are described at the transistor level. The concept of gate here deviates from that used in logic simulation to represent specific structures of transistors. These structures are either a configuration of driver and load devices or pass transistors, and are in general functionally more complex than logic gates. Timing simulator evaluates its gates by finding the current in each device and then integrating the net charging current flowing into the gate output capacitance. The gate voltages obtained in this way are propagated to other gates by techniques similar to those used in logic simulators. By using tables to store device I-V characteristics, and through simplified model of the transistors and their associated capacitances, timing simulators are faster than circuit simula-

tors. Because of the amount of detail the timing simulators have to examine, the number of components in a circuit that these simulators can handle within reasonable amount of time and space is limited to less than a few thousands gates.

In a logic simulator, circuits are described at the gate level, whose inputs and outputs are binary valued and the signal propagation delay through the device can be specified. Logic simulators exist with capability of dealing with circuits up to tens of thousands of gates. However, the delay models used are generally insufficient for the analysis of MOS LSI circuits, because the circuit delay times are affected not only by the output loading but also by the input loading and input waveforms. The mixed-mode simulators, which aim at accuracy as in circuit simulation and efficiency as in logic simulation, still have the drawback that accurate timing may be lost in interfacing between timing and logic levels.

The multiple delay simulator for MOS LSI circuits proposed by Nham and Bose [16] makes significant use of device level information. Their approach has a number of limitations as pointed out by the authors, including the inability to handle "multiple input to output delays", "delay of a gate driving the data input of a pass transistor", "slope of the input waveform", and "overlapping transition".

Perhaps, a better tool for MOS LSI logic verification is a switch level simulator such as MOSSIM [5], and others [3]

[17]. However, currently such simulators use a unit delay model which can only verify logic without providing any timing information. Switch level simulators model the network in a way which corresponds closely to the actual circuit. Transistors are viewed as switches with no assigned direction of information flow. Nodes can either provide strong signals to the network or can store charge dynamically. Switch level simulators can model a large class of designs, because the basic logic elements of the simulator correspond directly to the basic components of the circuit. The circuit for a switch level simulation can be extracted directly from the layout masks; it requires no knowledge of logic design or the intended functions of the system. The combination of this automatic network extraction followed by switch level simulation may uncover many errors in both the logic design and the layout design. This check may prove to be invaluable.

The multiple delay switch level simulator presented in this thesis is developed to bridge the gap between logic and timing simulators and to provide a compromise between their respective advantages of speed and accuracy. The simulator makes significant use of the device level information; transistors are evaluated logically, and variable rise and fall delays are associated with the transitions. The algorithm used is based on Bryant's algorithm [5], but it is table-driven event-directed and therefore allows for multiple

delays. This simulator also helps in removing most of the limitations mentioned above for that proposed by Nham and Bose [16].

The organization of the thesis is as follows :

Chapter 2 introduces MOS LSI technology. Basic theory and characteristics of the MOS devices are discussed. Delays for the MOS circuits are derived.

Chapter 3 describes some of the techniques used in a conventional logic simulation.

Chapter 4 describes a new multiple delay simulator for MOS LSI circuits. Algorithms for the simulator are presented.

Chapter 5 describes the implementation issues of the simulator.

Chapter II

MOS LSI TECHNOLOGY

2.1 Introduction

Metal oxide semiconductor (MOS) very-large-scale integration (VLSI) has emerged as the most significant development in the electronic industry. MOS technology is the basis for most of the LSI/VLSI digital memory and microprocessor circuits.

The most important advantage of MOS circuits over bipolar circuits is that more transistors and more functions can be successfully fabricated on a single chip. The reasons are threefold: First, an individual MOS transistor occupies less chip area. Second, the fabrication process for MOS circuits involves fewer steps, and thus, results in fewer defects per unit area. This makes it feasible to produce larger chips. Third, dynamic circuit techniques that require fewer transistors to realize a given circuit function are practical and commonly used in MOS technology. The result of these differences is that, for a given function, MOS LSI circuits are significantly cheaper to produce than bipolar circuits. This, accompanied by the fact of increased familiarization of the design techniques for MOS circuits since the introduction of structured VLSI design methodology, accounts for

the trend of steadily increasing fraction of the total digital IC market being taken up by MOS LSI/VLSI circuits.

Even though bipolar circuits are traditionally thought of as very high speed applications, the speed advantage is gradually disappearing as minimum feature size of advanced MOS technology is being scaled down into submicron range [14].

2.2 MOS Transistor

A MOS field-effect transistor (FET) features extremely high input impedance and voltage-controlled output current. A diagrammatic cross-section of an n-channel MOS (NMOS) transistor is shown in Figure 2.1. It consists of two regions of heavily doped n-type (n^+) silicon, introduced in a p-type substrate by diffusion or ion-implantation. By convention, during circuit operation the n^+ region with more positive voltage is referred to as the drain while the other as the source. Because of the symmetry, the source and drain are interchangeable. The p-type area between the source and the drain is the channel region. On top of the channel region is a thin layer of dielectric material, typically silicon dioxide (SiO_2), and a layer of conductor, traditionally metal but largely replaced by polycrystalline silicon (polysilicon) more recently. This forms the gate terminal of the transistor. Note that the term MOS (metal-oxide-semiconductor) is derived from the device structure.

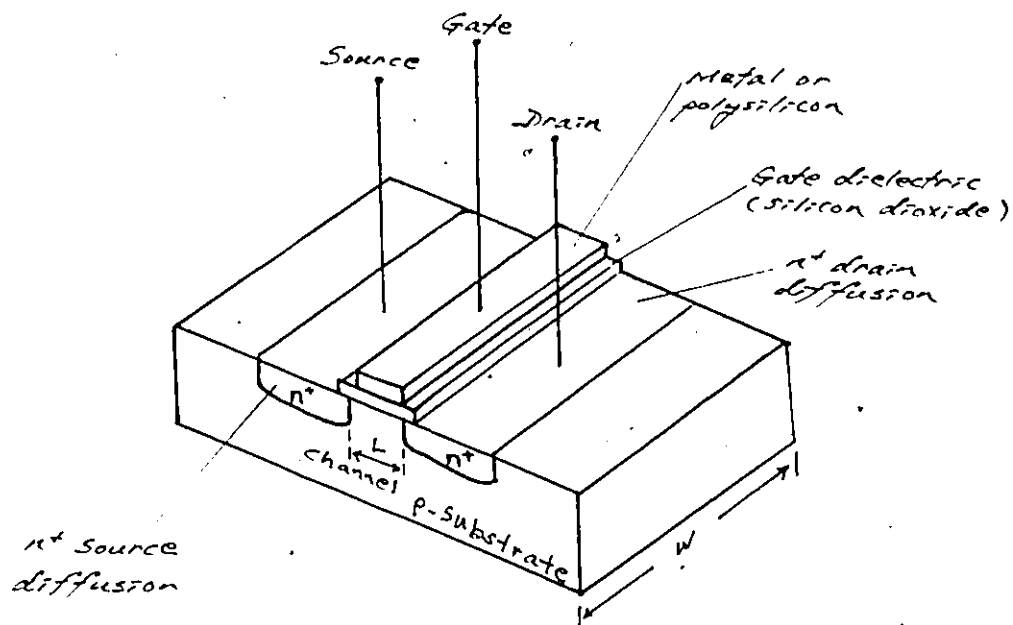


Figure 2.1: NMOS Transistor.

The thin layer of dielectric material is used to insulate the gate from the rest of the MOS device and has a capacitive effect. If a positive voltage is applied to the gate terminal, an electric field is set up which will draw electrons from the substrate into the channel region. If the applied gate voltage is large enough, the p-type material in the channel region will be changed into n-type, thus creating an n-type channel. This n-type channel becomes a conduction path between the source and drain regions through which

the current flows. The direction of the current flow depends on the voltages on the source and the drain. Since the current can flow in either direction through the channel, a MOS transistor is a bilateral device.

A p-channel MOS (PMOS) transistor can be obtained by using an n-type substrate and diffused or ion-implanted p-type source and drain. The p-channel MOS transistor has inferior operating performance, because the charge carriers, holes, move much slower than those (electrons) in n-channel transistors: the mobility of holes is roughly $1/3$ of that of electrons. With improvement in IC processing such as ion-implantation, self-alignment due to the use of polysilicon gates, and the use of depletion-mode load devices, NMOS has been widely used.

CMOS (complementary-symmetric MOS) technology incorporates both p-channel and n-channel transistors in the formation of functional circuits. It features extremely low static power consumption and good noise immunity. However, due to the necessity of device isolation, functional circuits usually occupy larger silicon area than their NMOS counterparts. Further, the fabrication process is more complicated. Nonetheless, CMOS is conceived as the technology for very dense ICs where power density and heat dissipation are premium considerations. To overcome the silicon area penalty, recent trend in CMOS technology is to use n-channel devices to form the functional circuits while p-channel devices are

used sparingly, mainly as the load devices. In this way, the "pseudo-CMOS" technology is essentially a variation of NMOS. The thesis will concentrate on simulation aspects of NMOS circuits, and with slight modification, the results can be used with pseudo-CMOS circuits as well.

2.3 Analysis of the MOS Transistor

The concepts which are necessary for an understanding of the operation of MOS transistors will be discussed in this section. A more detailed theory and derivation of equations can be found in many digital integrated electronic textbooks.

In MOS devices, the conducting channel does not form for very small positive gate voltages because electrostatic potential at the surface of the p-type channel region must be made positive by application of 0.5V to 2V of gate-source voltage. The gate voltage needed to initiate formation of a conducting channel is termed the threshold voltage V_T [13]. In many practical MOS devices, the channel doping concentration is modified by ion-implantation to alter the threshold voltage. A p-type implant will make the threshold more positive. On the other hand, an n-type implant will make the threshold voltage more negative. A large n-type implant can make the n-type channel exist even with a zero gate-source voltage. The threshold voltage in this case is negative.

NMOS transistors that have no conducting channel at zero gate-source voltage are termed enhancement-mode devices. A device which has a conducting channel at zero gate-source voltage is termed a depletion-mode device. For an NMOS depletion device, a negative gate-source voltage is required to deplete the conducting channel. Threshold voltages of enhancement and depletion devices are denoted as V_{TE} and V_{TD} , respectively.

For many NMOS processes, the enhancement threshold voltage, V_{TE} , is usually set at roughly $0.2V_{DD}$ to leave sufficient noise margin, and the depletion threshold voltage, V_{TD} , is set at $-0.8V_{DD}$ for optimizing electrical characteristics of functional circuits. We shall use these figures for illustration purposes in this thesis. However, it must be noted that they are process dependent parameters.

2.3.1 Current-Voltage Characteristics

Within an NMOS device, the charge carriers (electrons) move away from the source and towards the drain region through the channel (see Figure 2.2). The conventional direction of current flow within the devices is from drain to source. Figure 2.3 shows typical I-V characteristics of n-channel MOS devices. In Figure 2.3(a) the MOS device characteristics refer to an enhancement device. In such a device there is no channel between source and drain at $V_{GS} = 0V$. No drain-to-source current I_{DS} flows until the gate-to-source voltage exceeds the threshold voltage V_T . In Figure 2.3(b)

the MOS device characteristics refer to a depletion device. Here a channel exists when $V_{GS} = 0V$ and the threshold voltage V_T is negative.

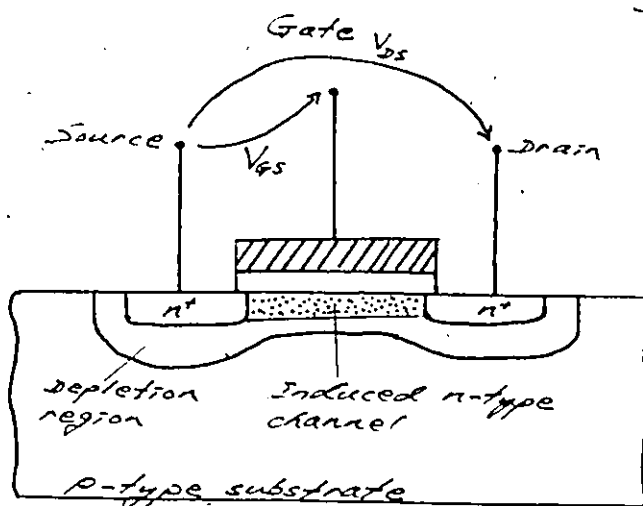
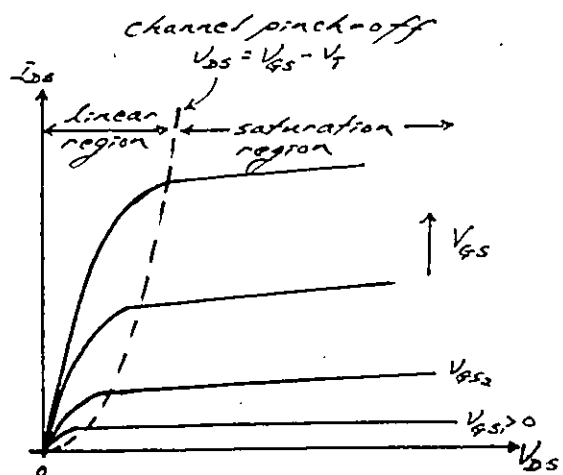
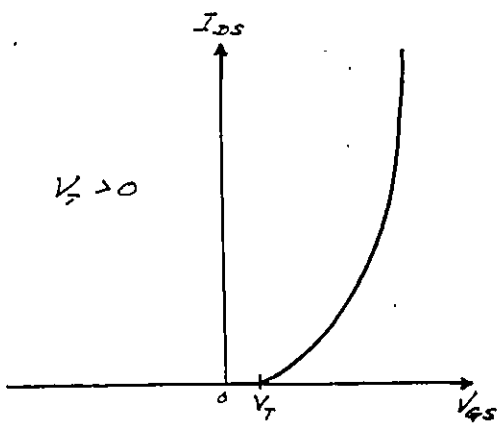


Figure 2.2: NMOS device cross-section showing depletion region and induced channel.

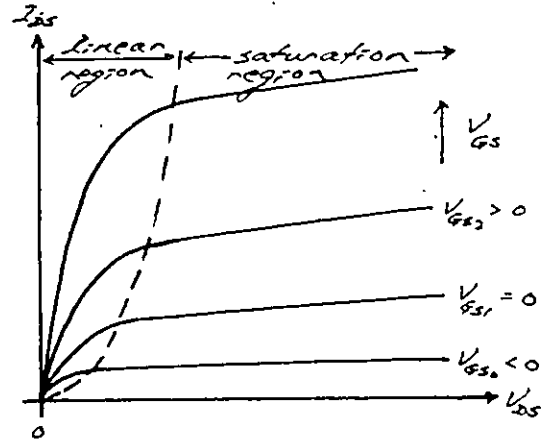
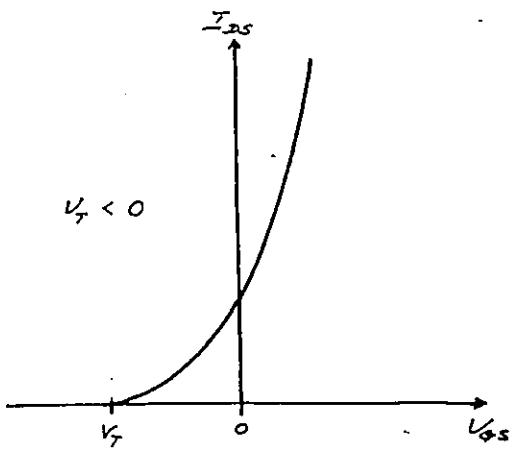
Either transistor type may operate in the linear region or in the saturation region. In the linear region there is a continuous channel between source and drain, and I_{DS} varies almost linearly with V_{DS} for a fixed V_{GS} . In the saturation region, the channel is pinched off at the drain when $V_{GS} - V_T \leq V_{DS}$, the current I_{DS} remains nearly constant.

In the linear region, the drain current is given by the equation

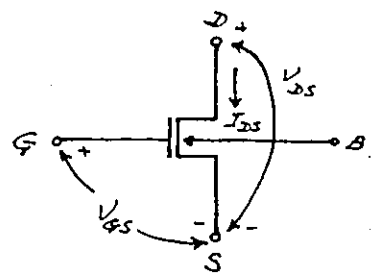
$$I_{DS} = \beta [2(V_{GS} - V_T)V_{DS} - V_{DS}^2] \quad \text{for } 0 < V_{DS} \leq V_{GS} - V_T$$



(a) Enhancement device



(b) Depletion device



(c) Defining voltages and current

Figure 2.3: I-V characteristics for a MOS transistor.

In the saturation region, the drain current is given by the equation

$$I_{DS} = \beta (V_{GS} - V_T)^2 \quad \text{for } 0 < V_{GS} - V_T \leq V_{DS}$$

The constant β is often referred to as the transistor gain factor, which is defined as

$$\beta = \frac{\mu_n C_{ox}}{2} \cdot \frac{W}{L}$$

where

μ_n - mobility of electrons in the channel

C_{ox} - gate oxide capacitance per unit area

W - channel width

L - channel length

In a p-channel device, where the carriers are positive (holes), V_{SD} and I_{SD} are positive. Furthermore, a channel forms to allow current I_{SD} to flow, when the source-to-gate voltage V_{SG} exceeds the threshold voltage $|V_T|$. In the linear region, the drain current is given by the equation.

$$I_{SD} = \beta [2(V_{SG} - |V_T|) V_{SD} - V_{SD}^2] \quad \text{for } 0 < V_{SD} \leq V_{SG} - |V_T|$$

In the saturation region, the drain current is given by the equation

$$I_{SD} = \beta (V_{SG} - |V_T|)^2 \quad \text{for } 0 < V_{SG} - |V_T| \leq V_{SD}$$

The above equations are approximations and do not include all higher-order effects. However, they are entirely adequate for a first-order analysis.

2.3.2 Capacitances of the MOS Transistor

Since the MOS transistor is a field-effect device, the switching speed of MOS circuits is limited by the time required to charge and discharge the capacitances at the driving and driven devices' electrodes and the interconnecting lines. Within LSI circuits all of these capacitances are so small (0.01 to 1 pF) that they are difficult to measure. For circuit analysis, these capacitances are calculated from process dependent data and the size of devices.

Figure 2.4 shows the capacitances among the electrodes of a MOS transistor. The capacitances C_{sb} and C_{db} are the n^+p junction capacitances. Theoretical equations for these capacitances can be derived from the basic physical model of the device. Hogdes [13] gives this derivation and the resultant equation is

$$C_{j0} = \sqrt{\frac{q \epsilon_{si} N_A}{2 \phi_0}}$$

and the built-in junction potential ϕ_0 is given by

$$\phi_0 = (kT/q) \cdot \ln(N_A N_D / n_i^2)$$

where k - Boltzmann's constant
 T - absolute temperature
 q - electronic charge

N_A, N_D - doping concentration

n_i - intrinsic carrier concentration of the silicon

ϵ_{si} - permittivity of the silicon

The capacitance from the gate to other electrodes, to a first-order approximation, can be calculated as the sum C_g of C_{gs} , C_{gb} and C_{gd} , which is nearly a constant and equal to

$$C_g = W \cdot L \cdot C_{ox} = W \cdot L \cdot \frac{\epsilon_{ox}}{t_{ox}}$$

where

W - channel width

L - channel length

ϵ_{ox} - permittivity of the gate dielectric

t_{ox} - thickness of the gate dielectric

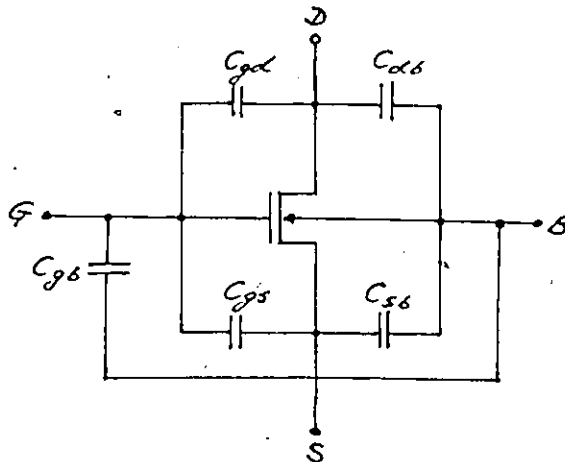


Figure 2.4: MOS transistor capacitances.

In an integrated circuit, capacitances of circuit nodes are due not only to the capacitance of gates connected to the nodes but also to the distributed capacitance of the

signal paths and other stray capacitances. These capacitances, called parasitic capacitances, are not negligible. While gate capacitances are typically an order of magnitude greater per unit area than capacitances of the signal paths, the signal paths are often much larger in area than the associated gate regions. Therefore, a substantial fraction of the delay encountered may be accounted for by stray capacitance rather than by the inherent properties of the active transistors.

There is another type of parasitic capacitance, however, which is not easily accounted for. The Miller capacitance is a feedback capacitance between the drain edge of the gate and the drain node, see Figure 2.5. In Section 2.5-2, we show how these capacitances are used in delay calculations.

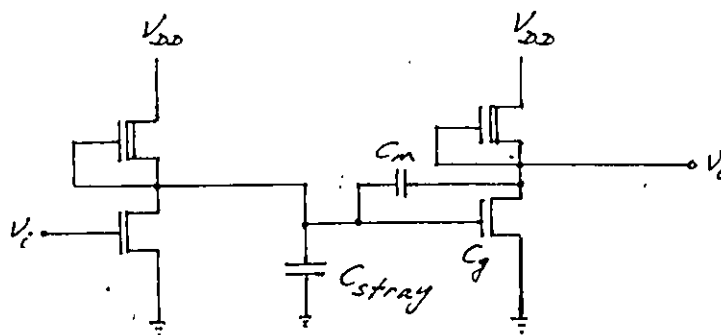
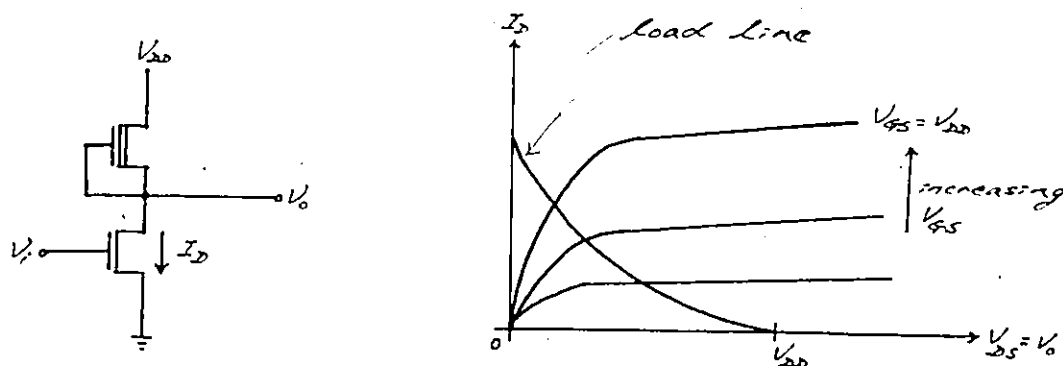


Figure 2.5: The Miller capacitance.

2.4. MOS Circuits

In MOS technology, digital circuits are commonly constructed entirely from transistors. The simplest digital circuit is an inverter. A MOS inverter exhibits all the essential features of a MOS logic circuit.

Figure 2.6 shows a basic NMOS depletion-load inverter circuit; together with drain current-voltage characteristics and load line. The single voltage supply V_{DD} is typically 5 volts. The input; or driver, transistor is an enhancement-mode device with a positive threshold voltage (typically $0.2V_{DD}$), and the load transistor is a depletion-mode device with a negative threshold voltage (typically $-0.8V_{DD}$).



(a) Depletion-load inverter. (b) Drain characteristic and load line.

Figure 2.6: NMOS depletion-load inverter.

Positive logic is used with NMOS digital circuits. Logic values 0 and 1 are at voltage levels near the ground potential 0V and V_{DD} , respectively. The logic operation of the inverter circuit is as follows. When the input voltage V_i is at the logic value 1, the driver transistor is conducting. The relatively low on-resistance of the driver transistor will pull the output voltage V_o down to nearly the ground

potential and thus has a logic value 0. When V_i is at the logic value 0, the driver transistor is non-conducting, and the off-resistance is very high. Thus the output voltage V_o is pulled up through the load transistor to nearly V_{DD} and has a logic value 1.

NMOS NOR and NAND gates are easily constructed from the simple inverter configuration. NOR gates are formed simply by paralleling additional driver transistors, as illustrated in Figure 2.7. The parallel connection of driver transistors in the NOR gates allows the output to rise to V_{DD} only when all driver transistors are turned off. Otherwise, the output is pulled down to nearly the ground potential. NAND gates are formed simply by connecting additional driver transistors in series, as shown in Figure 2.8. The series connection of driver transistors in the NAND gates allows the output to be pulled down to nearly the ground potential only when all driver transistors are turned on. Otherwise, the output is pulled up to nearly V_{DD} .

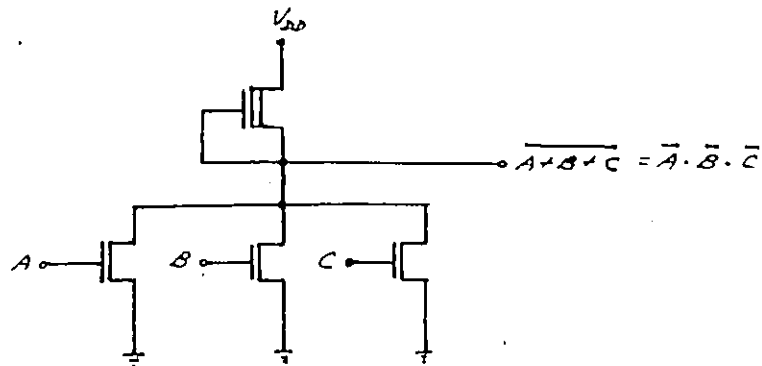


Figure 2.7: 3-input NOR gate.

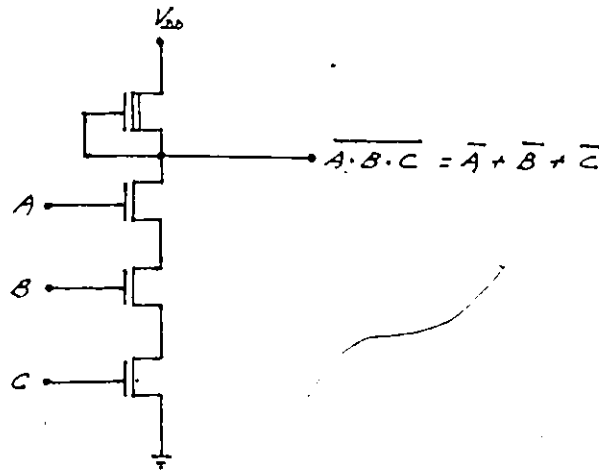


Figure 2.8: 3-input NAND gate.

The transmission gates, or pass transistors, can be used in a way similar to switches to realize logic functions. As shown in Figure 2.9, signals are stored in the input capacitors of a driver transistor in some logic gates in the form of charge. Gates can be subsequently activated by providing suitable control signal so that the stored signals may be used. The transmission gate of Figure 2.9 has the advantage that each additional input requires only a minimum sized transistor. However, the voltage at the input of the inverter will be one threshold voltage lower than V_{DD} when the input voltage at X is high at V_{DD} due to the saturation of the pass transistor. We can transfer pass transistor networks used for steering purpose into the driver part of complex gates. A functional equivalent for the circuit of Figure 2.9 is shown in Figure 2.10.

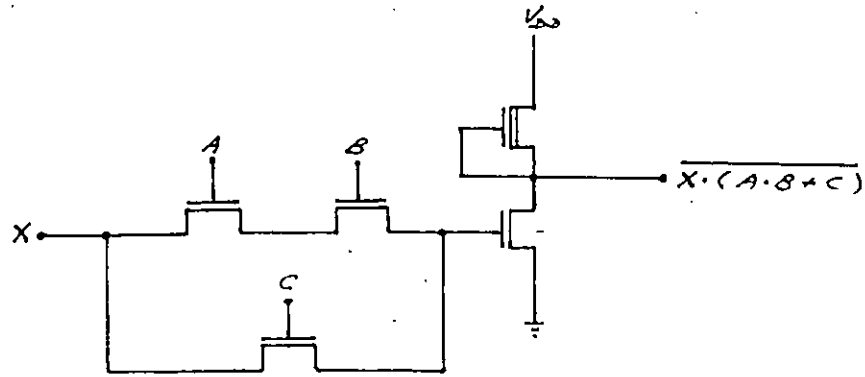


Figure 2.9: Steering logic circuit.

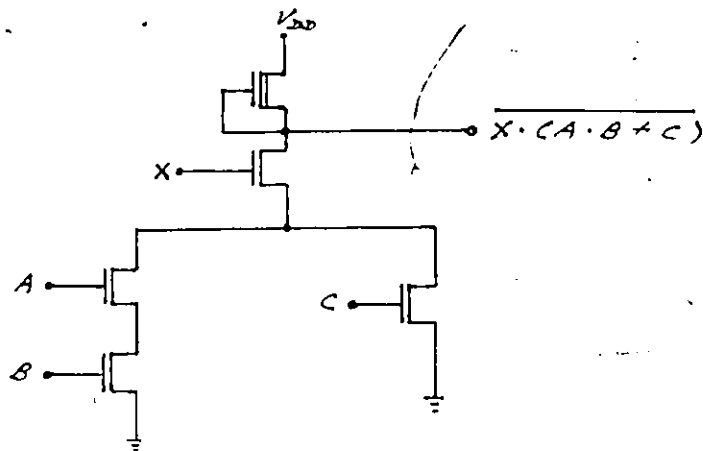


Figure 2.10: An equivalent circuit of Figure 2.9.

2.5 Transient Response of an NMOS Inverter

For an understanding of the transient behaviour of the NMOS inverter, the circuit shown in Figure 2.11 will be analyzed.

To simplify the analysis, the following assumptions are made:

1. All capacitances at the output node are lumped into a single load capacitor, C_L . This allows an analytical

solution to be developed that is adequate for most static circuits. In some dynamic circuit configurations, a more complex equivalent circuit is required due to the consideration of the voltage dependence of various capacitances.

2. The input voltage of the inverter is a step function. Theoretical expressions will be derived for the rise time and the fall time of the inverter.

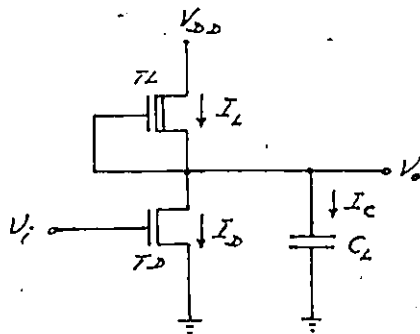


Figure 2.11: Transient model for an NMOS inverter.

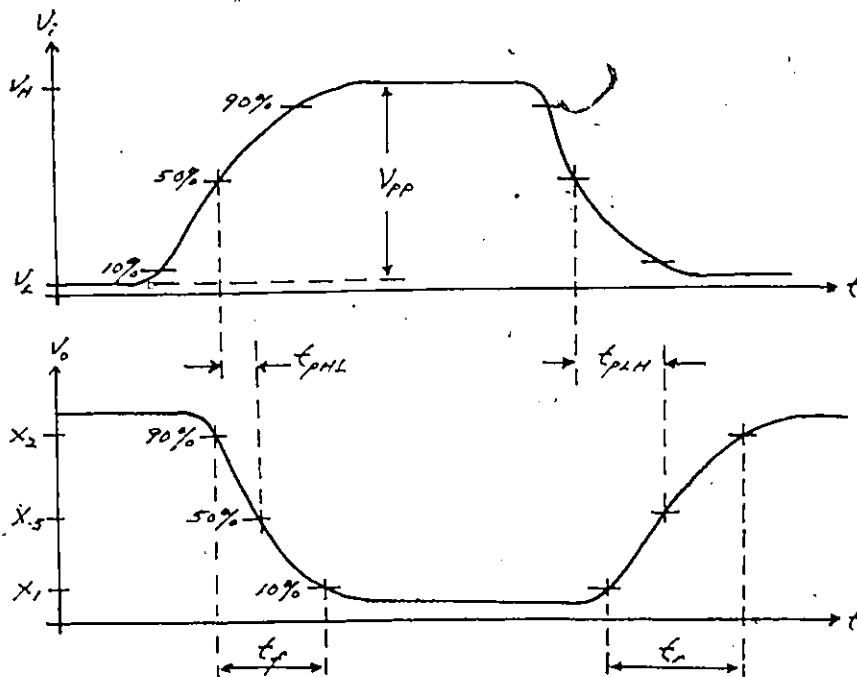
2.5.1 Definition of Transient Characteristics

Before analyzing the transient response of an NMOS inverter, it is necessary to define the transition and propagation delay times [13].

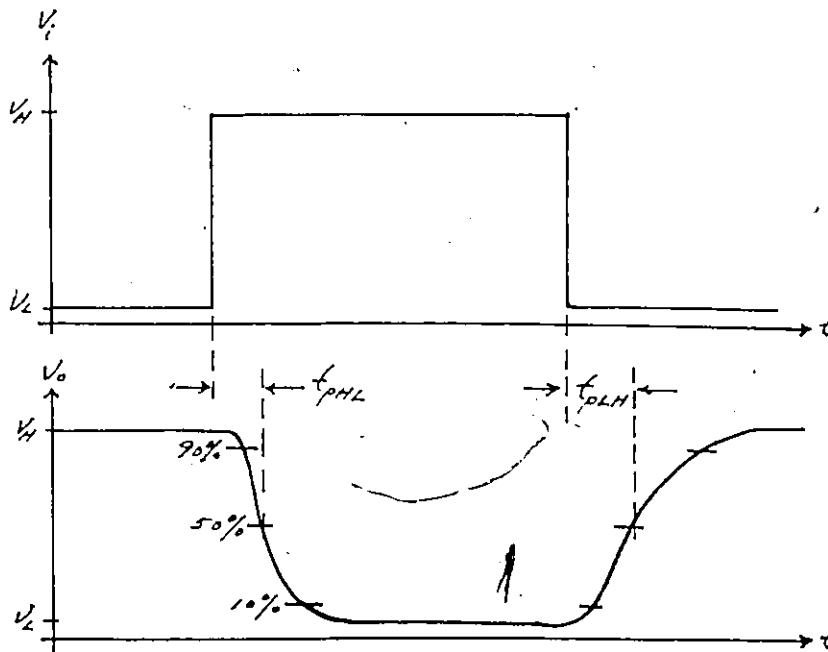
The waveforms at the input and output nodes are shown in Figure 2.12(a), where V_i is the input node voltage, V_o is the output node voltage, V_H , V_L and V_{PP} are the output high, output low levels and the magnitude of the voltage swing, respectively. Rise and fall times, t_r and t_f , are defined as the time duration in which the output node voltage swings between 10% and 90% points.

There are two propagation delays associated with transitions: the rise delay t_{pLH} for the output to rise from low voltage level to high voltage level, and the fall delay t_{pHL} for the output to drop from the high voltage level to the low voltage level. Both delays are defined as the time between the 50% points of the input and output waveforms.

The following expressions for the various delay times are derived based on the assumption of ideal step input waveform as illustrated in Figure 2.12(b). This ideal step input waveform is positioned with its edge at the 50% point of the actual input waveform. Therefore, the propagation delay times are measured from the edge of ideal step input waveform to the 50% point of the output waveform.



(a) Actual transient voltages.



(b) Idealized transient voltages.

Figure 2.12: Definitions of transition and delay times.

2.5.2 Equivalent Capacitance Calculations

As described in Section 2.3-2, each MOS transistor has five separate voltage-dependent capacitances connecting its four electrodes. An analytical solution that takes the voltage dependence into consideration is very difficult, if not impossible, without the use of computer aids. However, an approximate solution can be obtained if all capacitances are lumped into a single capacitance C_T at the output node.

Three of the capacitances, C_{gb} , C_{gd} and C_{gs} , can be approximated as a sum C_g , as described in Section 2.3-2. Voltage dependent junction capacitances, C_{db} and C_{sb} , can be replaced by an equivalent linear capacitance C_{eq} , as follows:

$$C_{eq} = K_{eq} \cdot C_{j0}$$

where C_{j0} is the junction capacitance per unit area as given in Section 2.3-2. The dimensionless parameter K_{eq} is derived in Hogdes [13]. A typical value of K_{eq} is 0.55 for a supply voltage V_{DD} of 5V and a body voltage V_{BB} of 0V.

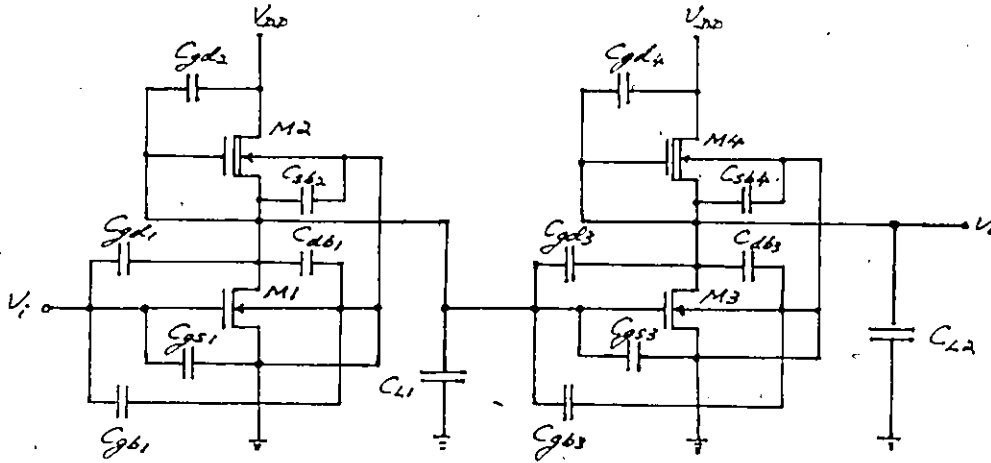
Figure 2.13 shows how the device capacitances in a circuit comprising two cascaded inverters can be lumped at the inverter output nodes. First, all capacitances across which there is no voltage change are ignored, since they have no effect on circuit performance. The device capacitances which must be considered are shown in Figure 2.13(a). In this figure, C_L is the capacitance associated with interconnecting wires at the inverter outputs.

The capacitances C_{T1} and C_{T2} are calculated as follows:

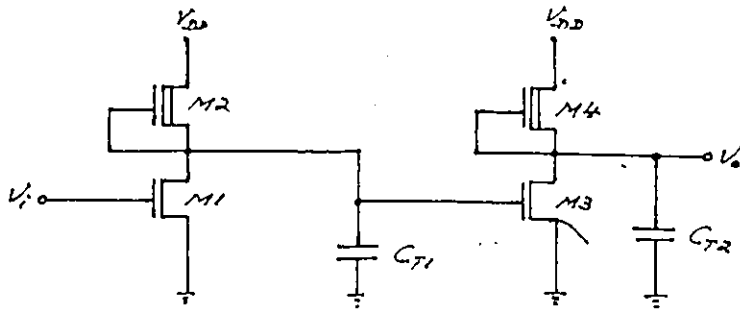
$$C_{T1} = K_{eq} (C_{db1} + C_{sb2}) + C_{L1} + C_{g3}$$

$$C_{T2} = K_{eq} (C_{db3} + C_{sb4}) + C_{L2}$$

The result of the linearization of junction capacitances using K_{eq} is a minor distortion of the shape of transient voltage waveform. However, the propagation delays are not affected significantly by this approximation.



(a) Inverter chain capacitances.



(b) Simplified circuit of Figure 2.13(a).

Figure 2.13: Lumping of capacitances at inverter output nodes.

2.5.3 Rise Time and Rise Delay

To derive the rise time t_r and the rise delay t_{PLH} , consider the situation represented in Figure 2.11. Initially, the driver transistor TD is ON and the output voltage V_o ($V_o = V_c$, the capacitor voltage) is near ground potential. Then the driver transistor TD is turned OFF by the input voltage step at $t=0$. As a result, for $t > 0$, I_D is assumed to be equal to zero and the currents I_L and I_c are given by:

a) When $V_{DS} - V_o = V_{DS} \geq V_{GS} - V_{TD}$ and $V_{GS} > V_{TD}$, the load transistor TL is in saturation region, and the currents are given by

$$I_L = \frac{\mu_n C_{ox}}{2} \cdot \frac{W_L}{L_L} \cdot (V_{GS} - V_{TD})^2$$

$$I_c = C_L \cdot \frac{dV_o}{dt}$$

b) when $V_{DS} - V_o = V_{DS} \leq V_{GS} - V_{TD}$ and $V_{GS} > V_{TD}$, the load transistor TL is in linear region, the currents are given by

$$I_L = \frac{\mu_n C_{ox}}{2} \cdot \frac{W_L}{L_L} \cdot [2(V_{GS} - V_{TD})V_{DS} - V_{DS}^2]$$

$$I_c = C_L \cdot \frac{dV_o}{dt}$$

From these equations we can derive the rise time t_r and the rise delay t_{PLH} . Details are shown in Appendix A. The resultant equations are as follows:

$$t_r = \frac{2C_L}{\mu_n C_{ox} W_L / L_L V_{DD}} \cdot \left[\frac{V_{DD}}{(-V_{TD})^2} (V_{DD} + V_{TD} - X_1) + \frac{V_{DD}/2}{(-V_{TD})} \cdot \ln \left(\frac{2(-V_{TD}) - (V_{DD} - X_2)}{(V_{DD} - X_2)} \right) \right] \quad (2.1)$$

$$t_{PLH} = \frac{2C_L}{\mu_n C_{ox} W_L / L_L V_{DD}} \cdot \left[\frac{V_{DD}}{(-V_{TD})^2} (V_{DD} + V_{TD} - V_L) + \frac{V_{DD}/2}{(-V_{TD})} \cdot \ln \left(\frac{2(-V_{TD}) - (V_{DD} - X_5)}{(V_{DD} - X_5)} \right) \right] \quad (2.2)$$

where

W_L - width of the load channel

L_L - length of the load channel

X_1 , X_2 and X_3 - 10%, 90% and 50% points of the voltage swing

In a typical process, where $\mu_n C_{ox} = 2 \times 10^{-5} \text{ A/V}^2$, $V_{TD} = -0.8V_{DD}$, $V_{DD} = V_{DD}$ and $V_{DD} = 5V$,

$$t_r = 37.0 \times 10^3 \cdot (L_L/W_L) \cdot C_L \quad (2.3)$$

$$t_{pLH} = 16.1 \times 10^3 \cdot (L_L/W_L) \cdot C_L \quad (2.4)$$

2.5.4 Fall Time and Fall Delay

To derive the fall time t_f and the fall delay t_{pHL} , consider the situation represented in Figure 2.11. Initially, the driver transistor TD is OFF and the output voltage V_o is at V_{DD} . Then the driver transistor TD is turned ON by the input voltage step at $t=0$. As a result, for $t > 0$, the currents I_D , I_L and I_C are given by:

a) When $V_{DD} \geq V_o \geq V_{DD} - V_{TE}$, load transistor TL is in linear region and driver transistor TD is in saturation region, and the currents are given by:

$$I_L = \frac{\mu_n C_{ox}}{2} \cdot \frac{W_L}{L_L} \cdot [2(-V_{TD})(V_{DD} - V_o) - (V_{DD} - V_o)^2]$$

$$I_D = \frac{\mu_n C_{ox}}{2} \cdot \frac{W_D}{L_D} \cdot (V_{DD} - V_{TE})^2$$

$$I_C = C_L \cdot \frac{dV_o}{dt}$$

b) When $V_{DD} - V_{TE} \geq V_o \geq V_{DD} + V_{TD}$, both transistors are in linear region, and the currents are given by:

$$I_L = \frac{\mu_n C_{ox}}{2} \cdot \frac{W_L}{L_L} \cdot [2(-V_{TD})(V_{DD} - V_o) - (V_{DD} - V_o)^2]$$

$$I_D = \frac{\mu_n C_{ox}}{2} \cdot \frac{W_D}{L_D} \cdot [2(V_{DD} - V_{TE})V_o - V_o^2]$$

$$I_C = C_L \cdot \frac{dV_o}{dt}$$

c) When $V_o \leq V_{DD} + V_{TD}$, load transistor TL is in saturation region and driver transistor TD is in linear region, and the currents are given by:

$$I_L = \frac{\mu_n C_{ox}}{2} \cdot \frac{W_L}{L_L} \cdot (-V_{TD})^2$$

$$I_D = \frac{\mu_n C_{ox}}{2} \cdot \frac{W_D}{L_D} \cdot [2(V_{DD} - V_{TE})V_o - V_o^2]$$

$$I_C = C_L \cdot \frac{dV_o}{dt}$$

From the current equations given above, we can derive the fall time t_f and the fall delay t_{PHL} . Details are shown in Appendix B. The resultant equations are as follows:

$$\begin{aligned} t_f = & \frac{2C_L}{\mu_n C_{ox} W_L / L_L V_{DD}} \cdot \left[\frac{V_{DD}}{[k(V_{DD} - V_{TD})^2 - V_{TD}^2]^{1/2}} \cdot \left(\tan^{-1} \frac{V_{TE} + V_{TD}}{[k(V_{DD} - V_{TD})^2 - V_{TD}^2]^{1/2}} - \tan^{-1} \frac{V_{DD} - X_2 + V_{TD}}{[k(V_{DD} - V_{TD})^2 - V_{TD}^2]^{1/2}} \right) \right. \\ & + \frac{V_{DD}}{[b_2^2 - 4a_2c_2]^{1/2}} \cdot \left(\ln \left| \frac{2a_2(V_{DD} + V_{TD}) + b_2 - (b_2^2 - 4a_2c_2)^{1/2}}{2a_2(V_{DD} + V_{TD}) + b_2 + (b_2^2 - 4a_2c_2)^{1/2}} \right| \right. \\ & \quad \left. \left. - \ln \left| \frac{2a_2(V_{DD} - V_{TE}) + b_2 - (b_2^2 - 4a_2c_2)^{1/2}}{2a_2(V_{DD} - V_{TE}) + b_2 + (b_2^2 - 4a_2c_2)^{1/2}} \right| \right) \right. \\ & + \frac{V_{DD}}{[b_3^2 - 4a_3c_3]^{1/2}} \cdot \left(\ln \left| \frac{2a_3X_1 + b_3 - (b_3^2 - 4a_3c_3)^{1/2}}{2a_3X_1 + b_3 + (b_3^2 - 4a_3c_3)^{1/2}} \right| \right. \\ & \quad \left. \left. - \ln \left| \frac{2a_3(V_{DD} + V_{TD}) + b_3 - (b_3^2 - 4a_3c_3)^{1/2}}{2a_3(V_{DD} + V_{TD}) + b_3 + (b_3^2 - 4a_3c_3)^{1/2}} \right| \right) \right] \quad (2.5) \end{aligned}$$

$$\begin{aligned}
t_{PHL} = & \frac{2 C_L}{\mu_n C_{ox} W/L V_{DD}} \cdot \left[\frac{V_{DD}}{[k(V_{DD}-V_{TD})^2 - V_{TD}^2]^{1/2}} \cdot \left(\tan^{-1} \frac{V_{TE} + V_{TD}}{[k(V_{DD}-V_{TD})^2 - V_{TD}^2]^{1/2}} \right. \right. \\
& \left. \left. - \tan^{-1} \frac{V_{DD} - V_H + V_{TD}}{[k(V_{DD}-V_{TD})^2 - V_{TD}^2]^{1/2}} \right) \right. \\
& + \frac{V_{DD}}{[b_2^2 - 4a_2c_2]^{1/2}} \cdot \left(\ln \left| \frac{2a_2x.5 + b_2 - (b_2^2 - 4a_2c_2)^{1/2}}{2a_2x.5 + b_2 + (b_2^2 - 4a_2c_2)^{1/2}} \right| \right. \\
& \left. \left. - \ln \left| \frac{2a_2(V_{DD} - V_{TE}) + b_2 - (b_2^2 - 4a_2c_2)^{1/2}}{2a_2(V_{DD} - V_{TE}) + b_2 + (b_2^2 - 4a_2c_2)^{1/2}} \right| \right) \right] \quad (2.6)
\end{aligned}$$

and

$$\begin{aligned}
a_2 &= (k-1) \\
b_2 &= 2V_{TD} + 2V_{DD} - 2k(V_{DD} - V_{TE}) \\
c_2 &= -2V_{TD} V_{DD} - V_{DD}^2 \\
a_3 &= k \\
b_3 &= -2k(V_{DD} - V_{TE}) \\
c_3 &= (-V_{TD})^2
\end{aligned}$$

where

$$k = \frac{W_d/L_d}{W_L/L_L}$$

In a typical process, where $V_{TE} = 0.2V_{DD}$ and $V_{TD} = -0.8V_{DD}$, the above equations become as follows:

i) for $k = 4$,

$$t_f = 4.0624 \left(\frac{1}{\mu_n C_{ox} V_{DD}} \right) \cdot \left(\frac{L_d}{W_d} \right) \cdot C_L \quad (2.7)$$

$$t_{PHL} = 1.6197 \left(\frac{1}{\mu_n C_{ox} V_{DD}} \right) \cdot \left(\frac{L_d}{W_d} \right) \cdot C_L \quad (2.8)$$

ii) for $k = 8$,

$$t_f = 3.8758 \left(\frac{1}{\mu_n C_{ox} V_{DD}} \right) \cdot \left(\frac{L_d}{W_d} \right) \cdot C_L \quad (2.9)$$

$$t_{PHL} = 1.6209 \left(\frac{1}{\mu_n C_{ox} V_{DD}} \right) \cdot \left(\frac{L_d}{W_d} \right) \cdot C_L \quad (2.10)$$

There is a set of equations for each value of k , since the discharging current also depends on the load transistor's geometric aspect ratio.

2.5.5 Transient Response of NMOS Circuits

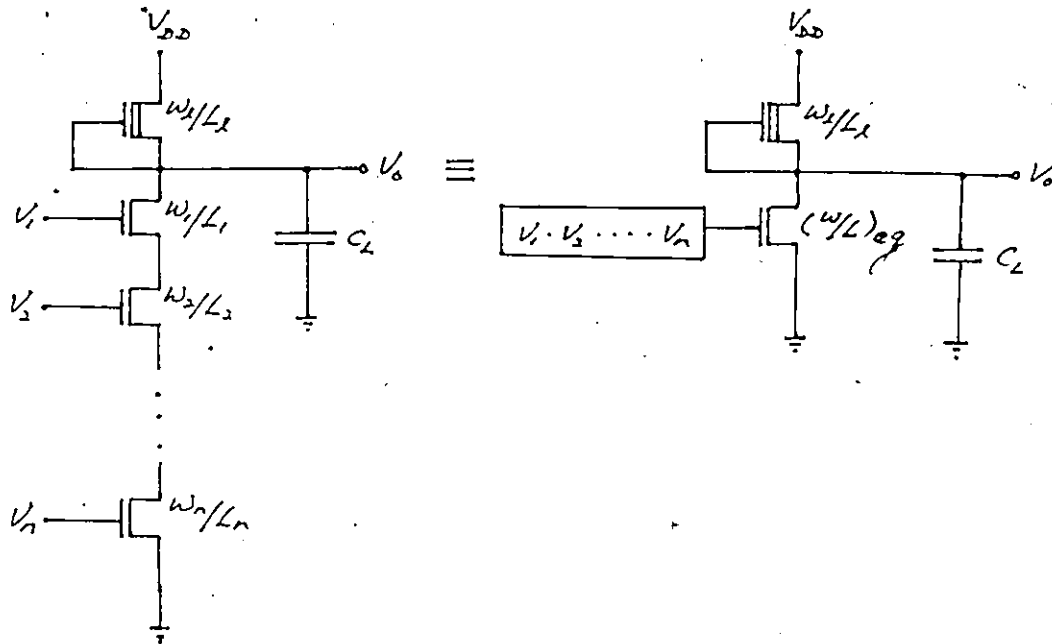
In the previous section, we have derived all the delay time equations for an NMOS inverter. Here, we are going to extend the concepts to any multiple inputs gate such as NAND, NOR and any combination of series and parallel driver transistors. This is done by using the following steps.

First, transform the multiple inputs gate into an equivalent inverter. Second, obtain an equivalent aspect ratio, $(W/L)_{eq}$, for the driver transistors. Then, with this equivalent aspect ratio, we can use the equations for inverter to estimate the rise and fall times, rise and fall delays.

The following shows how NAND and NOR gates are being transformed into an equivalent inverter and the procedure for calculating the equivalent aspect ratio. For the NOR gate, only the active driver transistors are included for calculation of the equivalent aspect ratio.

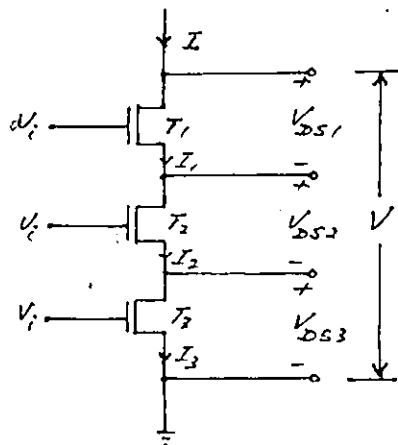
For several devices connected in series whose geometric aspect ratios are W_1/L_1 , W_2/L_2 , ..., W_n/L_n ,

$$\left(\frac{W}{L}\right)_{eq} = \frac{1}{L_1/W_1 + L_2/W_2 + \dots + L_n/W_n}$$



The above expression can be proved (for $n=3$) as follows:

Case 1: When $V_i - V_{TE} \geq V > 0$, all transistors operate in the linear region.



$$V = V_{DS1} + V_{DS2} + V_{DS3}$$

$$I_1 = \mu_n C_{ox} \cdot \left(\frac{W_1}{L_1}\right) \cdot \left[(V_i - V_{DS2} - V_{DS3} - V_{TE}) V_{DS1} - \frac{V_{DS1}^2}{2} \right]$$

$$I_2 = \mu_n C_{ox} \cdot \left(\frac{W_2}{L_2}\right) \cdot \left[(V_i - V_{DS2} - V_{TE}) V_{DS2} - \frac{V_{DS2}^2}{2} \right]$$

$$I_3 = \mu_n C_{ox} \cdot \left(\frac{W_3}{L_3}\right) \cdot \left[(V_i - V_{TE}) V_{DS3} - \frac{V_{DS3}^2}{2} \right]$$

Since $I_1 = I_2 = I_3 = I$,

$$\left(\frac{L_1}{W_1}\right) I = \mu_n C_{ox} \cdot \left[(V_i - V_{TE}) V_{DS1} - V_{DS1} \cdot V_{DS2} - V_{DS1} \cdot V_{DS3} - \frac{V_{DS1}^2}{2} \right]$$

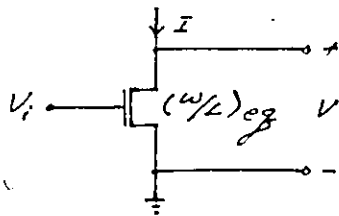
$$\left(\frac{L_2}{W_2}\right) I = \mu_n C_{ox} \cdot \left[(V_i - V_{TE}) V_{DS2} - V_{DS2} \cdot V_{DS3} - \frac{V_{DS2}^2}{2} \right]$$

$$\left(\frac{L_3}{W_3}\right) I = \mu_n C_{ox} \cdot \left[(V_i - V_{TE}) V_{DS3} - \frac{V_{DS3}^2}{2} \right]$$

Adding up the three equations, we have

$$\begin{aligned} \left(\frac{L_1}{W_1} + \frac{L_2}{W_2} + \frac{L_3}{W_3}\right) I &= \mu_n C_{ox} \cdot \left[(V_i - V_{TE}) (V_{DS1} + V_{DS2} + V_{DS3}) \right. \\ &\quad \left. - \frac{1}{2} (V_{DS1}^2 + V_{DS2}^2 + V_{DS3}^2 + 2V_{DS1} V_{DS2} + 2V_{DS1} V_{DS3} + 2V_{DS2} V_{DS3}) \right] \\ &= \mu_n C_{ox} \cdot \left[(V_i - V_{TE}) V - \frac{V^2}{2} \right] \end{aligned}$$

$$I = \mu_n C_{ox} \cdot \left(\frac{1}{\frac{L_1}{W_1} + \frac{L_2}{W_2} + \frac{L_3}{W_3}} \right) \cdot \left[(V_i - V_{TE}) V - \frac{V^2}{2} \right]$$



$$I = \mu_n C_{ox} \cdot \left(\frac{W}{L}\right)_{eq} \cdot \left[(V_i - V_{TE}) V - \frac{V^2}{2} \right]$$

$$\left(\frac{W}{L}\right)_{eq} = \frac{1}{\frac{L_1}{W_1} + \frac{L_2}{W_2} + \frac{L_3}{W_3}}$$

Case 2: When $V \geq V_i - V_{TE} > 0$, transistor T, saturates while T_1 and T_3 operate in the linear region.

$$I_1 = \mu_n C_{ox} \cdot \left(\frac{W_1}{L_1}\right) \cdot \frac{1}{2} (V_i - V_{TE} - V_{DS2} - V_{DS3})^2$$

$$I_2 = \mu_n C_{ox} \cdot \left(\frac{W_2}{L_2}\right) \cdot \left[(V_i - V_{TE} - V_{DS3}) V_{DS2} - \frac{V_{DS2}^2}{2} \right]$$

$$I_3 = \mu_n C_{ox} \cdot \left(\frac{W_3}{L_3}\right) \cdot \left[(V_i - V_{TE}) V_{DS3} - \frac{V_{DS3}^2}{2} \right]$$

$$\left(\frac{L_1}{W_1}\right) I_1 = \mu_n C_{ox} \cdot \left[\frac{1}{2} (V_i - V_{TE})^2 + \frac{1}{2} V_{DS2}^2 + \frac{1}{2} V_{DS3}^2 - (V_i - V_{TE}) V_{DS2} - (V_i - V_{TE}) V_{DS3} + V_{DS2} V_{DS3} \right]$$

$$\left(\frac{L_2}{W_2}\right) I_2 = \mu_n C_{ox} \cdot \left[(V_i - V_{TE}) V_{DS2} - \frac{V_{DS2}^2}{2} \right]$$

$$\left(\frac{L_3}{W_3}\right) I_3 = \mu_n C_{ox} \cdot \left[(V_i - V_{TE}) V_{DS3} - \frac{V_{DS3}^2}{2} \right]$$

Adding up the three equations, we have

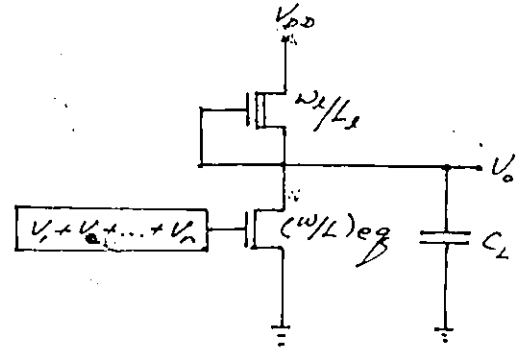
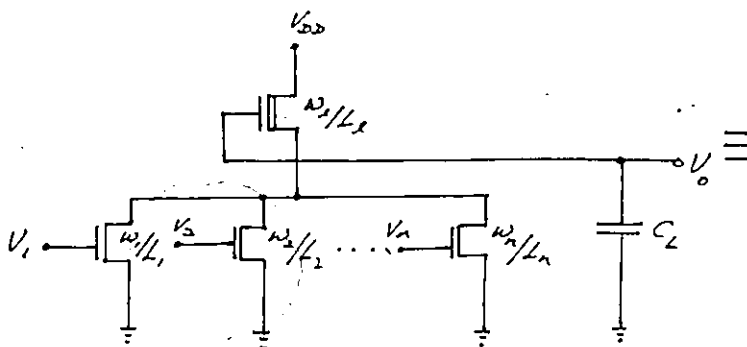
$$\left(\frac{L_1}{W_1} + \frac{L_2}{W_2} + \frac{L_3}{W_3}\right) I = \mu_n C_{ox} \cdot \frac{1}{2} (V_i - V_{TE})^2$$

$$I = \mu_n C_{ox} \cdot \left(\frac{W}{L}\right)_{eq} \cdot \frac{1}{2} (V_i - V_{TE})^2$$

$$\left(\frac{W}{L}\right)_{eq} = \frac{1}{L_1/W_1 + L_2/W_2 + L_3/W_3}$$

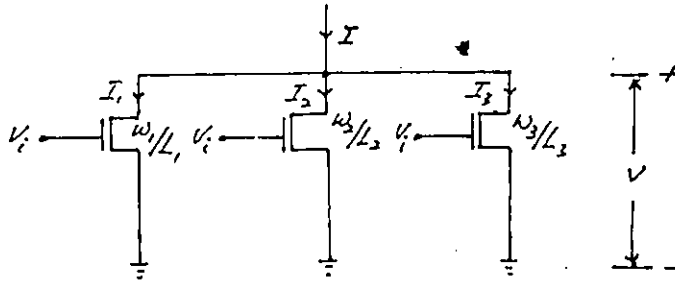
For several devices connected in parallel whose geometric aspect ratios are W/L , W/L , ..., W/L ,

$$\left(\frac{W}{L}\right)_{eq} = \frac{W_1}{L_1} + \frac{W_2}{L_2} + \dots + \frac{W_n}{L_n}$$



The above expression can be proved (for $n=3$) as follows:

Case 1: When $V_i - V_{TE} \geq V > 0$, all transistors operate in the linear region.



$$I_1 = \mu_n C_{ox} \cdot \left(\frac{W_1}{L_1}\right) \cdot \left[(V_i - V_{TE})V - \frac{V^2}{2} \right]$$

$$I_2 = \mu_n C_{ox} \cdot \left(\frac{W_2}{L_2}\right) \cdot \left[(V_i - V_{TE})V - \frac{V^2}{2} \right]$$

$$I_3 = \mu_n C_{ox} \cdot \left(\frac{W_3}{L_3}\right) \cdot \left[(V_i - V_{TE})V - \frac{V^2}{2} \right]$$

Since $I = I_1 + I_2 + I_3$, adding up the equations, we get

$$\begin{aligned} I &= I_1 + I_2 + I_3 \\ &= \mu_n C_{ox} \cdot \left(\frac{W_1}{L_1} + \frac{W_2}{L_2} + \frac{W_3}{L_3} \right) \cdot \left[(V_i - V_{TE})V - \frac{V^2}{2} \right] \end{aligned}$$

$$\left(\frac{W}{L}\right)_{eq} = \frac{W_1}{L_1} + \frac{W_2}{L_2} + \frac{W_3}{L_3}$$

Case 2: When $V \geq V_i - V_{TE} > 0$, all transistors operate in the saturation region.

$$I_1 = \mu_n C_{ox} \cdot \left(\frac{W_1}{L_1}\right) \frac{1}{2} (V_i - V_{TE})^2$$

$$I_2 = \mu_n C_{ox} \cdot \left(\frac{W_2}{L_2}\right) \frac{1}{2} (V_i - V_{TE})^2$$

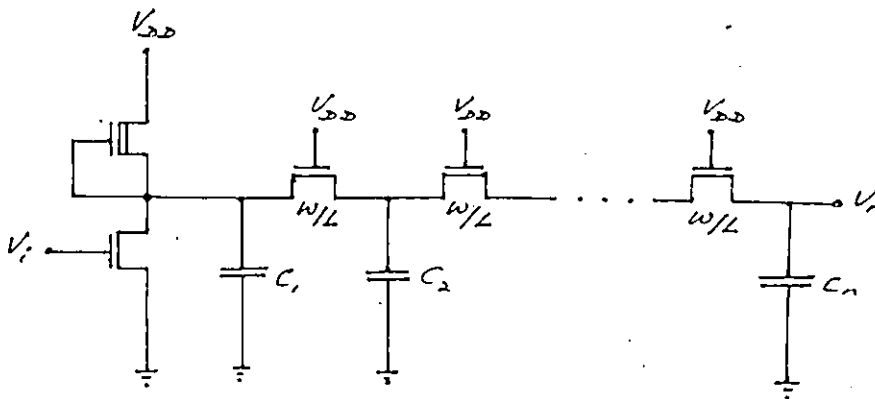
$$I_3 = \mu_n C_{ox} \cdot \left(\frac{W_3}{L_3}\right) \frac{1}{2} (V_i - V_{TE})^2$$

Adding up the three equations, we get

$$\begin{aligned} I &= I_1 + I_2 + I_3 \\ &= \mu_n C_{ox} \cdot \left(\frac{W_1}{L_1} + \frac{W_2}{L_2} + \frac{W_3}{L_3}\right) \frac{1}{2} (V_i - V_{TE})^2 \\ \left(\frac{W}{L}\right)_{eq} &= \frac{W_1}{L_1} + \frac{W_2}{L_2} + \frac{W_3}{L_3} \end{aligned}$$

The circuit below shows an inverter driving a pass transistor chain. The transition and delay times of the inverter can be calculated as before, but with the substitution of an equivalent load capacitance, C_{eq} as given below:

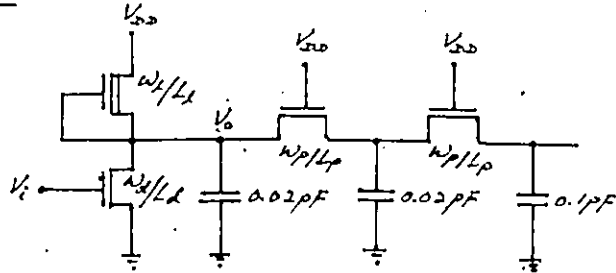
$$C_{eq} = \left(C_1 + \frac{1}{N^2} C_2 + \frac{1}{N^3} C_3 + \dots + \frac{1}{N^n} C_n \right)$$



The above expression gives a reasonable approximation of the delay times and it can be shown with some examples.

As an illustration, the transition and delay times of the following circuit are calculated using the above equations. The results are compared with SPICE simulation results.

Example 1:



Given process parameters:

$$\begin{aligned} & W_n/L_n = 5/10, W_p/L_p = 10/5, W_p/L_p = 5/5 \text{ (all in } \mu\text{m)} \\ & V_{DD} = 5V, \mu_n \mu_p C_{ox} = 2 \times 10^{-5} \text{ A/V}^2 \end{aligned}$$

The equivalent load capacitance,

$$C_{eq} = (0.02 + \frac{1}{\sqrt{2}} \times 0.02 + \frac{1}{\sqrt{3}} \times 0.1) = 0.09 \text{ pF}$$

From eqs. (2.3) and (2.4),

$$t_r = 37 \times 10^3 \cdot \left(\frac{10}{5}\right) \times 0.09 \times 10^{-12} = 6.7 \text{ ns}$$

$$t_{pLH} = 16.1 \times 10^3 \cdot \left(\frac{10}{5}\right) \times 0.09 \times 10^{-12} = 2.9 \text{ ns}$$

From eqs. (2.7) and (2.8),

$$t_f = 40.624 \times 10^3 \cdot \left(\frac{5}{10}\right) \times 0.09 \times 10^{-12} = 1.8 \text{ ns}$$

$$t_{pHL} = 16.197 \times 10^3 \cdot \left(\frac{5}{10}\right) \times 0.09 \times 10^{-12} = 0.7 \text{ ns}$$

(ns)	Approximate Results	SPICE Results
t_r	6.7	7.0
t_f	1.8	1.2
t_{pLH}	2.9	1.3
t_{pHL}	0.7	0.3

In the above delay estimation, we assumed that the equivalent load capacitance is a fixed value C_{eq} . In general, the load which is driven by a MOS inverter composed of pn junction depletion capacitances, the input gate capacitance of driven gate(s), and the net capacitance of a large number of stray or parasite capacitances. All these capacitance values are function of voltage; thus, as the inverter output voltage changes so does the load capacitance. In spite of the simple model used in the derivation and the assumptions that we have made, the estimated delays are pessimistic and with a right order of magnitude.

Figure 2.14 shows a pass transistor with load capacitance C_L . The derivation of the transition and delay time equations are given in Appendix C. The resultant equations are as follows:

$$t_r = 17.778 \left(\frac{1}{\mu_n C_{ox} V_f} \right) \cdot \left(\frac{L_p}{W_p} \right) \cdot C_L$$

$$t_{pLH} = 2 \left(\frac{1}{\mu_n C_{ox} V_f} \right) \cdot \left(\frac{L_p}{W_p} \right) \cdot C_L$$

$$t_f = 2.7438 \left(\frac{1}{\mu_n C_{ox} V_f} \right) \cdot \left(\frac{L_p}{W_p} \right) \cdot C_L$$

$$t_{pHL} = 1.0986 \left(\frac{1}{\mu_n C_{ox} V_f} \right) \cdot \left(\frac{L_p}{W_p} \right) \cdot C_L$$

where

V_f - final value at output node

L_p - channel length of pass transistor

W_p - channel width of pass transistor

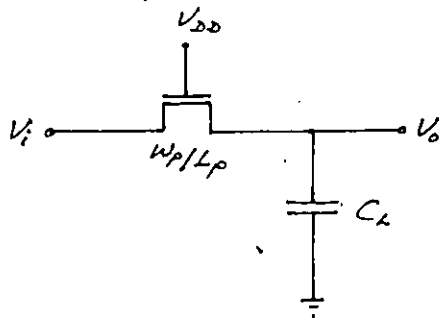


Figure 2.14: A pass transistor.

The above equations can also be used for a pass transistor chain, see Figure 2.15, but with the substitution of C_L and W_p/L_p with C_{eq} and $(W/L)_{eq}$, respectively, as given below:

$$C_{eq} = \frac{1}{Nn} (C_1 + \sqrt{2} C_2 + \dots + \sqrt{n} C_n)$$

$$\left(\frac{W}{L}\right)_{eq} = \frac{1}{n} \cdot \left(\frac{W_p}{L_p}\right)$$

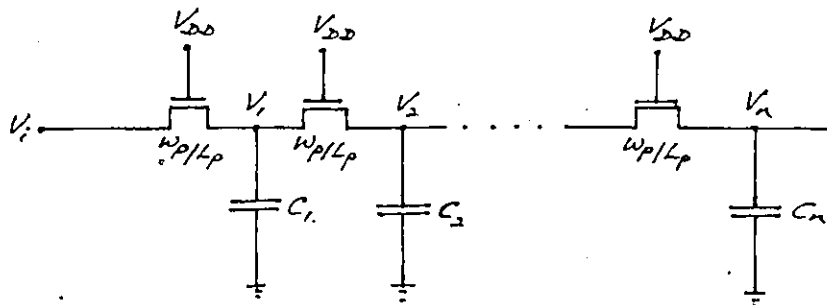
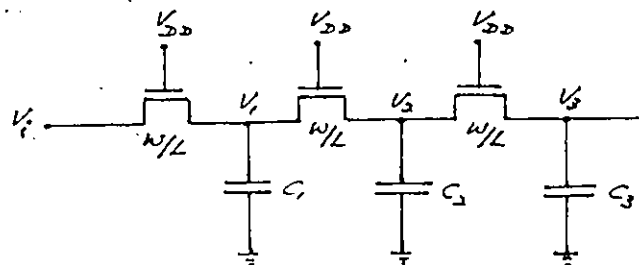
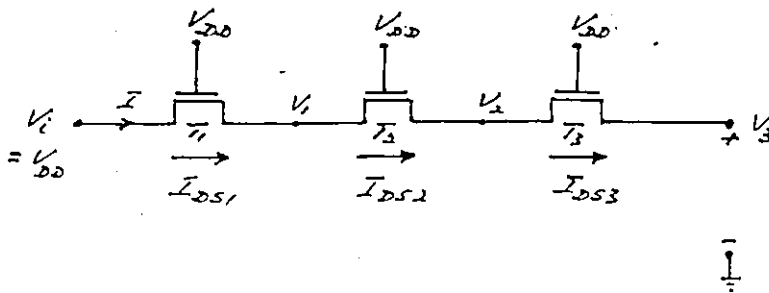


Figure 2.15: Pass transistor chain.

The above expression can be proved (for $n=3$) as follows:



Static analysis



T_1 saturates, T_2 and T_3 operate in linear region.

$$I_{DS1} = \mu_n C_{ox} \cdot \left(\frac{W}{L}\right) \frac{1}{2} (V_{DD} - V_1 - V_{TE})^2$$

$$I_{DS2} = \mu_n C_{ox} \cdot \left(\frac{W}{L}\right) \frac{1}{2} [(V_{DD} - V_2 - V_{TE})^2 - (V_{DD} - V_1 - V_{TE})^2]$$

$$I_{DS3} = \mu_n C_{ox} \cdot \left(\frac{W}{L}\right) \frac{1}{2} [(V_{DD} - V_3 - V_{TE})^2 - (V_{DD} - V_2 - V_{TE})^2]$$

Adding up the three equations, we have

$$3I = \mu_n C_{ox} \cdot \left(\frac{W}{L}\right) \frac{1}{2} (V_{DD} - V_3 - V_{TE})^2$$

Thus,

$$I = \frac{1}{3} \left[\mu_n C_{ox} \cdot \left(\frac{W}{L}\right) \frac{1}{2} (V_{DD} - V_3 - V_{TE})^2 \right]$$

Then,

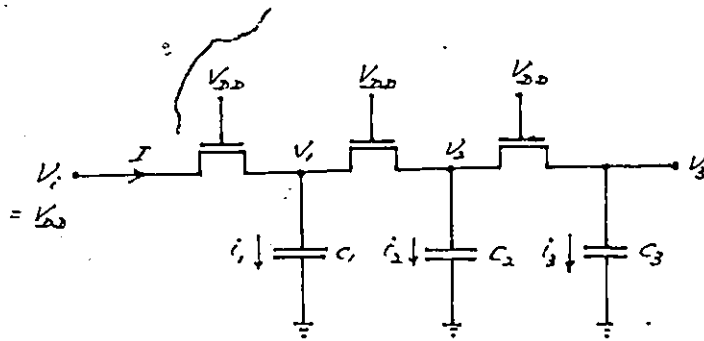
$$(V_{DD} - V_1 - V_{TE})^2 = \frac{1}{3} \cdot (V_{DD} - V_3 - V_{TE})^2$$

$$(V_{DD} - V_2 - V_{TE})^2 = \frac{2}{3} \cdot (V_{DD} - V_3 - V_{TE})^2$$

$$V_1 = \frac{1}{\sqrt{3}} \cdot V_3 + \left(1 - \frac{1}{\sqrt{3}}\right) \cdot (V_{DD} - V_{TE})$$

$$V_2 = \frac{\sqrt{2}}{\sqrt{3}} \cdot V_3 + \left(1 - \frac{\sqrt{2}}{\sqrt{3}}\right) \cdot (V_{DD} - V_{TE})$$

Adding capacitors to the circuit used for static analysis



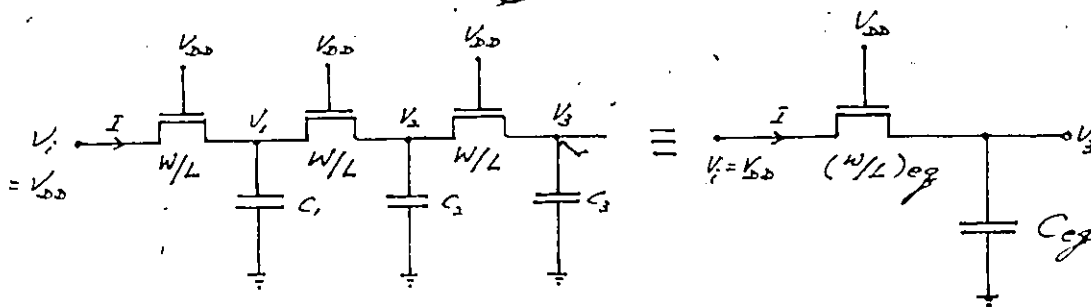
$$i_1 = C_1 \frac{dV_1}{dt} = C_1 \frac{1}{\sqrt{3}} \frac{dV_3}{dt}$$

$$i_2 = C_2 \frac{dV_2}{dt} = C_2 \frac{\sqrt{2}}{\sqrt{3}} \frac{dV_3}{dt}$$

$$i_3 = C_3 \frac{dV_3}{dt} = C_3 \frac{\sqrt{3}}{\sqrt{3}} \frac{dV_3}{dt}$$

$$I = i_1 + i_2 + i_3 = \frac{1}{\sqrt{3}} (C_1 + \sqrt{2} C_2 + \sqrt{3} C_3) \frac{dV_3}{dt}$$

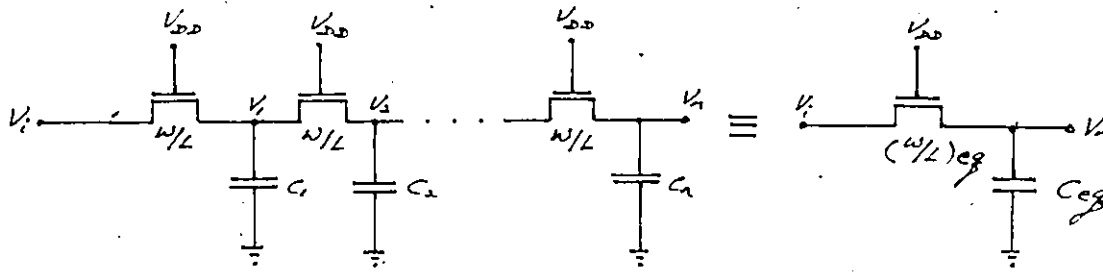
Equivalent Circuit



$$C_{eq} = \frac{1}{\sqrt{3}} (C_1 + \sqrt{2} C_2 + \sqrt{3} C_3)$$

$$\left(\frac{W}{L}\right)_{eq} = \frac{1}{3} \left(\frac{W}{L}\right)$$

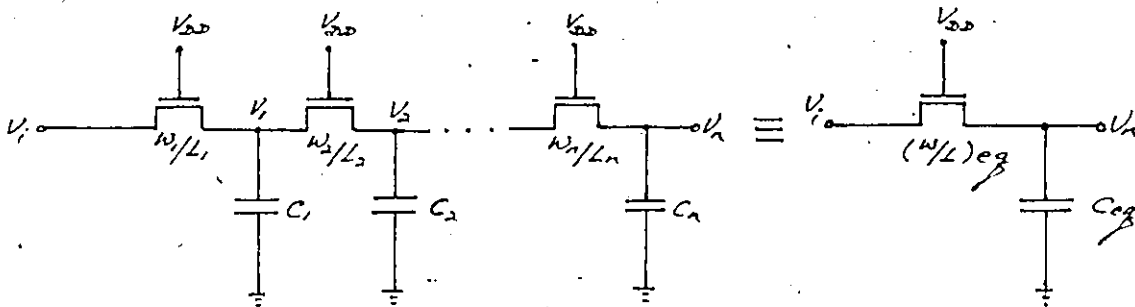
Generalization



$$C_{eq} = \frac{1}{\sqrt{N}} \cdot (C_1 + \sqrt{2} C_2 + \sqrt{3} C_3 + \dots + \sqrt{N} C_N)$$

$$\left(\frac{W}{L}\right)_{eq} = \frac{1}{N} \cdot \left(\frac{W}{L}\right)$$

More on Generalization

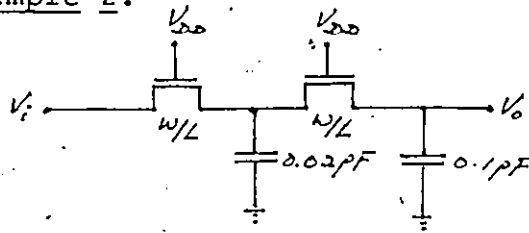


$$C_{eq} = \frac{1}{\sqrt{\sum_{i=1}^N \frac{L_i}{W_i}}} \cdot \left(\sum_{k=1}^N \sqrt{\sum_{j=1}^k \frac{L_j}{W_j}} \cdot C_k \right)$$

$$\left(\frac{W}{L}\right)_{eq} = \frac{1}{\sum_{i=1}^N \frac{L_i}{W_i}}$$

As an illustration, the delays for the following circuit are calculated using the above equations and the results are compared with SPICE simulation results.

Example 2:



Given process parameters:

$$V_{DD} = 5V, \mu_n C_{ox} = 2 \times 10^{-5} \text{ A/V}^2, W/L = 5/5 \text{ (in } \mu\text{m)}$$

$$V_{TE} = 0.2V_{DD}$$

So, $V_f = V_{DD} - V_{TE} = 4V.$

$$\left(\frac{W}{L}\right)_{eq} = \frac{1}{2} \cdot \left(\frac{5}{5}\right) = \frac{1}{2}$$

$$C_{eq} = \frac{1}{\sqrt{2}} \cdot (0.02 + \sqrt{2} \times 0.1) = 0.1141 \text{ pF}$$

$$t_r = 17.778 \left(\frac{1}{2 \times 10^{-5} \times 4} \right) (2) (0.1141 \times 10^{-12}) = 50.7 \text{ ns}$$

$$t_{PLH} = 2 \left(\frac{1}{2 \times 10^{-5} \times 4} \right) (2) (0.1141 \times 10^{-12}) = 5.7 \text{ ns}$$

$$t_f = 2.7438 \left(\frac{1}{2 \times 10^{-5} \times 4} \right) (2) (0.1141 \times 10^{-12}) = 7.8 \text{ ns}$$

$$t_{PHL} = 1.0986 \left(\frac{1}{2 \times 10^{-5} \times 4} \right) (2) (0.1141 \times 10^{-12}) = 3.1 \text{ ns}$$

(ns)	Approximate Results	SPICE Results	% error
t_r	50.7	47.5	7
t_f	7.8	7.1	10
t_{PLH}	5.7	5.8	-2
t_{PHL}	3.1	3.3	-6

2.6 Delay Calculations With Linear Ramp Input

In Section 2.5, we have derived the delay equations for the NMOS circuits. The simple model used in the derivation can occasionally produce large errors in delay estimate. There are two sources of error in the simple model. One source of error is the lumping of equivalent capacitance when there are pass transistors at the output node. This tends to overestimate the delays. Fortunately, for most circuits, the number of pass transistors is usually small and the error produced is not very significant.

The second and more significant source of error in the simple model comes from the assumption that the input waveform is a step function. Consider the situation of Figure 2.16. In (b), the inverter is driven by a linear ramp input waveform; the inverter will take much longer to drive its output load to zero than in (a), because the gate voltage is lower than V_{DD} when the output is being driven in (b). In general, the switching delay of a transistor is a function of both the input waveform and the load being driven.

The solution to this problem is to include the effects of the input waveform. Each input is characterized by its slope (rise/fall time) and the input capacitance, C_I . A rise/fall time of zero corresponds to a step function, and a large rise/fall time corresponds to a slowly rising or falling signal. Typically, if a gate is driving a large output load, or has small input capacitance, only a very slow input rise/

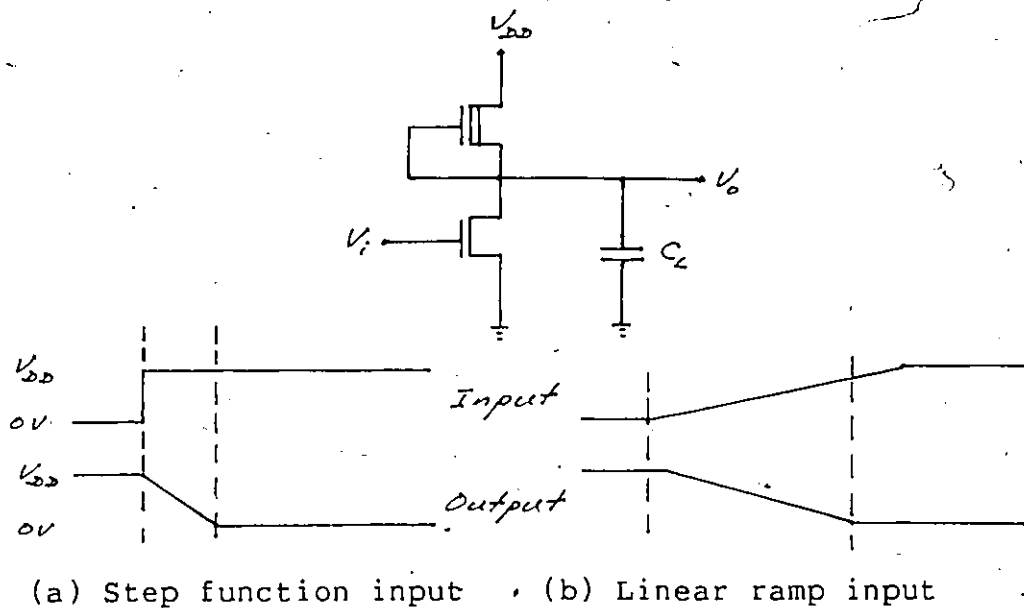


Figure 2.16: An inverter driven by different input waveforms.

fall time will affect its delays. If a gate is driving a small output load, or has very large input capacitance, its delay will be more sensitive to the rise/fall time of the input waveform.

The following subsections show how input waveform is included in delay calculations.

2.6.1 Delays of an Inverter

Here, we analyze an inverter and the results can be applied to other NMOS gates. Figure 2.17 shows an NMOS inverter chain; the various input waveforms to gate G_n are obtained by varying C_{n-1} , the load capacitance of the preceding gate G_{n-1} .

Figure 2.18 shows delay times of gate G_n for various values of C_n and C_{n-1} . The rise delay t_{pLH} depends largely on

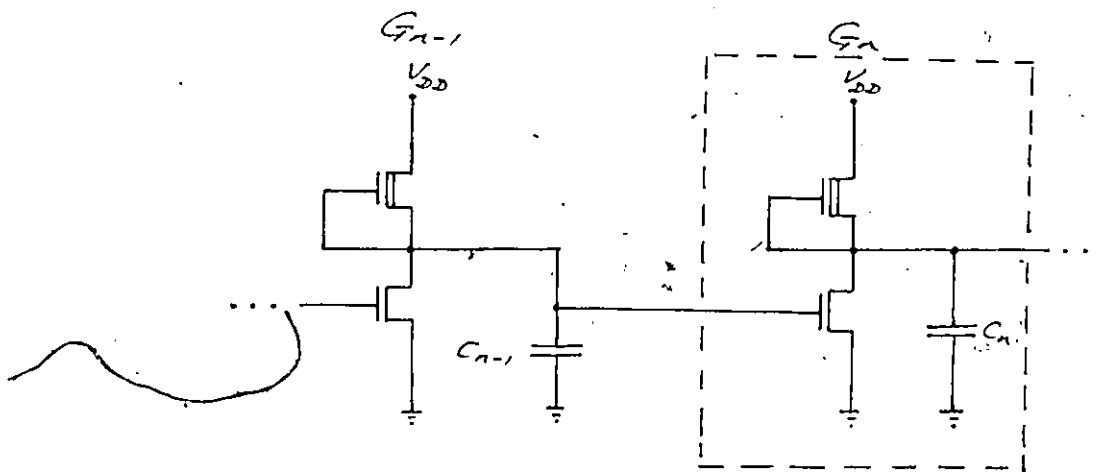


Figure 2.17: NMOS inverter chain.

the load capacitance C_n but less on the input capacitance. The fall delay t_{pHL} is largely affected by the input waveform and the load capacitance C_n .

From here onwards we are going to use a superscript $*$ to indicate rise time or fall time that would occur at the output if the input were driven by a step function, e.g. t_r^* means the rise time of a gate with step function input. Since input waveform is characterized by rise/fall time and the input capacitance, we use a subscript I to indicate it as an input rise time or fall time, e.g. t_{rI} means the input rise time of the gate, and C_I is the input capacitance.

With the above notation, the delay times of the inverter can be approximately given by the following empirical equations by replacing C_n with C_L and C_{n-1} with C_I .

$$t_r = t_r^* (1 + 0.3 (t_{fI} / t_r^*)^{0.5})$$

$$t_f = t_f^* (1 + 0.25 (t_{rI} / t_f^*)^{0.5})$$

$$t_{PLH} = t_r / [2.9^2 + 0.15(C_I/C_L)^2]^{1/2}$$

$$t_{PHL} = t_f / [1.9^2 + 0.06(C_I/C_L)^2]^{1/2}$$

Here, t_r^* and t_f^* are calculated as in Section 2.5. All the empirical constants are obtained from circuit simulation.

As an illustration, the delays for gate G_n in Figure 2.17 are estimated using the above empirical equations. First, assuming the input waveform to gate G_{n-1} is a step function, the output will have various waveform by varying C_{n-1} . The following results are obtained by using equations from Section 2.5.

$C_{n-1}(\text{pF})$	t_r (ns)	t_f (ns)
0.02	1.5	0.4
0.1	7.4	2.0
0.2	14.8	4.1
0.4	29.6	8.1
1.0	74.0	20.3
2.0	147.9	40.6

These output waveforms will become the input waveforms for gate G_n . For gate G_n , first, the rise time t_r^* and fall time t_f^* are calculated with equations from Section 2.5.

Then, using the empirical equations, the output transition and delays are calculated as follows:

Given process parameters:

$$V_{DD} = 5V, \mu_n C_{ox} = 2 \times 10^{-5} \text{ A/V}^2$$

$$W_L/L_L = 5/10, W_\alpha/L_\alpha = 10/5 \text{ (all in } \mu\text{m)}$$

$$C_n = 0.2 \text{ pF}$$

So,

$$t_{rI}^* = 3.6976 \left(\frac{1}{\mu_n C_{ox} V_{DD}} \right) \left(\frac{L_L}{W_L} \right) \cdot C_n = 14.8 \text{ ns}$$

$$t_{fI}^* = 4.0624 \left(\frac{1}{\mu_n C_{ox} V_{DD}} \right) \left(\frac{L_\alpha}{W_\alpha} \right) \cdot C_n = 4.1 \text{ ns}$$

and

$$t_r = 14.8 \left[1 + 0.3 \left(t_{fI}^*/14.8 \right)^{1.5} \right]$$

$$t_{PLH} = t_r / \left[2.9^2 + 0.15(C_{n-1}/0.2)^2 \right]^{1/2}$$

$$t_f = 4.1 \left[1 + 0.25(t_{rI}/4.1)^{1.5} \right]$$

$$t_{PHL} = t_f / \left[1.9^2 + 0.06(C_{n-1}/0.2)^2 \right]^{1/2}$$

The results are given in the following table and plotted in Figure 2.18.

C_{n-1}/C_n	t_r (ns)	t_f (ns)	t_{pLH} (ns)	t_{pHL} (ns)
0.02/0.2	14.8	4.4	5.1	2.3
0.1/0.2	15.0	6.0	5.2	3.2
0.2/0.2	15.4	8.3	5.3	4.3
0.4/0.2	16.6	13.1	5.5	6.7
1.0/0.2	21.9	28.8	6.3	12.7
2.0/0.2	35.0	57.0	7.2	18.4

The results obtained by SPICE simulation program are given in the following table and also plotted in Figure 2.18.

C_{n-1}/C_n	t_r (ns)	t_f (ns)	t_{pLH} (ns)	t_{pHL} (ns)
0.02/0.2	14.9	4.3	5.1	2.3
0.1/0.2	15.5	6.4	5.1	3.9
0.2/0.2	16.3	9.0	5.1	5.4
0.4/0.2	18.3	14.0	5.3	7.0
1.0/0.2	24.0	28.0	6.0	11.5
2.0/0.2	35.0	50.5	6.8	17.0

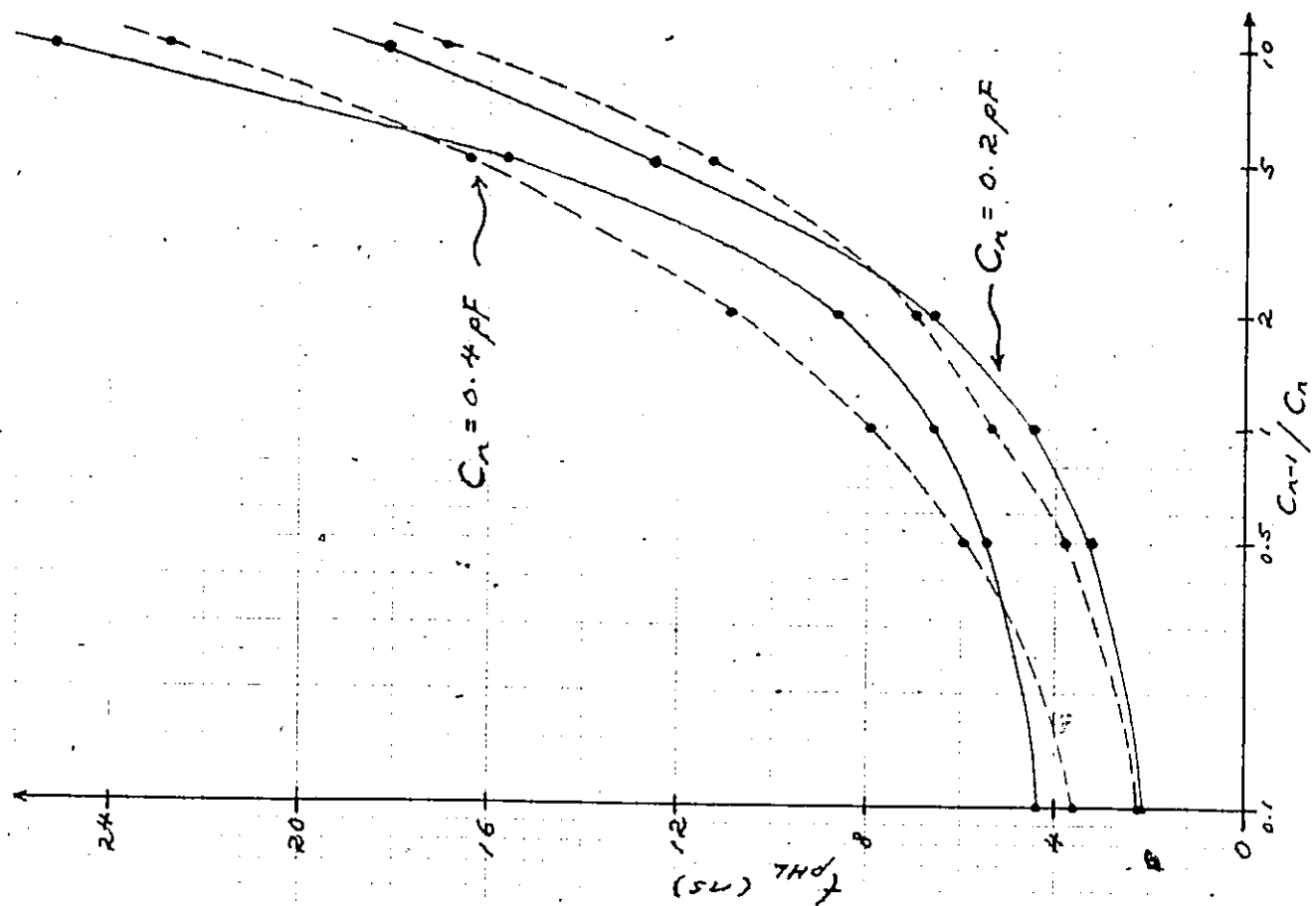
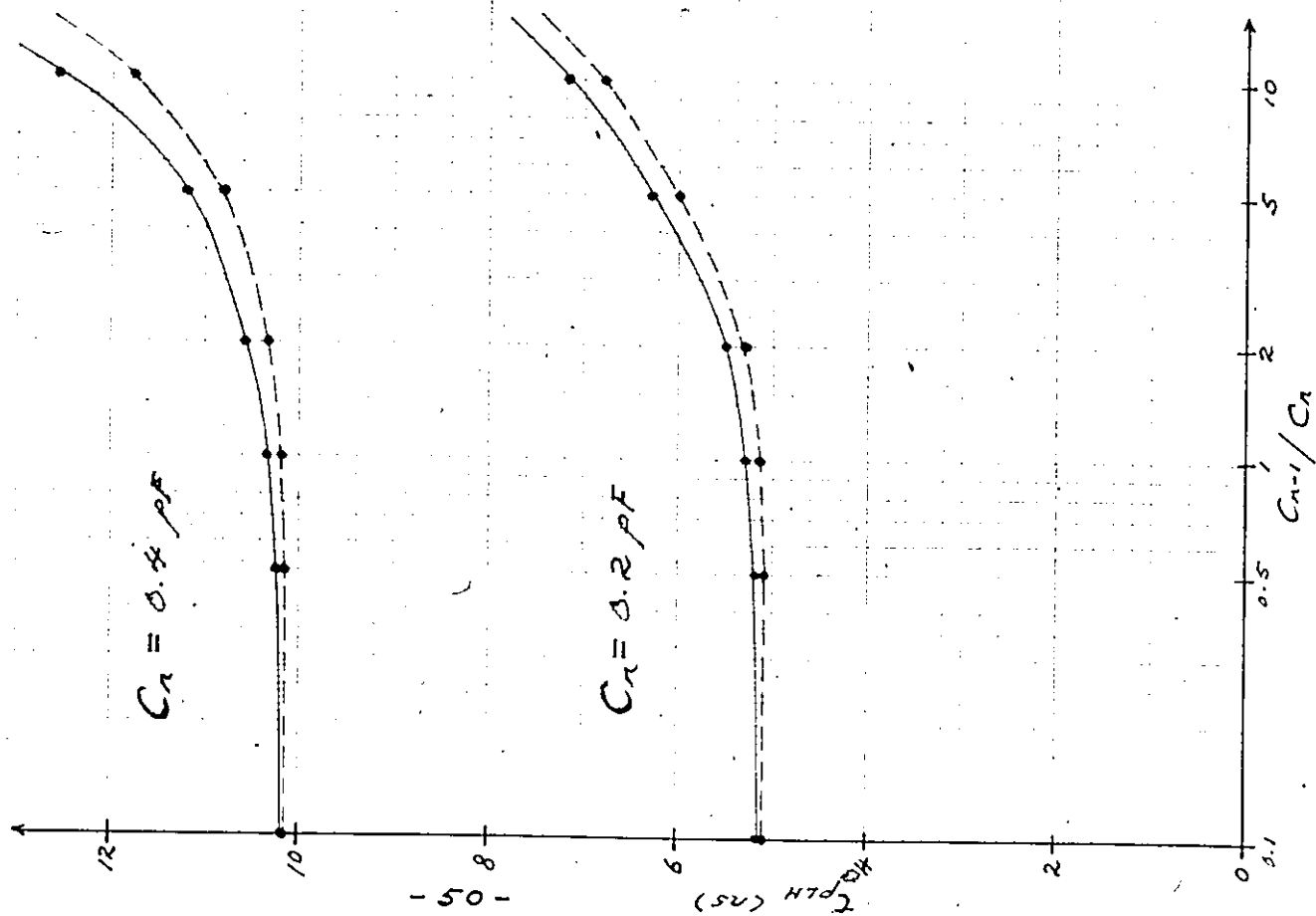


Figure 2.18: Delay times t_{PLH} and t_{PHL} for various capacitive load conditions. The dotted lines are the results obtained by circuit simulation.



2.6.2 Delays of a Pass Transistor Chain

In an earlier section we have calculated the delay times for a pass transistor chain with step input. Here, a pass transistor chain which is driven by an inverter, as shown in Figure 2.19, is considered.

To calculate the delays of the pass transistor chain, first, the output transition times of the inverter are calculated. Then, with these transition times as the input of the pass transistor chain, the delays of the pass transistor chain can be approximately given by the following empirical equations:

$$t_r = t_r^* [1 + 0.3 (t_{rI}/t_r^*)^{0.5}]$$

$$t_{pLH} = t_r / 8.9$$

$$t_f = t_f^* [1 + (t_{fI}/t_f^*)^{0.7}],$$

$$t_{pHL} = t_f / 2.5$$

Here, t_r^* and t_f^* are calculated as in Section 2.5. All the empirical constants are obtained from circuit simulation.

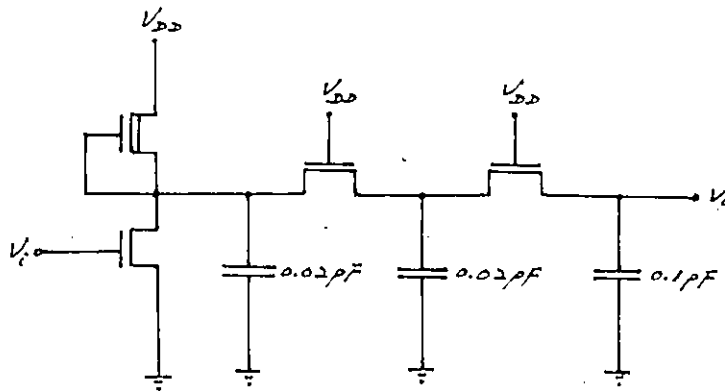


Figure 2.19: A pass transistor chain driven by an inverter.

As an illustration, we will show how the delay times of the circuit in Figure 2.19 are calculated using the above empirical equations.

Example 3

Given process parameters:

$$V_{DD} = 5V, \mu_n C_{ox} = 2 \times 10^{-5} \text{ A/V}^2$$

$$W_n/L_n = 5/10, W_p/L_p = 10/5, W_p/L_p = 5/5 \text{ (in } \mu\text{m)}$$

$$V_{TN} = -0.8V_{DD}, V_{TP} = 0.2V_{DD}$$

First, we calculate the transition times of the inverter. As we have shown in Example 1, the inverter rise and fall times are given by:

$$t_r = 6.7 \text{ ns}$$

$$t_f = 1.8 \text{ ns}$$

Next, the transition times of the pass transistor chain with step input waveform are calculated. As we have shown in Example 2, the rise and fall times of the pass transistor chain are given by:

$$t_r^* = 50.7 \text{ ns}$$

$$t_f^* = 7.8 \text{ ns}$$

With the above values and the empirical equations, the transition and delay times can then be calculated as follows:

$$t_r = 50.7 [1 + 0.3 (6.7/50.7)^{1.5}] = 51.4 \text{ ns}$$

$$t_{PLH} = 51.4/8.9 = 5.8 \text{ ns}$$

$$t_f = 7.8 [1 + (1.8/7.8)^{0.7}] = 10.6 \text{ ns}$$

$$t_{PHL} = 10.6/2.5 = 4.2 \text{ ns}$$

(ns)	Approximate Results	SPICE Results	% error
t_r	51.4	48.5	6
t_f	10.6	10.5	1
t_{PLH}	5.8	5.5	5
t_{PHL}	4.2	5.0	-16

In this example, a different pass transistor structure, pass transistor tree, is considered. Figure 2.20 shows a pass transistor tree driven by an inverter. The delay calculation considers only the direct path between the pullup node (node 3) and the output node (node 7). All the side capacitances are assumed to be connected to the branch nodes. This will reduce the tree structure into a chain structure, and the previous equations can then be applied to delay calculation.

Example 4

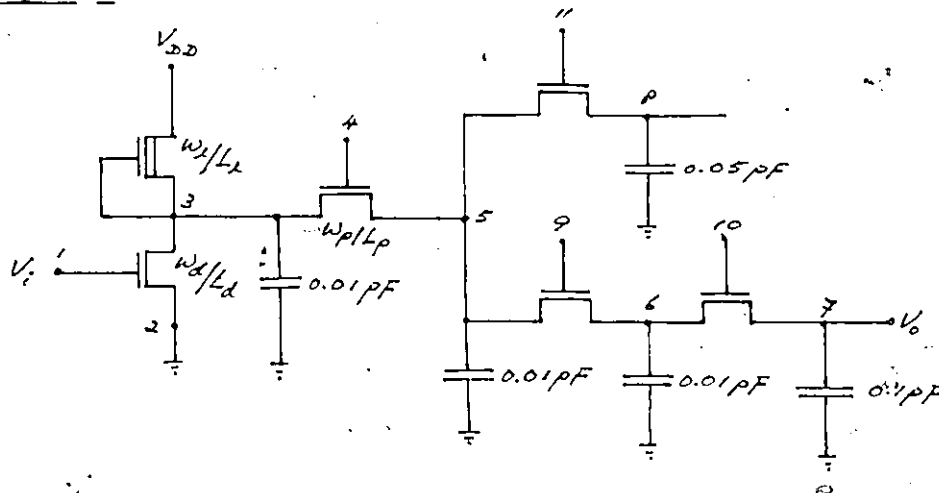


Figure 2.20: A pass transistor tree driven by an inverter.

Given process parameters:

$$V_{DD} = 5V, \mu_n C_{ox} = 2 \times 10^{-5} \text{ A/V}^2$$

$$W_n / L_n = 5/10, W_p / L_p = 10/5, W_p / L_p = 5/5 \text{ (in } \mu\text{m)}$$

$$V_{TD} = -0.8V_{DD}, V_{TE} = 0.2V_{DD}$$

The first step is to calculate the equivalent load capacitance, and the rise and fall times of the inverter.

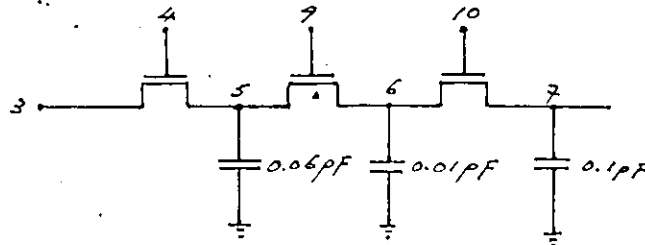
$$C_{eq} = (0.01 + \frac{1}{\sqrt{2}} 0.06 + \frac{1}{\sqrt{3}} 0.01 + \frac{1}{\sqrt{4}} 0.1) = 0.11 \text{ pF}$$

From equations (2.3) and (2.7),

$$t_r = 37 \times 10^3 \cdot \left(\frac{10}{5}\right) \times 0.11 \times 10^{-12} = 8.1 \text{ ns}$$

$$t_f^* = 40.624 \times 10^3 \cdot \left(\frac{5}{10}\right) \times 0.11 \times 10^{-12} = 2.2 \text{ ns}$$

The second step is to reduce the transistor tree into a chain structure, as shown below:



$$\text{So, } V_f = V_{DD} - V_{TE} = 4V$$

$$(W/L)_{eq} = \frac{1}{3} \left(\frac{W_p}{L_p} \right) = \frac{1}{3}$$

$$C_{eq} = \frac{1}{\sqrt{3}} (0.06 + \sqrt{2} 0.01 + \sqrt{3} 0.1) = 0.14 \text{ pF}$$

$$t_r^* = 17.778 \left(\frac{1}{2 \times 10^{-5} \times 4} \right) (3) (0.14 \times 10^{-12}) = 93.3 \text{ ns}$$

$$t_f^* = 2.7438 \left(\frac{1}{2 \times 10^{-5} \times 4} \right) (3) (0.14 \times 10^{-12}) = 14.4 \text{ ns}$$

Then, using the empirical equations,

$$t_r = 93.3 [1 + 0.3 (8.1/93.3)^{1.5}] = 94 \text{ ns}$$

$$t_{PLH} = 94/8.9 = 10.6 \text{ ns}$$

$$t_f = 14.4 [1 + (2.2/14.4)^{0.7}] = 18.3 \text{ ns}$$

$$t_{PHL} = 18.3/2.5 = 7.3 \text{ ns}$$

(ns)	Approximate Results	SPICE Results	% error
t_r	94.0	81.0	16
t_f	18.3	16.5	11
t_{PLH}	10.6	9.0	18
t_{PHL}	7.3	8.3	-12

Chapter III

LOGIC SIMULATION

3.1 Introduction

Logic simulation is the process of building and exercising a model of a digital circuit on a computer. By exercising, it means the evaluation of signal values in the modeled circuit as a function of time for some applied input sequence [4].

There are two main applications for a logic simulator. The first is in the logic and/or design verification of a new design. In logic verification, the logic designers simply verify the logical correctness of the design. While in design verification, they are interested in testing for logical correctness, as well as timing and signal propagation characteristics.

A second application for logic simulation is in the area of fault analysis. Here, the logic designer may desire information related to what faults are detected by a proposed test sequence, what are the operational characteristics of the circuit under specific fault conditions or what degree of fault resolution is obtainable with a given test sequence? These and other questions can be dealt with effectively by the process of fault simulation.

The usefulness of a logic simulator can be evaluated with respect to the following attributes:

1. Accuracy - There should be a close correspondence between predicted signal value in time as calculated by the simulator, and that which occurs in the actual circuit.
2. Efficiency - The process of simulation must be cost effective.
3. Generality - The simulator should be able to handle a broad class of circuits.

In many situations, the accuracy considerations can be thought of as being primarily theoretical, and the cost effectiveness as primarily practical implementation consideration.

This chapter gives an overview of logic simulation, detailed discussion can be found in [4], and as a background for the understanding of the remaining chapters.

3.2 Input Circuit Description

The circuit description can be supplied to the simulator in various forms; and a preprocessor translates the description into a form (data structure) used internally.

At least three possibilities exist for the input: Boolean equations, macro, and elements. The Boolean equation input would allow the user to describe the circuit in an equation form. For example:

$$Z = A \cdot B + C$$

would generate the circuit shown in Figure 3.1, via a Boolean preprocessor.

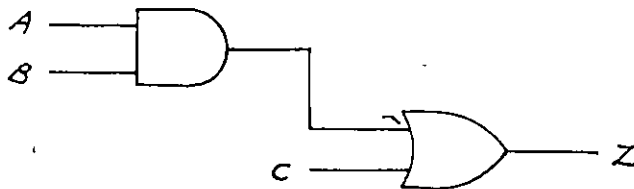


Figure 3.1: Circuit generated from Boolean equation

The macro input circuit description is in the forms of a procedure for highly repetitive logic circuits. For example the 32-bit register, as shown in Figure 3.2, is made up of 32 JK flip-flops. The macro allows the user to describe the flip-flop once at the gate level, and then use this description for each of the 32 bits of the register. This would result in a considerable simplification of the description process.

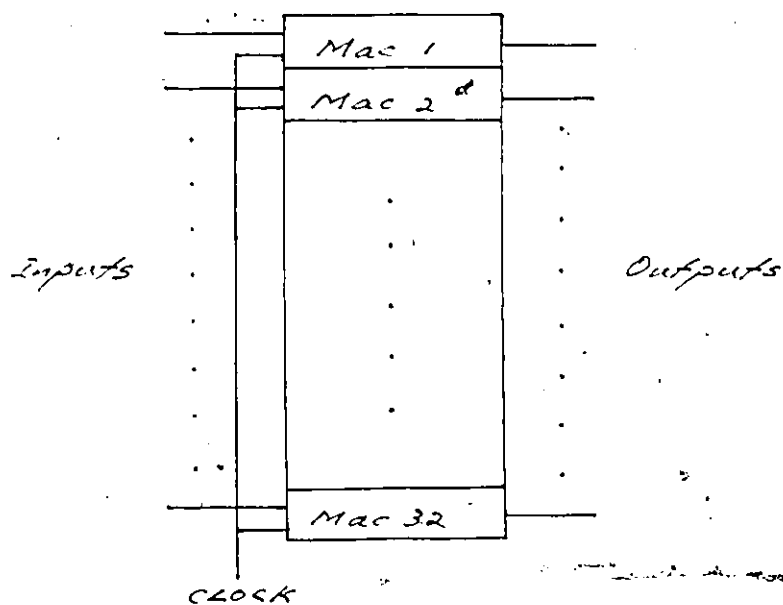


Figure 3.2: Macro representation of a 32-bit register

The element description is similar to the gate level description except that an element can have multiple inputs and outputs whereas a gate has a single output. Figure 3.3 shows an element representation of a JK flip-flop.

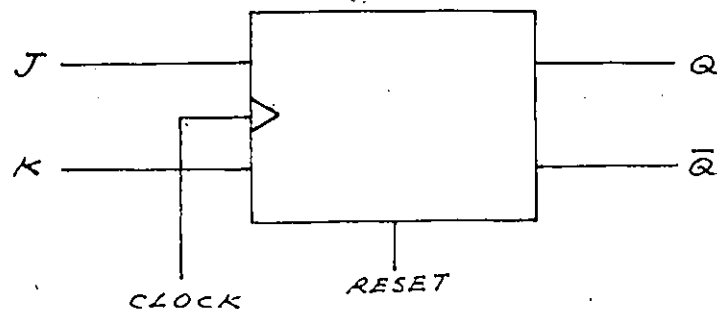


Figure 3.3: Element representation of a JK flip-flop

In a switch-level simulator, circuits are described by a set of nodes connected by transistor switches. The input circuit description consists of a list of transistors, each one consisting of a gate, a source, and a drain node, and other pertinent information, such as the width/length (W/L) aspect ratio for each transistor and the capacitance at each node. This input circuit description can usually be extracted directly from the mask layout; therefore, no knowledge of the logic function of the circuit is required. More detailed description on circuit representation in switch-level simulator is presented in Chapter 4.

3.3 Delay Modeling

Delay is an important attribute to the correct functional operation of many circuits. We can categorize most delay modeling techniques as being either pessimistic or optimistic models of the real circuit. Usually a more detailed delay model is used for design verification than is used for logic verification. In general, simulation delay models used can be categorized as zero, unit, rise/fall and precise delays.

As the timing precision of the model increases, so does the complexity of the implementation, and this complexity is often a major consideration. However, the implementation complexity should not be the dominant consideration. The principal applications area of the simulator is a more important consideration. Zero and unit (single delay value) delay simulators can be used for logic verification, but are not effective for design verification to catch timing errors. In the unit delay model, a single delay value is assigned to each type of logic element. Some devices, however, have different signal rise and fall times due to various electrical parameters such as input waveforms, input capacitances and output capacitances. Such devices can be modeled by assigning two delay values; one for a transition from 0 to 1, and another for a transition from 1 to 0. This model is referred to as a rise/fall delay model, which closely approximates the timing properties for some technologies.

Another timing model is the min/max delay model. These delays defined an ambiguous time region in which the actual signal value changes somewhere in the region. Yet another is called an inertia delay model. To switch a logic gate, some minimum energy is required. In the inertia delay model, this minimum energy is modeled as a minimum pulse width required to switch the logic gate. Figure 3.4 shows the input and output timing diagrams of an inverter for various delay models.

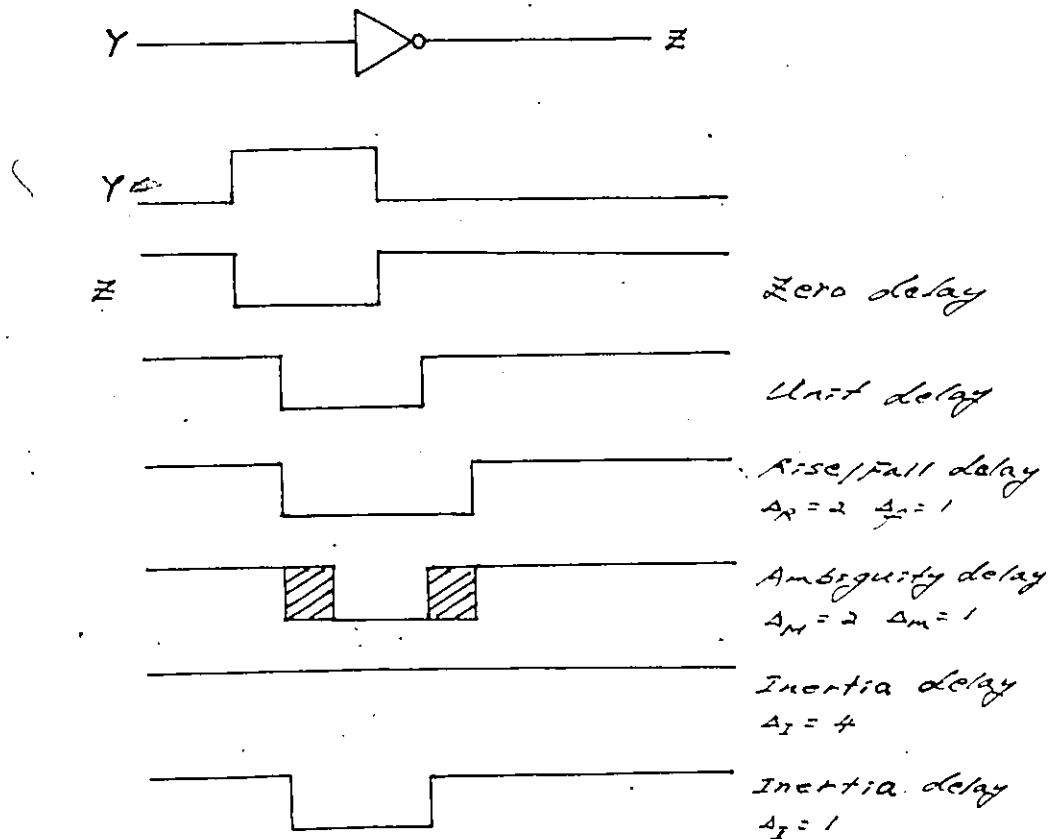


Figure 3.4: Input and output timing diagrams of an inverter for various delay models

3.4 Multiple Logic Values

The choice of particular delay parameters directly affects the number of logic values used in the simulator. Zero and unit delay models can use either two or three logic values for simulation. The values would be 0, 1 and X, where X is indeterminate or unknown. Two-valued (0 and 1) models are not sufficient in design verification. The problem is in the initialization of the circuit to be simulated. Since only two values exist, all signals would be initially set to 0 or 1. Consistency cannot be easily maintained. Also, the abnormal states due to timing errors cannot be represented. Thus, most simulators employ at least three logic values.

The rise/fall delay models use three or four logic values. The four logic values are 0, 1, X and E, where X is the initial unknown state and E represents errors. The min/max delay model requires two additional logic values of U (signal rising) and D (signal falling). For tri-state devices and transmission gates, a value Z is introduced to represent a high impedance state.

To model the circuits correctly, more logic values would be required, but this will generally lengthen the simulation time. Therefore, the selection of the number of logic values in implementation is dependent on the purpose of simulator.

This multiple delay simulator uses three logic values: 0, 1, and X, where X represents the initial unknown state and also the timing errors. A detailed description of this delay model is presented in Chapter 4.

3.5 Simulator Structures

There are two basic classes of simulators: compiled code and table-driven event-directed [4]. In compiled code simulators, the circuit to be simulated is actually represented internally as a sequence of computer instructions. The table-driven event-directed simulator is more versatile in handling delays and achieves computational efficiency. Therefore, table-driven event-directed simulation is described in the following section.

3.5.1 Event Directed Simulation

Simulation of a logic circuit starts from building a circuit model, which consists of the descriptions of circuit elements and their interconnections. Then an input sequence is introduced to the input terminals at predetermined times. The circuit will be simulated at discrete time steps by evaluating the response to the applied input stimuli. If any circuit elements change states, they are scheduled to change after some appropriate delay. Simulation process continues until the circuit stabilizes (no more inputs to simulate and the circuit reaches a steady state).

It is generally observed that at any simulation time step, only a small percentage of all the signal lines changes values, typically 2-10%. Thus, it appears wasteful, as is done with the compiled code approach, to simulate all the circuit elements when only a small portion of the circuit is actively changing. Another fact is that the output of a circuit element will change its value only when at least one of its inputs changes. An event is defined as a change in logic value of a signal line. Based on the facts above, circuit elements need to be evaluated only when an event occurs at one or more of its inputs.

When an event occurs, the outputs of all those elements with inputs connected to that line are potentially active and require evaluation. As one simulates all the potentially active circuit elements, one will find that only some have the output values changed while others do not. A significant reduction in computation can be achieved by simulating only the potentially active elements rather than all the elements. The technique is referred to as event directed or selective trace (tracing after events).

3.5.2 Event Scheduling

When a circuit element is evaluated at t_0 , and it has been determined that its output node has changed its logic state, then this output event is scheduled at the future time step $t_0 + \Delta$, where Δ is the delay time for this change to take place. The technique used to schedule and reschedule events is called the time-flow mechanism.

One way to organize the scheduling of events is to use a list structure as shown in Figure 3.5, where all the events occurring at the same time are linked together. The headers of these list are stored in increasing order, e.g., $t_i < t_j < t_k$ as illustrated.

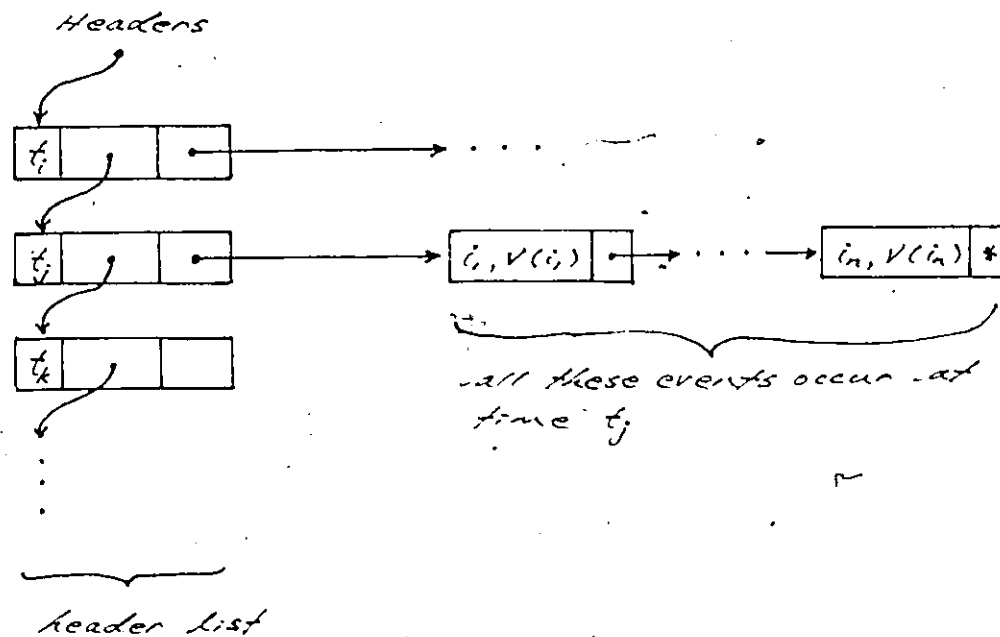


Figure 3.5: List structure scheduler

Chapter IV

MULTIPLE DELAY SWITCH-LEVEL SIMULATION ALGORITHM

4.1 Introduction

In simulating MOS circuits accurately, ~~one~~ of the problems is the accuracy of delay time. The delay time of a MOS gate depends not only on the output loading but also the input waveform.

The traditional approach to delay calculation is the use of circuit simulation programs such as SPICE [15]. In this case, circuit delays are obtained by solving a set of integral-differential equations. This approach produces highly accurate delays. However, this accuracy does not come without cost: intolerably long computing time. Thus, this approach is impractical for today's state-of-the-art LSI/VLSI circuits, which contain tens or hundreds of thousands of transistors.

Another approach is the use of a switch-level logic simulator such as MOSSIM [5] and others [3] [17]. Unfortunately, this type of simulator predicts accurately the logic levels without regard to the circuit delays due to the unit delay model used.

In this chapter, we shall describe a switch-level logic simulation algorithm that takes circuit delays into account.

It is an extension to the existing unit delay algorithm [5], but with a multiple delay model added. This delay model takes into consideration the effects of not only the output capacitive loading but also the input waveforms.

4.2 Network Model

A switch network [5][6][7] consists of a set of nodes, $n_1, n_2, \dots, n_k$, connected by a set of transistors $t_1, t_2, \dots, t_m$. Each node n_i is in a state s_i as one of 0, 1, and X, where 0 and 1 represent the low and high voltage level, respectively, and X indicates an indeterminate or unknown voltage level. Each node n_i is classified as either an input node or a storage node. Input nodes provide strong signals and storage nodes provide weak signals. By signal strength we mean the current supplying or sinking capability of the circuit node. The signal strengths are defined as follows:

1. A node with driver strength (D) provides a strong signal to the circuit being driven, and the signal is not affected by the circuit action. Typical examples of nodes with driver strengths are signal sources such as V_{DD} , GND, and clocks.
2. A node connected to V_{DD} through a resistor or a depletion pull-up transistor is considered to have the pull-up strength (L). This strength has sufficient driving capability but weaker than nodes with D strength.

3. All other nodes are of the weak strength (W). Typically, these nodes are internal circuit nodes connecting enhancement transistors. Such nodes are always connected to GND through stray capacitances due to interconnections or the gate capacitance of a transistor.

A signal is represented by a pair (s_i, f_i) , consisting of its logic state (s_i) and its strength (f_i) . Figure 4.1 illustrates the representation of a network.

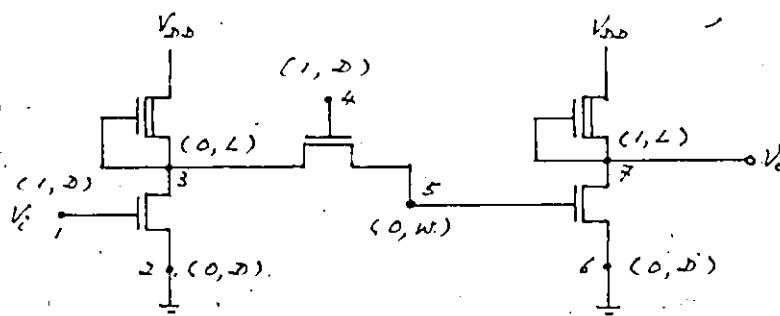


Figure 4.1: Illustrations of the node states and node strengths of a circuit.

A transistor is a three terminal device with terminals labelled "Drain", "Gate", and "Source" as shown in Figure 4.2. No distinction is made between the drain and the source. Each transistor has a type n, p, or d, corresponding to the n-type enhancement, p-type, or n-type depletion devices, respectively. A transistor acts as a resistive switch connecting its drain and source controlled by its gate. Each transistor t_i has a state z_i open, closed, or

unknown, where "open" indicates non-conducting and "closed" conducting. A transistor in the "unknown" state shows an indeterminate conductance, somewhere in-between the conductance of fully open and fully closed. Table 4.1 shows the transistor types and their behaviour.

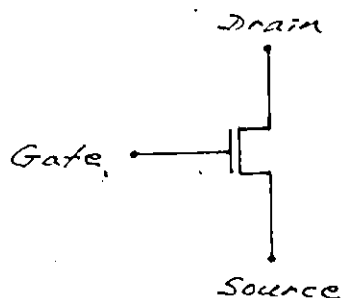


Figure 4.2: A MOS transistor.

n-type		p-type		d-type	
gate node state	transistor state (effect)	gate node state	transistor state (effect)	gate node state	transistor state (effect)
0	open	0	closed	0	closed
1	closed	1	open	1	closed
X	unknown	X	unknown	X	closed

Table 4.1: Transistor types and their behaviour

Nodes in a subnetwork are categorized as external or internal. All nodes with connections to circuit elements

outside the subnetwork are external nodes. They are points of interest because events at these nodes cause scheduling of evaluations of other subnetworks.

4.2.1 Network Representation

We assume that we have a logic network in which all the depletion load transistors are replaced by pull-up nodes. Then we can represent the structure of a network, Ω , in the following way:

$$\Omega = (N , T)$$

where

$$N = \{ n_i \}$$

denotes the set of nodes, and

$$T = \{ t_i \}$$

denotes the set of transistors. The state of the network is defined as:

$$M = (S , Z)$$

where

$$S = \{ s_i \}$$

denotes the node states, and

$$Z = \{ z_i \}$$

denotes the transistor states.

Information concerning the nodes and transistors is encoded by the following mappings:

NTYPE(N) --->	(internal, external)	node type
TTYPE(T) --->	(n, p, d)	transistor type
DRAIN(T) --->	N	drain node
GATE(T) --->	N	gate node
SOURCE(T) --->	N	source node

For example, see Figure 4.1, if we are given a node n_x , the mapping NTYPE(n_x) will give the information that node n_x is an external node.

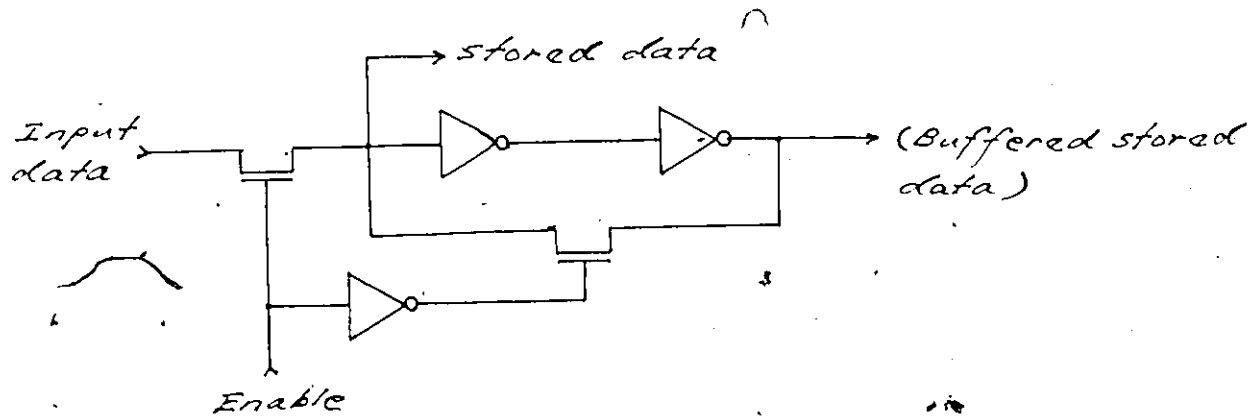
4.2.2 Partitioning of the Network

In order to apply selective trace of activities and time flow mechanism, a network is partitioned into its connected components, referred to as subnetworks. The nodes and transistors belonging to a subnetwork S_u are identified as follows:

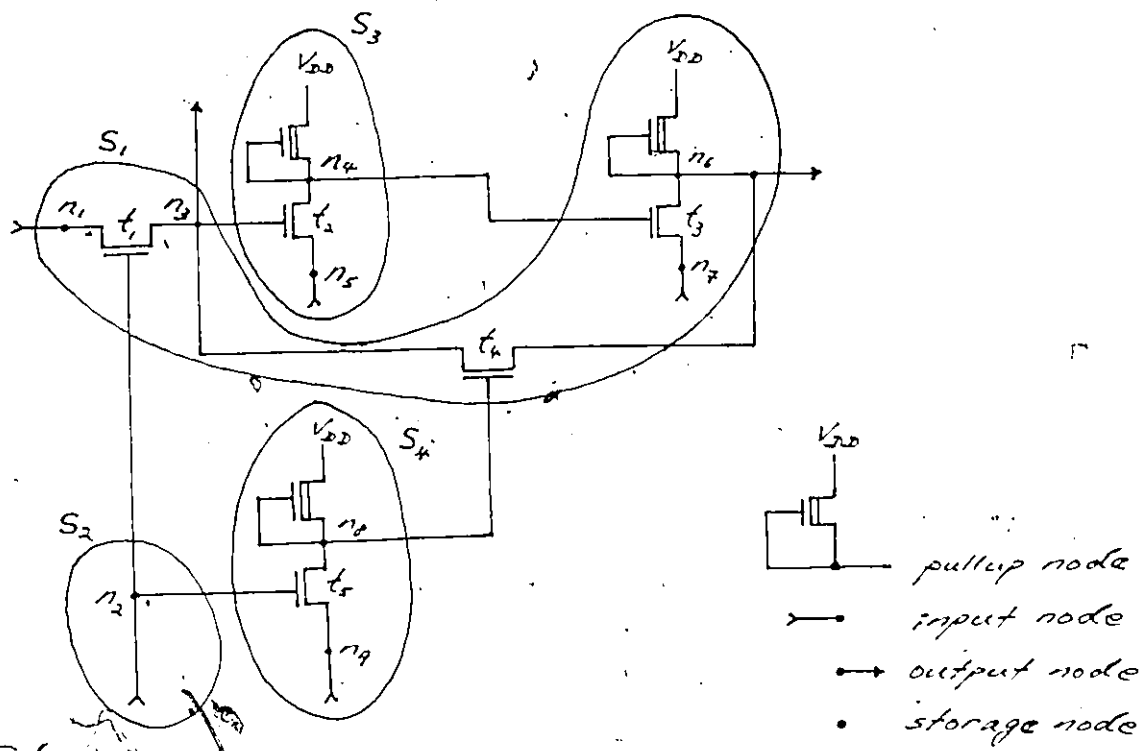
1. The nodes of S_u are obtained by partitioning the graph, formed by creating a vertex for each node and an edge between each pair of vertices that constitutes the source and drain for some transistor, into its connected components.
2. A transistor t_i is in the subnetwork S_u if a node of S_u is a source or drain node of t_i .

All nodes with connections to circuit elements outside the subnetwork are external nodes. The remaining nodes of

subnetwork are internal nodes. Figure 4.3 shows how a network is being partitioned into subnetworks.



(a) Logic diagram of a static register.



(b) Circuit diagram of network after node partitioning.

Figure 4.3: Network partitioning

4.3 Delay Model

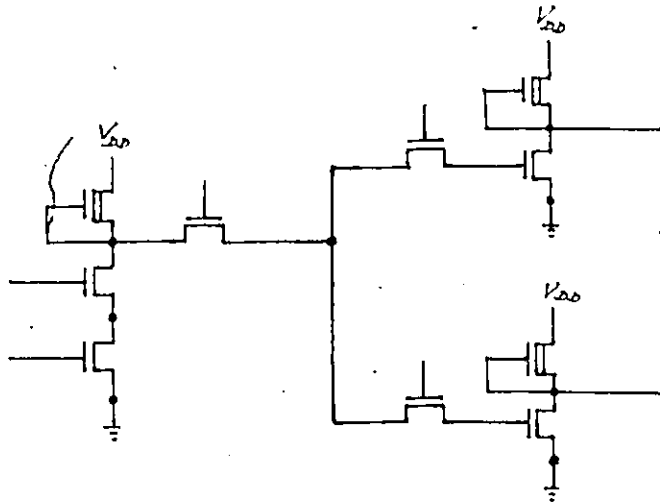
In this section a delay model is described. This delay model is organized around a subnetwork, instead of logic gates. The use of subnetwork permits both logic gates and pass transistors to be handled in a uniform fashion.

In any given time, the modeler considers a change in value at a particular transistor gate, called the trigger. The delay modeler is given the sizes and types of the transistors, the parasitic capacitances and the capacitance of the nodes of each subnetwork. If the trigger is the last transistor to turn on in a subnetwork, as shown in Figure 4.4(b), it may cause certain other transistor gates or output nodes to change value at later times. The modeler is also given information about the waveform at the input. Its job is to use this information to compute the waveform at the output of the subnetwork.

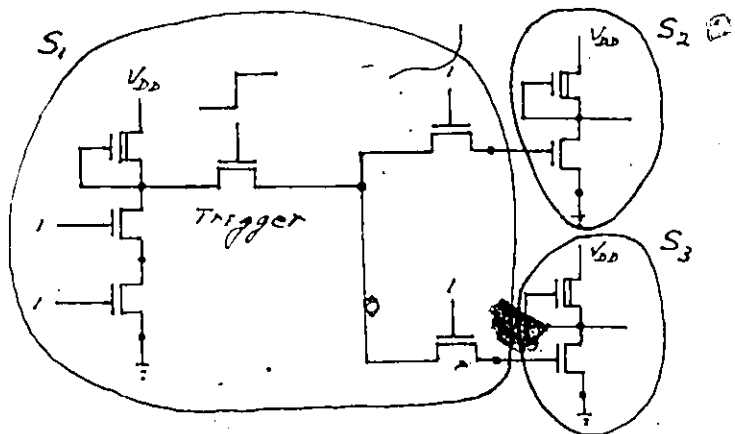
To compute the delay, first, the modeler starts at the source terminal of the trigger transistor and searches through sources and drains of other transistors to find all paths from the trigger source to V_{DD} or GND. For each such path, it then searches from the drain of the trigger transistor through sources and drains to all outputs. The path from the output through the trigger to V_{DD} or GND is used to compute the delay from trigger to output. Since all transistor sizes between trigger and output are known and the capacitances at each node are given, it can compute the delays

from these values by using the equations derived in Section 2.5.

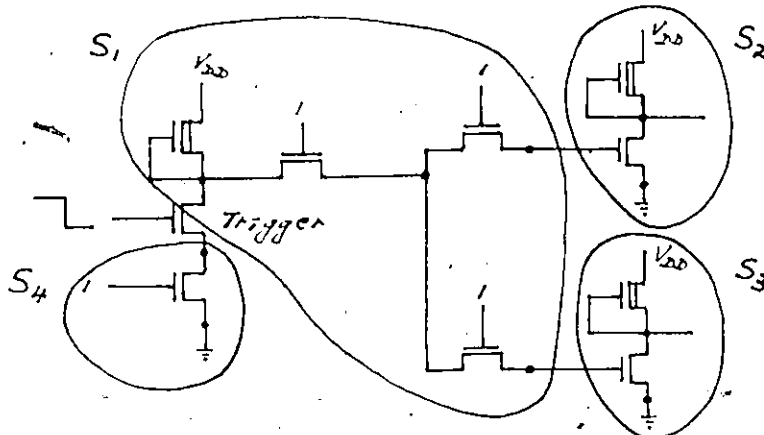
Figure 4.4 (b) shows the trigger transistor and the output nodes of subnetwork S_1 . In the case when the trigger transistor is turned off, as shown in Figure 4.4(c), it does not belong to any subnetwork. Then the path from the output node to the V_{DD} is used to compute the delays.



(a) A given circuit for delay calculation



(b) The trigger transistor is turned ON



(c) The trigger transistor is turned OFF

Figure 4.4: Searching of direct paths.

4.4 Simulation Algorithm

The techniques used in this algorithm are: event-driven, time flow mechanism with time queue array for simulation with variable rise and fall delays, selective trace of active path.

Scheduling of events, tracing of subnetworks for evaluation, and subnetwork evaluation proceed as follows:

1. Event scheduling - When an event occurs at a node, the time scheduled for the event is determined from the delay associated with the transition, and the node identifier together with the new node value is appended to the event list for that time slot.
2. Selective trace - For each node on the event list for the present time, all subnetworks which receive signals on the node as an input are selected for evaluation.
3. Subnetwork evaluation - After a subnetwork is evaluated, all resulting events at the output nodes are to be scheduled at appropriate future times.

The evaluation of new node values reflects an instantaneous reaction of the subnetwork due to the changing input states. This new state of the subnetwork is only a projected state which would be reached only after some delay if the input states were frozen for a sufficiently long time. But the inputs can change before this projected state is reached. When this happens the evolution is directed

towards another state and the previously scheduled delays are revised. Thus, a scheduled transition may be rescheduled or cancelled resulting in a spike condition. A spike is propagated as an X pulse, the pulse width of which is determined from the delay between the events that caused it.

There are three types of transitions and their respective delays for scheduling are as follows:

1. 0 --> 1 and X --> 1 transitions are scheduled with rise delays.
2. 1 --> 0 and X --> 0 transitions are scheduled with fall delays.
3. 0 --> X and 1 --> X transitions are scheduled with unit delay since occurrence of an X during simulation indicates usually an error condition.

Figure 4.5 shows how to keep track of scheduled events at the time queue (TQ). PT is the present time pointer pointing to event list for the present time. The event list contains descriptions for nodes which change states during that time slot. MTEL is the macro time event list or overflow event list, which contains events that are to occur at times which are beyond the range of the current TQ array time frame. Detailed discussion of the lists is presented in the next chapter.

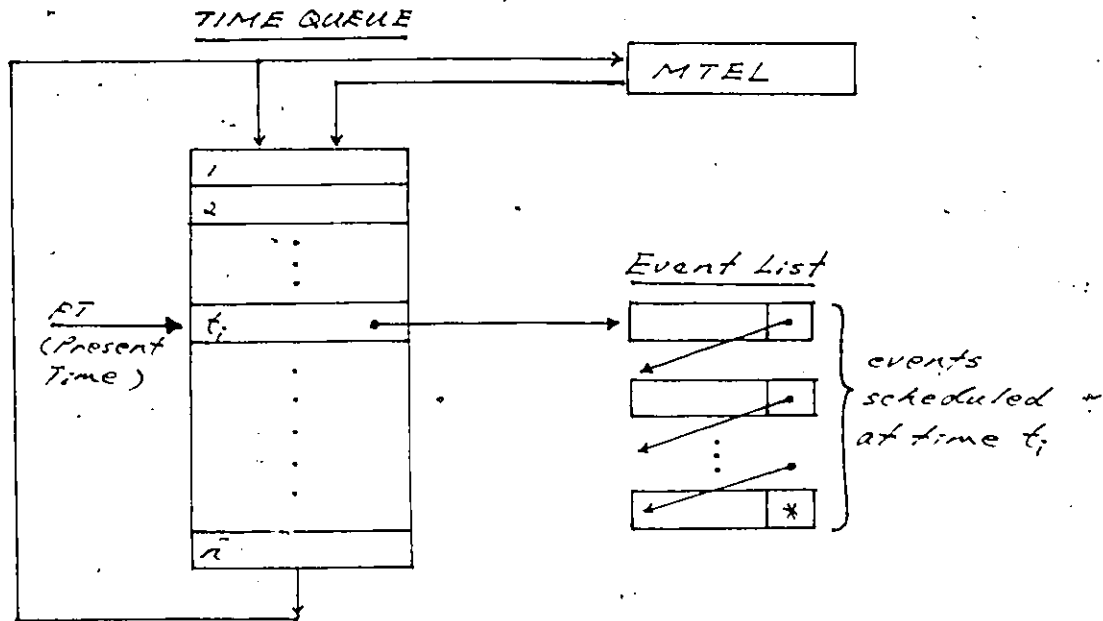


Figure 4.5: Simulation time flow mechanism (Time Queue).

During simulation, errors (e.g. spikes) are indicated by an X. For example, Figure 4.6 shows a circuit with rise delay $t_{PLH} = 5$ units and a fall delay $t_{PHL} = 2$ units. If a negative pulse with a width of 2 units is applied on the input, an abnormal situation occurs. That is, the output change caused by the first input change occurs later than that by the second input change (the first input change causes an output transition from 0 to 1 at time 7 units, the second input change causes an output transition from 1 to 0 at time 6 units). The output would be assigned an error state X with a pulse width of 1 unit.

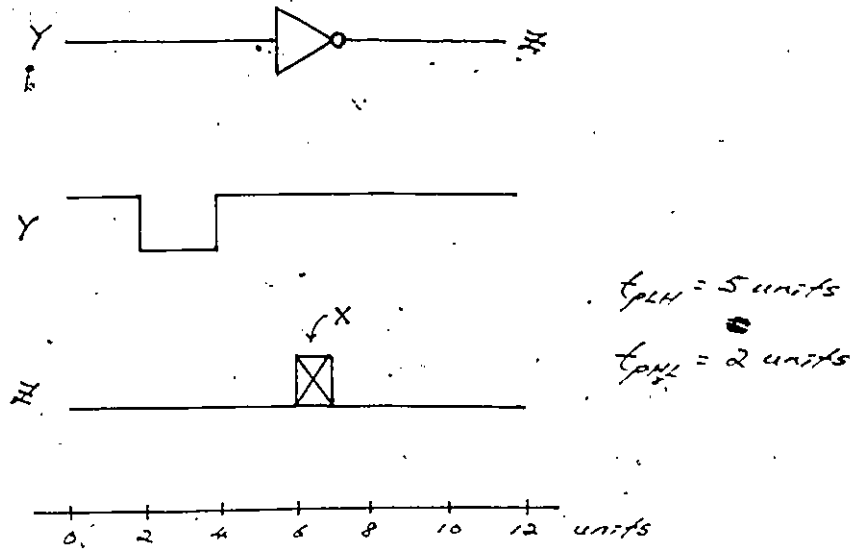


Figure 4.6: Input and output timing diagrams of an error condition.

A simplified event-driven simulation algorithm is flow-charted in Figure 4.7. This algorithm will be presented in a procedural form augmented by explanatory comments.

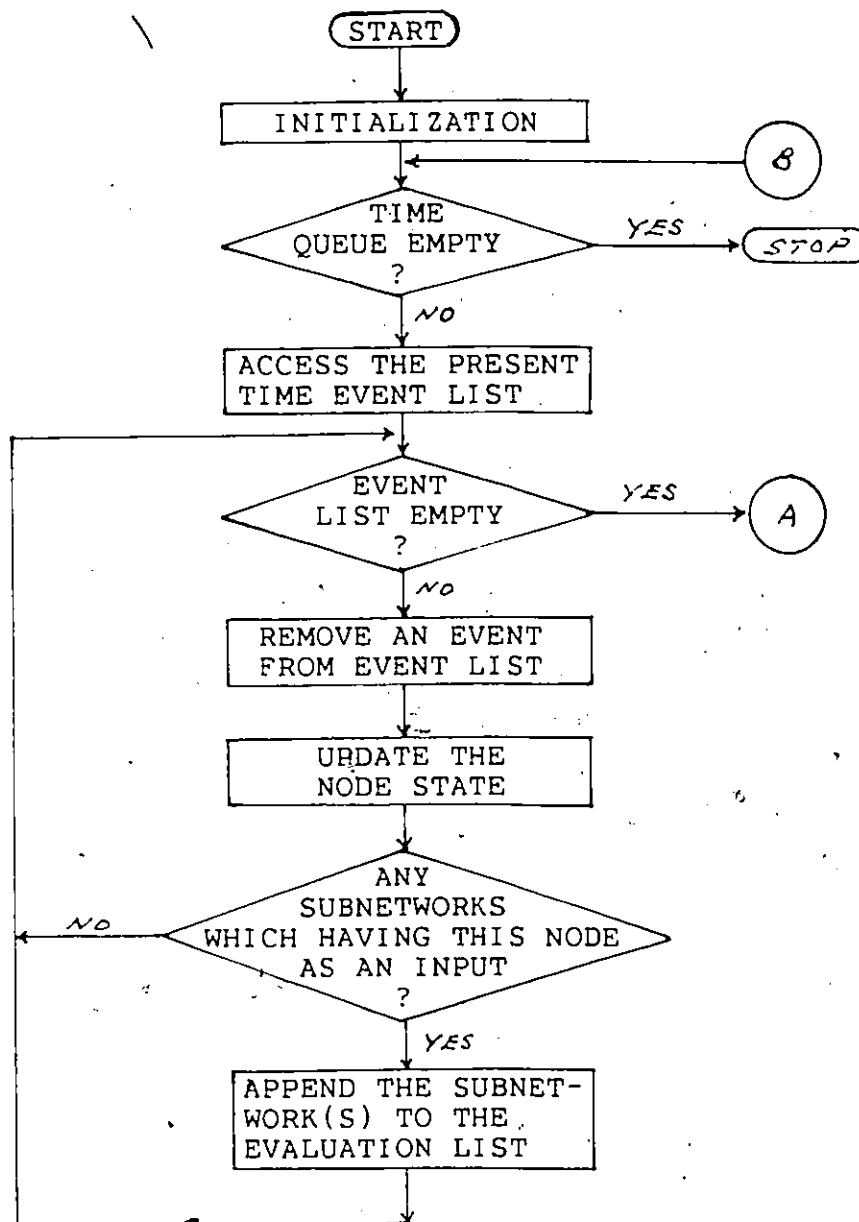


Figure 4.7: Event-Driven Simulation Algorithm.

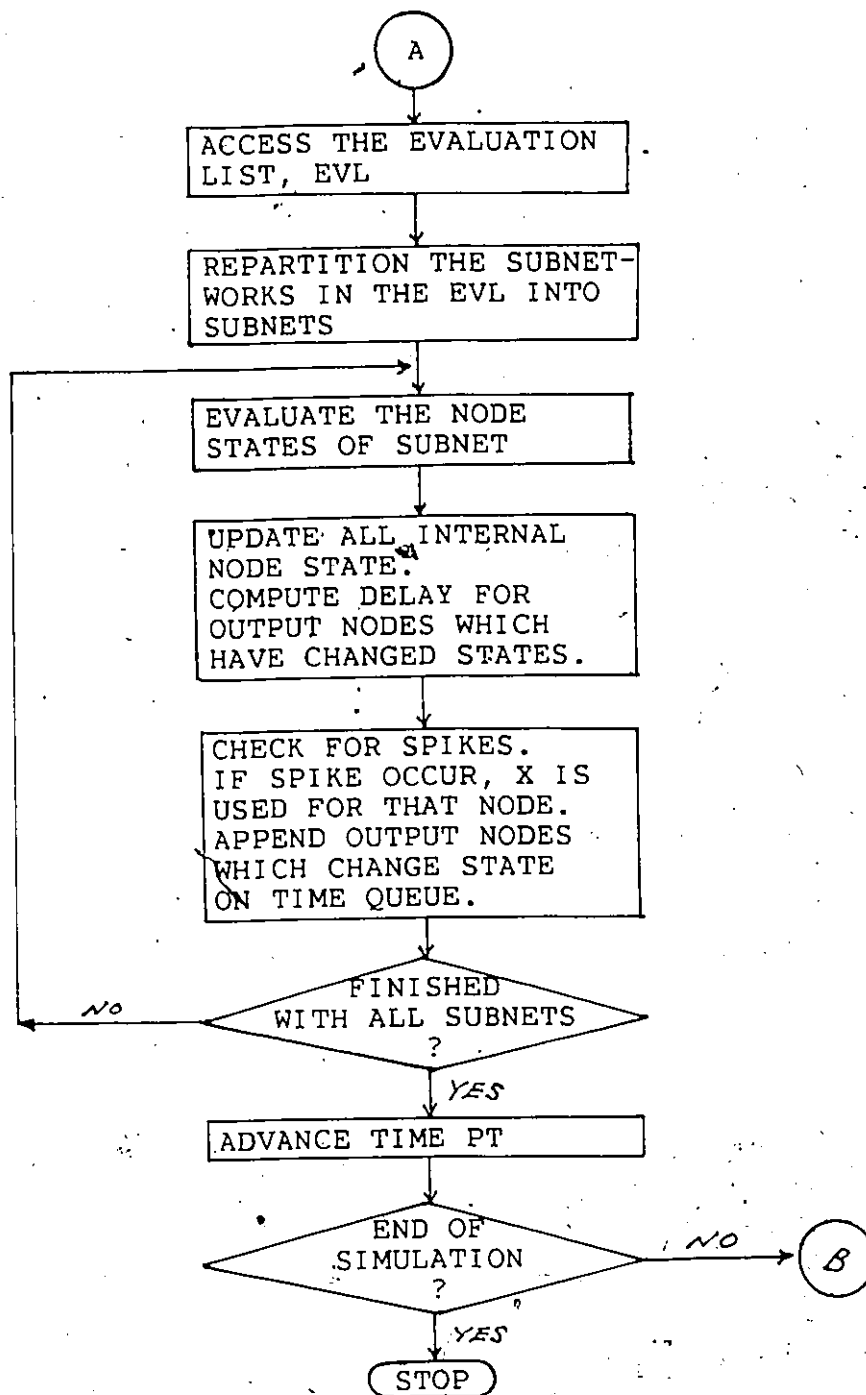


Figure 4.7 (continued)

Procedure SIMULATION is the main body of the algorithm; it shows how the simulation is performed. The procedure is divided into five phases, namely, initialization, node state update, transistor state update and subnetwork repartitioning, subnetwork evaluation, and output scheduling. In the first phase, the given network is partitioned into its connected components called SUBNETWORKS. All nodes in the subnetworks are initialized as follows: Nodes with pullup strength, L , are initialized to 1 and nodes with weak strength, W , are initialized to X . The input list A which contains input events (n_i, y_i, T_j) , where T_j is the time when node n_i has its new state y_i , are scheduled on the Time Queue.

In the second phase, events for the present time is assessed one by one. For each event, the node value is updated according to the change in the event. In the third phase, the state of transistors for which this node is their gate terminals is updated by using the procedure SET-TRANS. Updating a node value may cause some subnetworks, which having this node as an input, to be added to the evaluation list EVL. All the nodes in a subnetwork on the EVL form an undirected graph which has a vertex for each node and an edge for each transistor which is in the "closed" or "unknown" state. The connected components of this graph becomes SUBNETS.

In the fourth phase, the node states of each subnet is evaluated by procedure NODESTATE. Delays for output nodes which have changed states are computed. The last phase of evaluation is to schedule new events on the Time Queue. Evaluation of state and delay are described in later sections.

Procedure APPEND adds a subnetwork onto the evaluation list only if the given subnetwork is not already on the list. Then, this subnetwork is deleted from SUBNETWORKS, because it will be repartitioned into new subnetworks during the execution of EVL.

Input: A network Ω , a network configuration M and an input list A, containing sequence of input events to be simulated $\langle n_i, y_i, T_j \rangle$.

Output: M is updated by simulating the input events in A.

procedure SIMULATION (Ω, M, A);

begin

(* initialization phase *)

G <--- form an undirected graph with $V = \{n_i\}$ and

$E = \{ \langle i, j \rangle \mid \text{for some } t_g : \text{SOURCE}(t_g) = n_i \text{ and } \text{DRAIN}(t_g) = n_j \}$;

SUBNETWORKS <--- PARTITION(G);

for each n_i such that $f_i = 'L'$ do $s_i = 1$;

for each n_i such that $f_i = 'W'$ do $s_i = X$;

for each $\langle n_i, y_i, T_j \rangle$ in A do

TQ <--- $\langle n_i, y_i \rangle$ at time T_j ;

EVL = 0;

for all $n_i \in PT$ do

if $s_i \neq y_i$ then

begin (* node state update phase *)

$s_i = y_i$;

if for some t_g such that $\text{DRAIN}(t_g) = n_i$ and n_i is input to some S_u then

APPEND(EVL, S_u);

if for some t_g such that $\text{Gate}(t_g) = n_i$ then

begin (* transistor state update *)

z_g <--- SET_TRANS(TTYPE(t_g), s_i);

```

    if  $n_i$  input to some  $S_u$  then
        APPEND(EVL,  $S_u$ )
    else
        for some  $t_g$  such that SOURCE( $t_g$ )  $\in S_v$ 
        and DRAIN( $t_g$ )  $\in S_w$  do
            begin
                APPEND(EVL,  $S_v$ );
                APPEND(EVL,  $S_w$ )
            end
        end
    end

G <--- form an undirected graph with  $V = \{ n_i \mid n_i \in \text{EVL} \}$ 
and  $E = \{ \langle i, j \rangle \mid \text{for some } t_g : \text{SOURCE}(t_g) = n_i, \text{DRAIN}(t_g) = n_j \text{ and } Z_g = \text{'closed' or 'unknown'} \}$ ;
SUBNETS <--- PARTITION(G); (* subnetwork repartitioning *)
for all  $S_i \in \text{SUBNETS}$  do
    begin
        NODESTATE of  $S_i$ ; (* subnetwork evaluation phase *)
        .Delays of output nodes which have changed
        state in  $S_i$ ;
        .Check for spikes;
        (* output scheduling phase *)
        Schedule events with delay delta at  $PT + \Delta$ ;
        SUBNETWORKS <--- SUBNETWORKS  $\cup \{S_i\}$ 
    end
while not end of simulation do
    increment PT

```

end.

procedure APPEND(EVL, S_x);

begin

if $S_x \in$ EVL then

begin

EV L $\leftarrow$ EV L $\cup \{S_x\}$;

remove S_x from SUBNETWORKS

end

end

Procedure NODESTATE evaluates the node states of the given subnet containing a set of nodes and a set of closed- and unknown-state transistors (transistors with 1's or X's at their gate terminals). At the beginning, all pullup nodes are initialized to 1. Then, we consider the undirected graph containing a vertex for each node in the subnet and an edge for each transistor which is in the "closed" state. The connected components of the graph partition the set of nodes into groups called GROUPS. The state of each of the group is computed by the procedure STATE.

If the subnet contains X-transistors (having X on their gate terminal), then we must look at potential interactions between the groups. The state of an X-transistor is unknown: it may be opened, closed or somewhere in between. Hence, if a node has a unique state regardless of the behaviours of the X-transistors in the subnet, then the node will be set to this state; otherwise, it will be set to X.

Thus far, we have computed the state of each group assuming all X-transistors in the subnet are set "open". The next step is to analyze the groups and set the state of a group to X if some combination of X-transistors could be set to "closed" and result in a different group state. First a supergraph is formed containing a vertex for each group and an edge between a pair of vertices if an X-transistor connects two nodes in the corresponding groups. The connected components of the supergraph is called SUPERGROUP (super-group contains a set of groups linked by X-transistors).

If a supergroup contains only one element (one group), that means the subnet does not contain X-transistor, and no further analysis is required. Otherwise, the state and strength of the supergroup is computed by the procedure SUPERSTATE. Any group with a state different from the supergroup state must be set to X, because its state would be changed if all X-transistors were set to "closed". All the groups which have an X-state are called "poisoned" groups. Furthermore, a poisoned group can spread the X-state to its neighbor, unless the neighbor is stronger.

Input: A subnet S_i .

Output: The new states of subnet S_i .

procedure NODESTATE (S_i);

begin

for each n_i such that $f_i = "L"$ do $s_i := 1$;

$G \leftarrow$ form an undirected graph with $V = \{n_i\}$ and

$E = \{ \langle i, j \rangle \mid \text{for some } t_g : \text{SOURCE}(t_g) = n_i ,$

$\text{DRAIN}(t_g) = n_j \text{ and } Z_g = \text{'closed'} \} ;$

$\text{GROUPS} \leftarrow \text{PARTITION}(G)$;

for each $G_j \in \text{GROUPS}$ do

$\text{strength}(G_j), \text{state}(G_j) \leftarrow \text{STATE}(G_j)$;

$\text{SG} \leftarrow$ form an undirected graph with $V = \{G_j\}$ and

$E = \{ \langle i, j \rangle \mid \text{for some } t_g : \text{SOURCE}(t_g) \in G_i \text{ and}$

$\text{DRAIN}(t_g) \in G_j \text{ and } Z_g = \text{'unknown'} \} ;$

if $|\text{SG}| > 1$ then

begin

$Y \leftarrow \text{SUPERSTATE}(\text{strength}, \text{state}, \text{SG})$;

$P \leftarrow \{G_j \in \text{SG} \mid \text{state}(G_j) \neq Y\}$;

$\text{POISON}(P, \text{SG}, \text{strength})$;

for each $G_j \in P$ do $\text{state}(G_j) \leftarrow X$

end

for each $G_j \in \text{GROUPS}$ do

for each $n_i \in G_j$ do

if $f_i \neq "D"$ and $s_i \neq \text{state}(G_j)$ then

$y_i \leftarrow \text{state}(G_j)$;

for each $n_i \in S_i$ do

if $s_i \neq y_i$ and $\text{NTYPE}(n_i) \neq \text{'external'}$ then

```
si <-- yi
```

```
end
```

Procedure STATE computes the state and strength of a given group. In this procedure, the strongest node(s) in the group are inspected, where node strengths are ordered as Driver > Pullup > Weak. The strength of the group is defined as the strength of its strongest node(s). If the states of the strongest nodes are equal, the group state becomes this state; otherwise it becomes X, See Table 4.2.

Procedure SUPERSTATE closely resembles the procedure STATE. The strength of the supergroup is computed as the strength of its strongest group(s). The state of the supergroup is computed as the state of the strongest group(s), if they are equal, and as an X if they are not.

		node(i)		
		Driver (D)	Pullup (L)	Weak (W)
node(j)	Driver (D)	D	D	D
	Pullup (L)	D	L	L
	Weak (W)	D	L	W

(a) Group strength

		node(i)								
		Driver (D)			Pullup (L)			Weak (W)		
node(j)		0	1	X	0	1	X	0	1	X
Driver (D)	0	0	X	X	0	0	0	0	0	0
	1	X	1	X	1	1	1	1	1	1
	X	X	X	X	X	X	X	X	X	X
Pullup (L)	0	0	1	X	0	X	X	0	0	0
	1	0	1	X	X	1	X	1	1	1
	X	0	1	X	X	X	X	X	X	X
Weak (W)	0	0	1	X	0	1	X	0	X	X
	1	0	1	X	0	1	X	X	1	X
	X	0	1	X	0	1	X	X	X	X

(b) Group state

Table 4.2
: Group strength and state table.

Input: A group G_X .

Output: The strength and state of G_X .

procedure STATE(G_X);

begin

k $\leftarrow$ null; (* Driver > Pullup > Weak > null *)

y $\leftarrow$ X;

for each $n_i \in G_X$ do

if $f_i > k$ then

begin

k $\leftarrow$ f_i ;

y $\leftarrow$ s_i

end

else

if $f_i = k$ and $s_i \neq y$ then

y $\leftarrow$ X

end

Input: A supergroup, strength and state of each group in
the supergroup.

Output: State of supergroup.

procedure SUPERSTATE (strength, state, SG);

begin

K $\leftarrow$ null; (* Driver > Pullup > Weak > null *)

Y $\leftarrow$ X;

for each $G_i \in SG$ do

if strength(G_i) > K then

begin

K $\leftarrow$ strength(G_i);

Y $\leftarrow$ state(G_i);

end

else

if strength(G_i) = K and state(G_i) $\neq$ Y then

Y $\leftarrow$ X

end

In the procedure POISON, the initial set of poisoned groups P , is expanded to the neighboring groups. A neighboring group can be poisoned by these poisoned groups, unless the neighbor is stronger.

Input: An initial set of poisoned groups P , a supergroup SG ,
and strength: an array indicating the strength of
each group.

Output: P is expanded.

```
procedure POISON ( $P$ ,  $SG$ , strength);
```

```
  begin
```

```
    pstrength  $\leftarrow$  strength;
```

```
     $B \leftarrow P$ ;
```

```
    while  $B \neq 0$  do
```

```
      begin
```

```
         $G_j \leftarrow$  an element of  $B$  with maximal strength;
```

```
         $B \leftarrow B - \{G_j\}$ ;
```

```
        for each  $G_k$  connected to  $G_j$  by an X-transistor do
```

```
          if  $\text{pstrength}(G_k) < \text{pstrength}(G_j)$ 
```

```
          or  $(\text{pstrength}(G_k) = \text{pstrength}(G_j) \text{ and } G_k \notin P)$  then
```

```
            begin
```

```
               $P \leftarrow P \cup \{G_k\}$ ;
```

```
               $B \leftarrow B \cup \{G_k\}$ ;
```

```
               $\text{pstrength}(G_k) \leftarrow \text{pstrength}(G_j)$ 
```

```
            end
```

```
          end
```

```
    end
```

Procedure PARTITION is used for partitioning an undirected graph into its connected components. This algorithm is a variation of the depth-first search algorithm of Aho, Hopcroft and Ullman [2].

Input: A graph $G=(V,E)$ where V is a set of vertices, and E is a set of edges.

Output: A set of connected components.

```
procedure PARTITION(G);
```

```
  begin
```

```
    j  $\leftarrow$  1;
```

```
    for all  $v_i$  in  $V$  do mark  $v_i$  "new";
```

```
    while there exists a vertex  $v_i$  in  $V$  marked "new" do
```

```
      begin
```

```
         $S_j \leftarrow \{v_i\};$ 
```

```
        SEARCH( $S_j$ ,  $v_i$ );
```

```
        j  $\leftarrow$  j + 1
```

```
      end
```

```
    end
```

```
procedure SEARCH( $S,v$ );
```

```
  begin
```

```
    mark  $v$  "old";
```

```
    for each vertex  $w$  adjacent to  $v$  in  $G$  do
```

```
      if  $w$  is marked "new" then
```

```
        begin
```

```

    S <-- S U {w};
    SEARCH(S,w);
  end
end

```

The procedure DELAY computes the delay times for each output node, which has changed state, of the subnet S_i by using the equations which have been derived in previous sections. The procedure first checks whether the future state of the output node is a 1, 0 or X. If the future state is a 1, a direct path is found between the output node and the pullup node or the input node, and the rise delay is computed by using the appropriate rise delay equations. If the future state is a 0, a direct path is found between the output node and the pullup node or input node, an equivalent super-driver-transistor is derived, and the fall delay is computed by using the appropriate fall delay equations. If the future state is an X, a unit delay is assumed because occurrence of an X during simulation usually indicates an error condition for which pessimism dictates the shortest possible delay. In computing delays, capacitances from the side branches are assumed to be connected to the branch nodes (see Figure 4.8). This approach will reduce the tree structure into a chain structure.

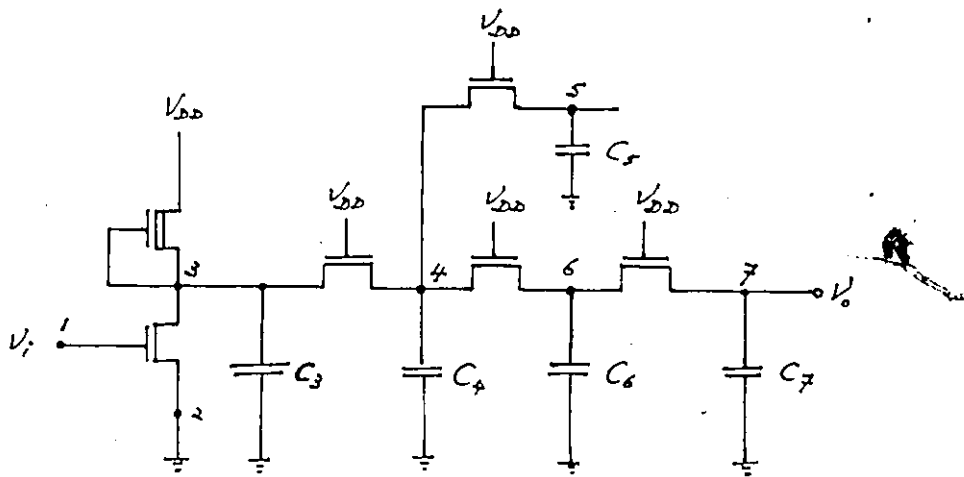


Figure 4.8 : Side capacitances are assumed to be connected to the branch nodes. In computing delays, for direct path from node 3 to node 7, side capacitance C_5 is assumed to be connected to node 4 (total capacitance at node 4 is $C_4 + C_5$).

Input: A subnet S

Output: Delays of each output node which has changed state.

procedure DELAY(S);

begin

for each $n_i \in S$ do

if NTYPE(n_i) = 'external' and $s_i \neq y_i$ then

if $y_i = 1$ then

begin

search for a direct path between n_i and

pullup node or input node;

compute the rise delay (delta)

end

else

if $y_i = 0$ then

begin

substitute the driver transistors with

an equivalent super-transistor;

search for a direct path between n_i and

pullup node or input node;

compute the fall delay (delta)

end

else

assign a unit delay (delta)

end

Chapter.V

IMPLEMENTATION

5.1 Introduction

As we have discussed in earlier chapters, there are a number of basic considerations which dictate the entire functioning of a simulator, as well as the system flexibility. Primary among these considerations is the handling of the logic network data and the basic simulation mechanism. There are two basic methods for digital logic simulation, compiled simulation and table-driven simulation. Compiled simulation could not provide the timing accuracy desired, hence, a table-driven simulation is used in this simulator.

For design verification, detection of timing problems is a major objective; hence, the selection of an appropriate time flow mechanism is of considerable importance. Since the decisions with respect to the table structure and time flow mechanism are considered to be of major importance, the following detailed discussion is provided.

This multiple delay switch-level simulator has been implemented, based on the algorithm described in the previous chapter, on the Amdahl 470/V8 system as a series of Pascal program. Executable version of the program is given in Appendix D.

5.2 Data Structures

In a table-driven simulator the circuit is represented by a set of tables indicating the important attributes of each node and transistor, such as:

1. the type of node
2. the state of the node
3. the delay at the node
4. the capacitance at this node,
5. the state of the transistor
6. the drain, gate and source of the transistor
7. transistors for which this node is the gate terminal
(fanouts)
8. transistors which connect this node to other nodes
(interconnects)

Numerous options exist for the implementation of a particular table structure. Each of these table structures has its pros and cons. One particular table structure that is general, effective and efficient is presented here.

The overall table configuration is shown in Figure 5.1. As can be seen from the figure, pointers and linked lists are extensively used. The node table contains all the information about each node and the interconnection pointers for each node. The transistor table contains pointers to the drain, gate and source nodes of each transistor. The fanoutset and interconset tables contain pointers to the respective fanout and interconnection transistors of each

node: fanout transistors are transistors for which this node is the gate node, interconnection transistors are transistors which connect this node to other nodes. The timing table contains the timing information of the node for delay calculation and spike analysis.

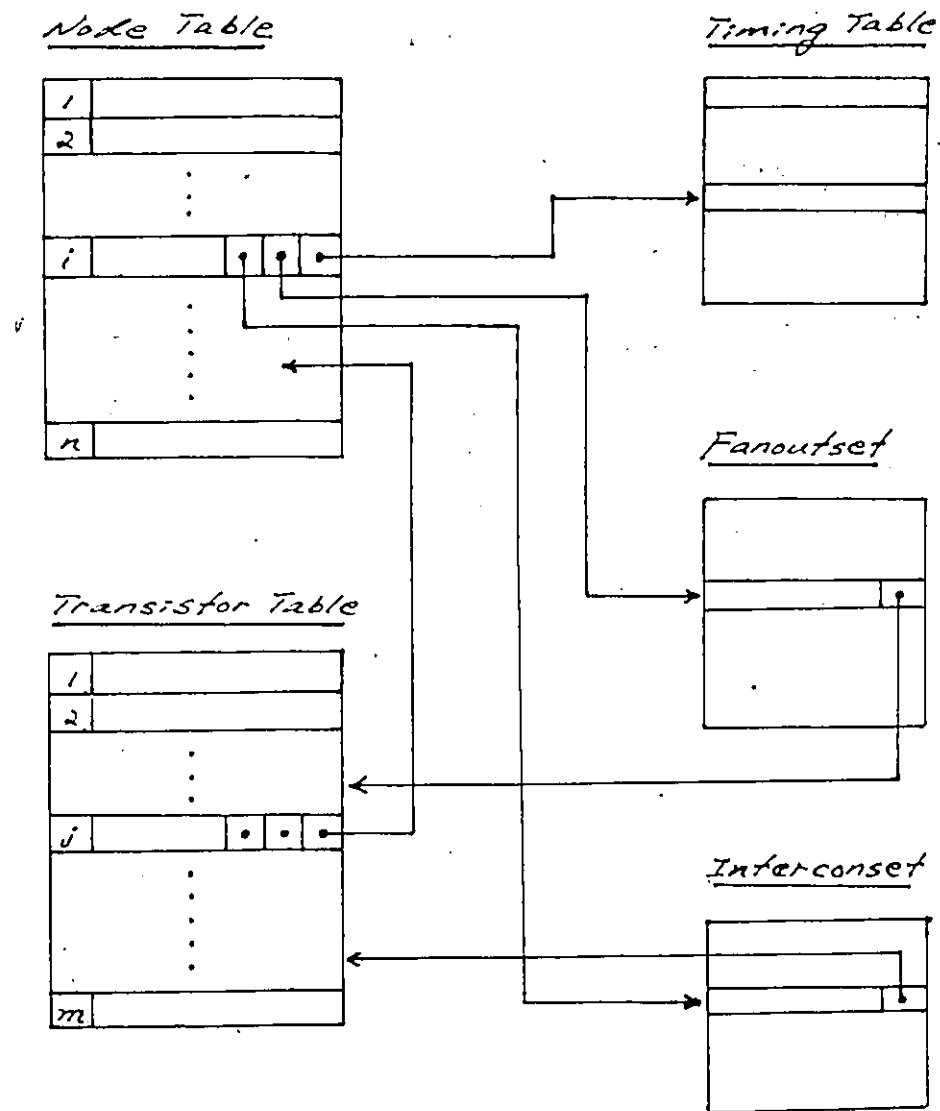


Figure 5.1 : Overall table configuration and interaction

The node table shown in Figure 5.2 contains information about the nodes of a circuit. Each node occupies three words of information. Detailed description of each field of these words is given in Figure 5.3.

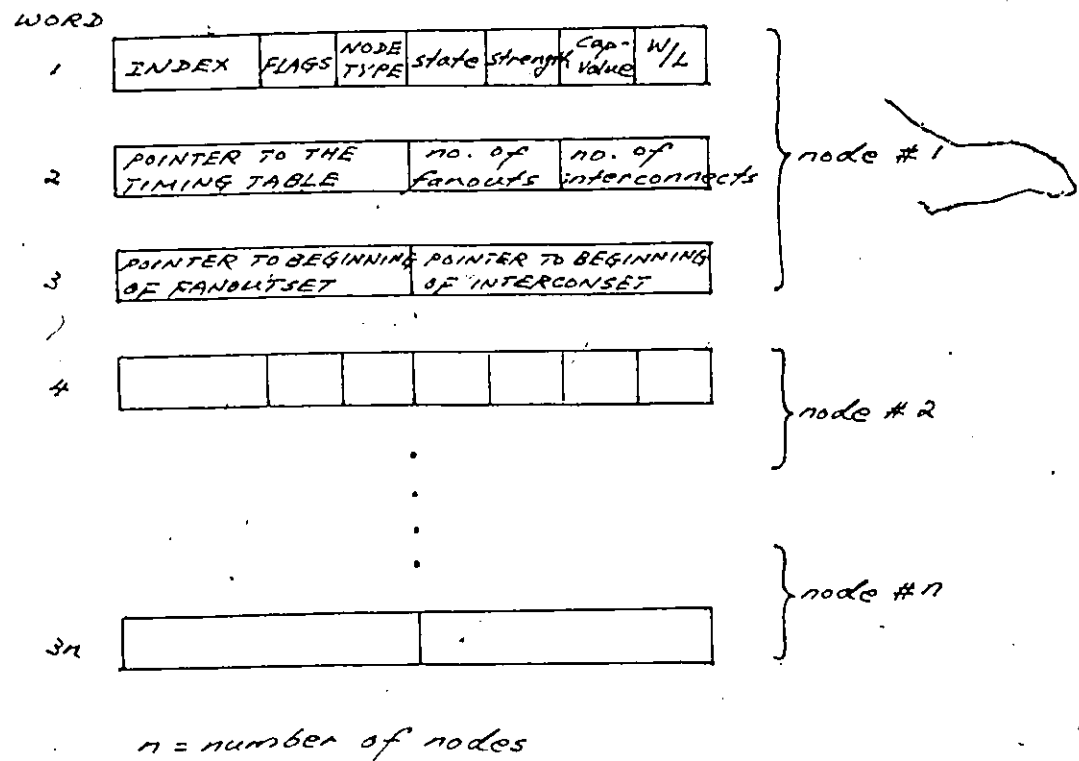


Figure 5.2 : Node table

Field	Description	Usage
index	indicates the node number	argument in vector arrays to address the piece of information desired
flags	indicators	checking of certain condition
node type	type of node	state evaluation
state	node state	state evaluation
strength	node strength	strength evaluation
cap-value	node capacitance	delay calculation
W/L	width and length of the load transistor; for pullup node only	delay calculation
pointer to the timing table	pointer points to the timing table	delay calculation and spike detection
no. of fanouts	number of fanout transistors	event scheduling
no. of interconnect	number of interconnect transistor	state evaluation
pointer to beginning of fanoutset	pointer points to the beginning of the fanoutset	event scheduling
pointer to beginning of interconset	pointer points to the beginning of the interconset	state evaluation

Figure 5.3 : Description of node table

The transistor table shown in Figure 5.4 contains information about the transistors of a circuit. Each transistor occupies three words of information. Detailed description of each field of these words is given in Figure 5.5.

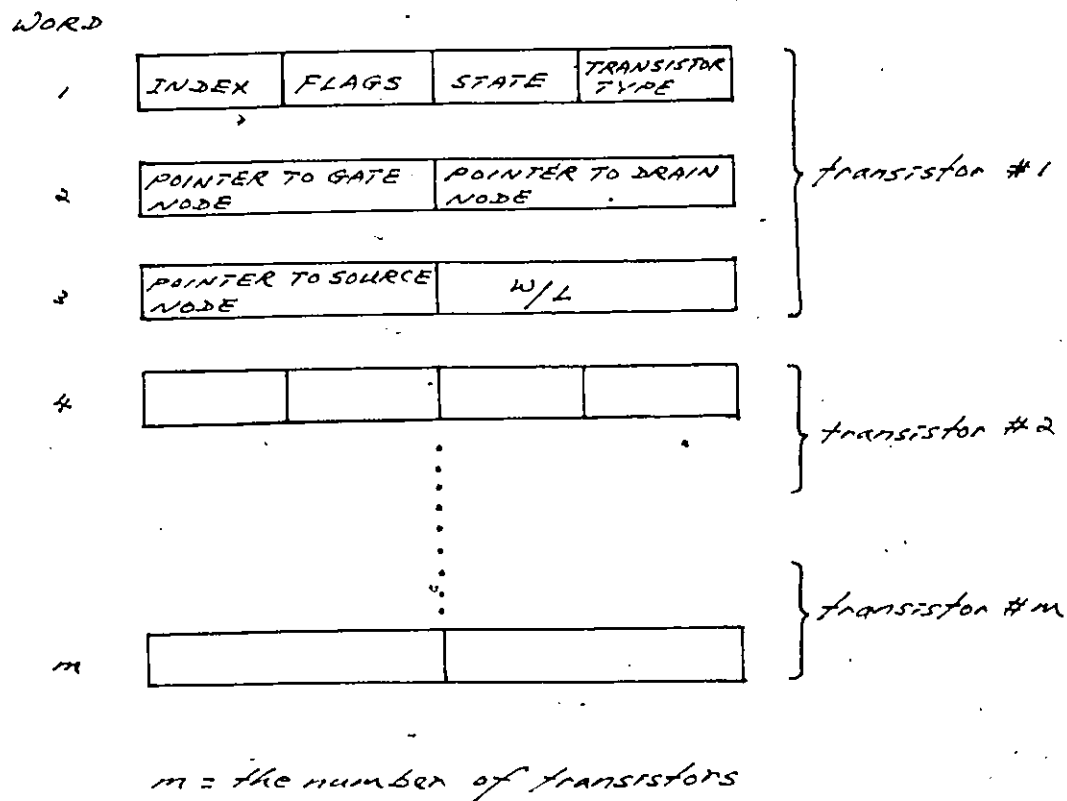


Figure 5.4 : Transistor table

Field	Description	Usage
index	indicates the transistor number	argument in vector arrays to address the piece of information desired
flags	indicators	checking of certain condition
state	transistor state	state evaluation
transistor type	type of transistor	state evaluation
pointer to gate node	pointer points to the gate terminal	state evaluation
pointer to drain node	pointer points to the drain terminal	state evaluation
pointer to source node	pointer points to the source terminal	state evaluation
W/L	width and length of the transistor channel	delay calculation

Figure 5.5 : Description of transistor table

The fanoutset table and interconset table, shown in Figure 5.6 and Figure 5.7 respectively, are closely associated with the node table. As we have seen previously, two of the entries in the node table are pointers to the fanoutset and interconset tables, which in turn contains pointers to the transistor table entries of interest.

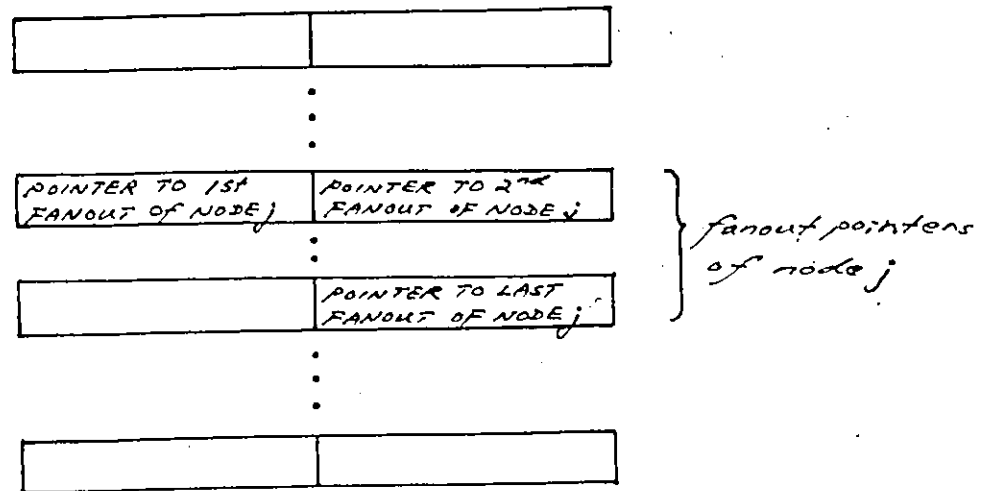


Figure 5.6 : Fanoutset table

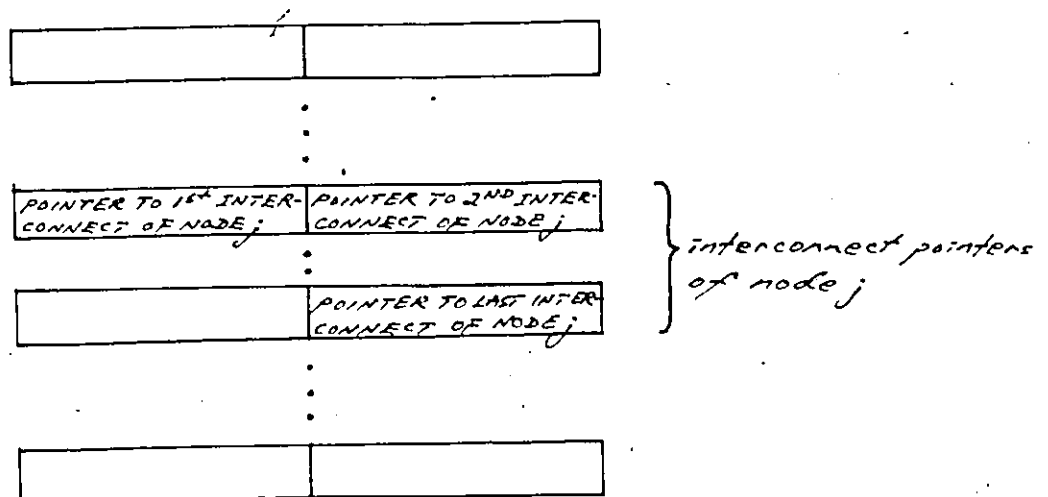


Figure 5.7 : Interconset table

7

The timing table, as shown in Figure 5.8, stores the timing information of each external (input and output) node. These timing information can be used to calculate the delays and checking of spikes. The first word contains the rise time and rise delay of the node. The second word contains the fall time and the fall delay of the node. The third word stores the times and the future states of the node, or zero if no future state pending for this node.

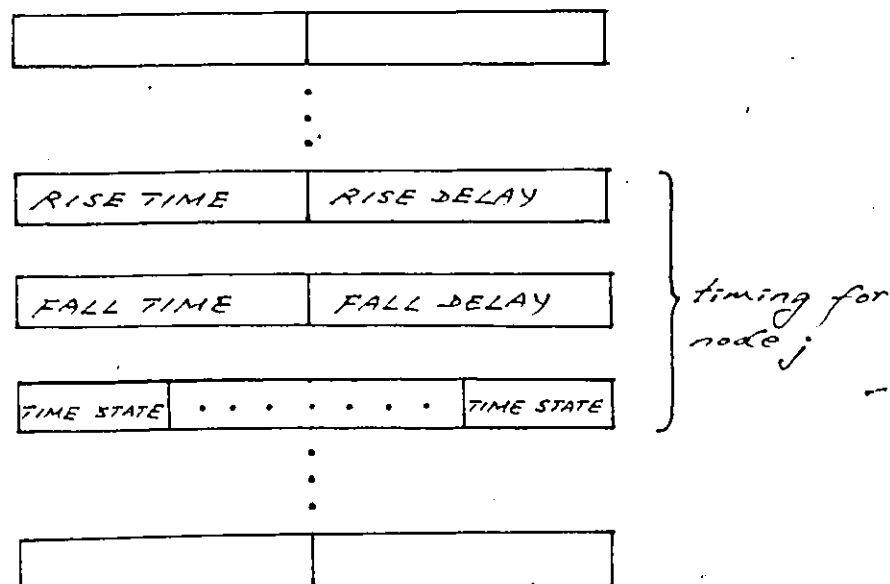


Figure 5.8 : Timing table

5.3 Time Flow Mechanism

Figure 5.9 shows the time flow mechanism used in this multiple delay simulator. The TQ (Time Queue) array is the basic element of storage in the time flow mechanism. Each row represents a discrete point in the simulation time base. Time in the simulator can move forward only by a fixed increment. Each entry in the TQ array contains pointers to a list of events which are to occur at that instant in time.

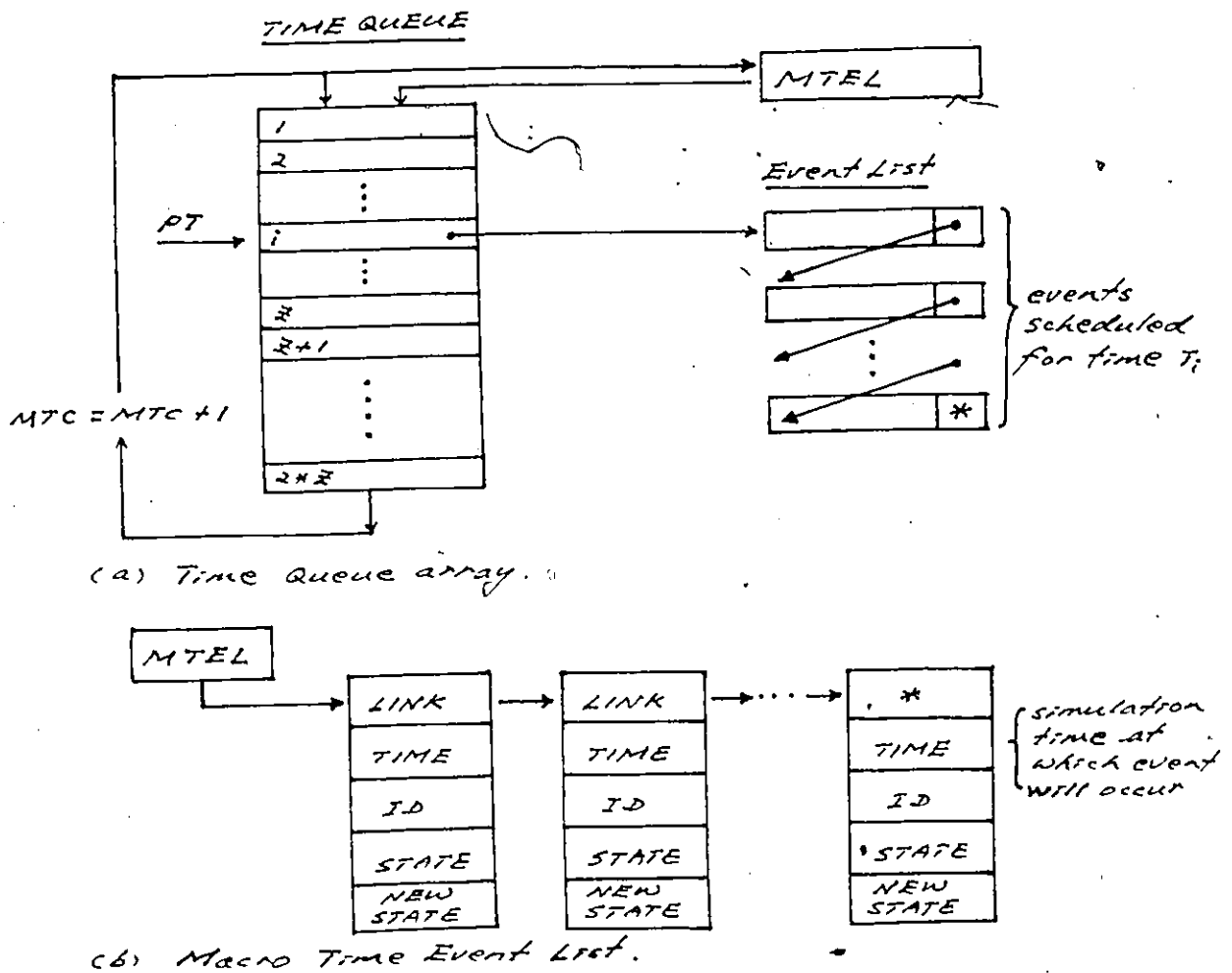


Figure 5.9 : Simulation time flow mechanism

There is one storage area, called the macro time event list (MTEL), used to contain events that are to occur at points in time which are beyond the range of the current TQ array time frame. Consider the TQ array to be indexed from 1 to $2*Z$. Let PT be a variable denotes the "present time" in the TQ array being processed and MTC be a variable starting at zero which denotes the number of cycles which have been made through the TQ array. Then, the simulation time is equal to the expression $(Z*MTC)+PT-1$ and the time frame of the TQ array is from $(MTC*Z)$ to $(MTC*Z)+(2*Z)-1$ inclusive. The MTEL is ordered on the time of occurrence of the events.

At entry $Z+1$ of the TQ array, an event known as the MTEL update is always scheduled to occur as the first event at that point in time. The action of this event is as follows:

1. Entries $Z+1$ through $2*Z$ replace entries 1 through Z in the TQ array and entries $Z+1$ through $2*Z$ are zeroed out.
2. MTC is incremented by one.
3. PT is set to 1.
4. The MTEL update event is scheduled at $Z+1$.
5. The MTEL is searched to determine if any events scheduled to occur between $(MTC*Z)+Z+1$ and $(MTC*Z)+(2*Z)$ inclusive. If such events, they are removed from the MTEL and placed in lists pointed to by the pointers on the proper entry in the TQ array.

The scheduling of an event is done by placing the event on the proper list. If the event is to occur within the time frame of the TQ array, then it is put on a list pointed to by a TQ array entry. If the event is to occur beyond the current time frame of the TQ array, then it is inserted in the MTEL in a manner so as to retain the ordering of the MTEL.

5.4 Examples

The algorithms described in the previous chapter have been implemented on the Amdahl 470/V8 system as a series of Pascal program, and a program listing is given in Appendix D. A number of NMOS circuits have been simulated by this program. A few examples are given below.

Example 5

The following circuit, with parallel and series driver transistors, is simulated. Node (2) and (3) are the input nodes. Node (10) is the output node. The output waveform at node (10) produced by this simulator is shown in solid line in Figure 5.10. For comparison purposes the waveform in dotted line is the ones produced by SPICE simulation program.

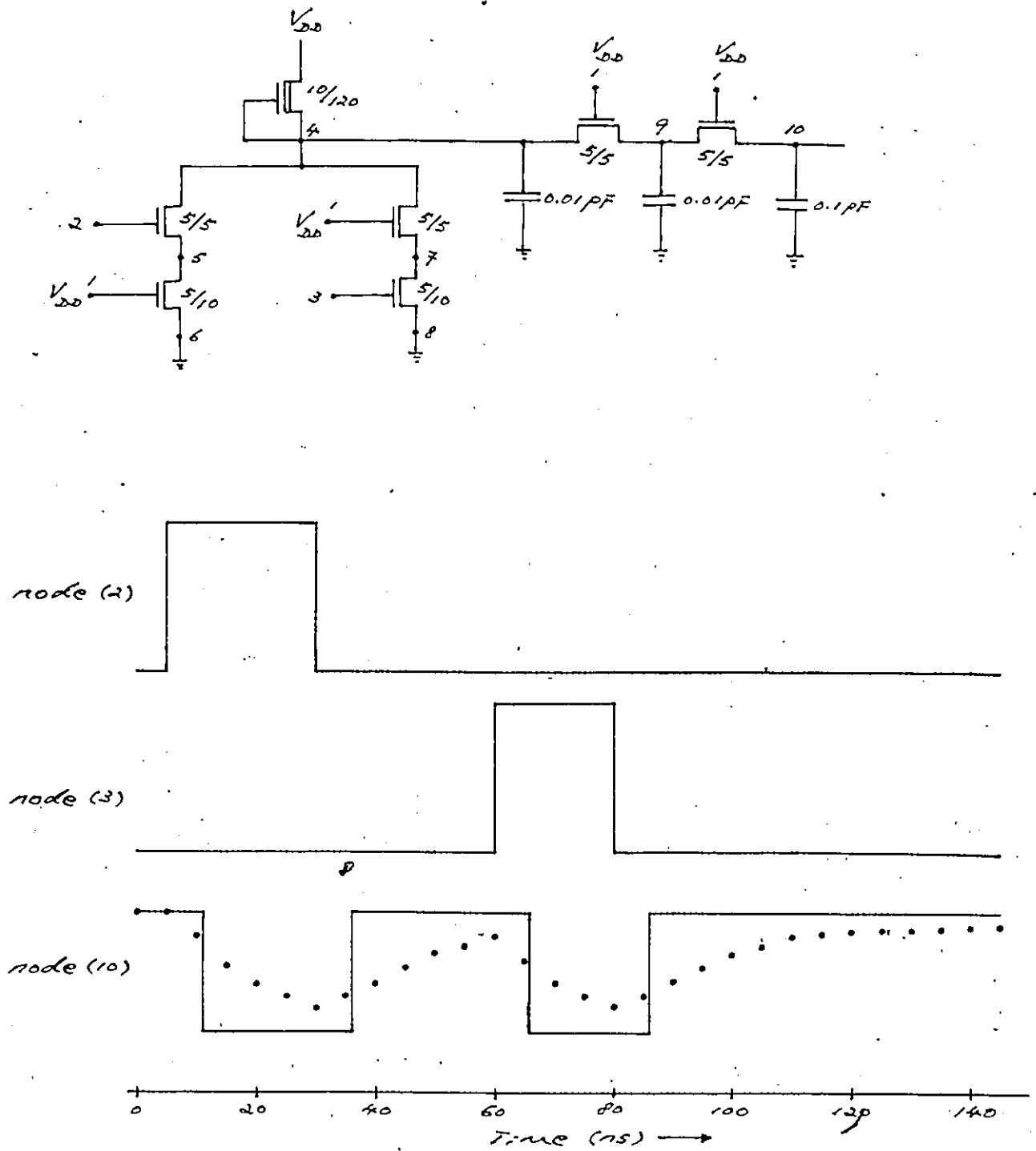
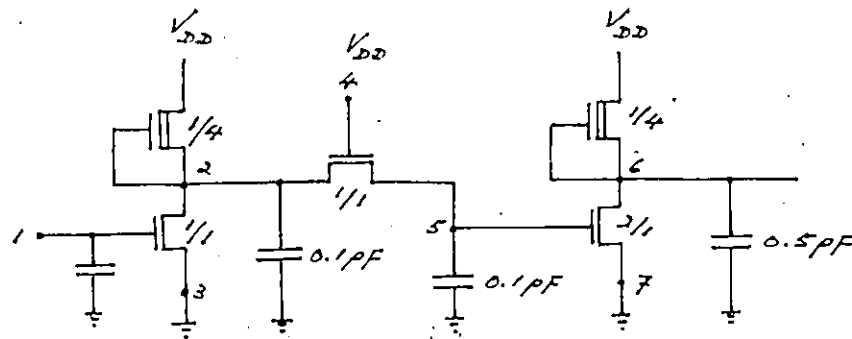


Figure 5.10 : Input and output waveforms for Example 5

Example 6

Example 6 is an inverter pair coupled by a pass transistor, as shown below. Node (1) is the input node and node (6) is the output node. The output waveform produced by this simulator is shown in solid line in Figure 5.11. For comparison purposes the waveform in dotted line is the ones produced by SPICE simulation program. This example is presented to illustrate the ability of this simulator to handle error condition (X-state).



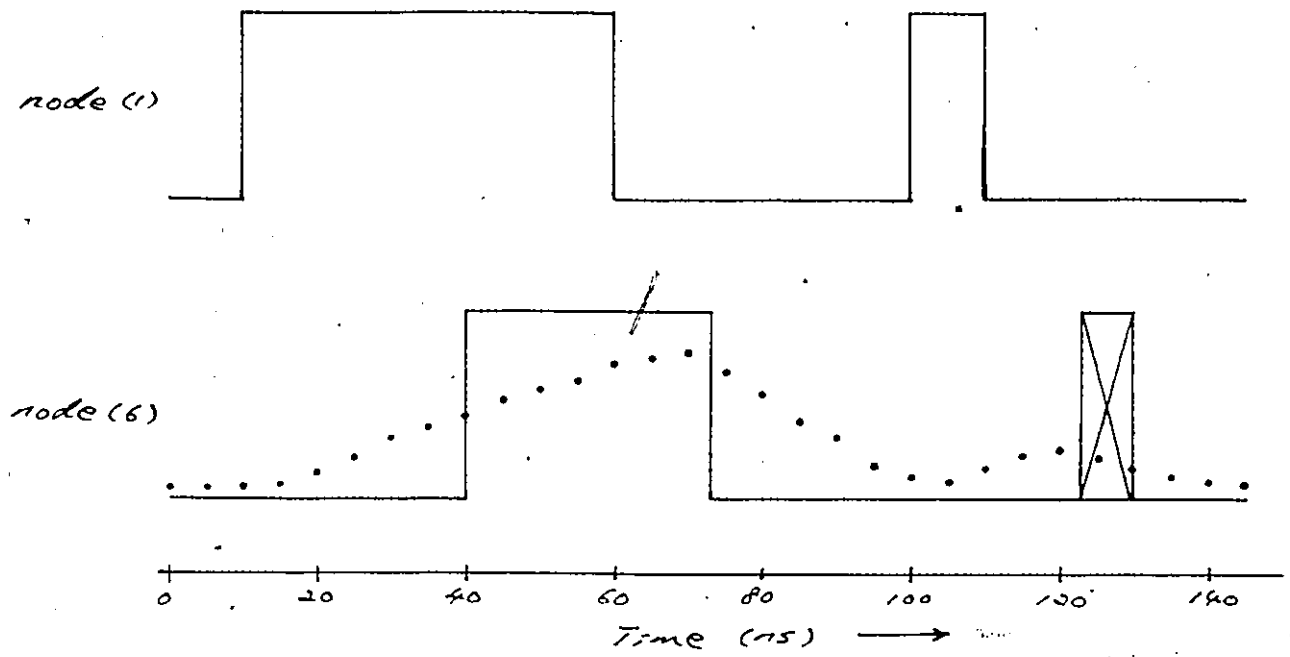


Figure 5.11 : Input and output waveforms for Example 6

Chapter VI

CONCLUSIONS

In this thesis, a new multiple delay switch-level simulator for MOS LSI circuits has been presented which includes the following features: table-driven, time queue with macro time event list for simulation with multiple rise and fall delays, selective tracing of active paths, and event scheduling and rescheduling on the time queue including spike detection.

The delay model used in this simulator is organized around a subnetwork, instead of logic gates. The use of subnetworks permits both logic gates and pass transistors to be handled in a uniform fashion. The delay model takes into account the effects of not only output loading capacitance but also the input waveform. The delay model presented here also helps in removing most of the limitations mentioned in [16]: inability to handle "multiple input to output delays", "delay of a gate driving the data input of a pass transistor", "slope of the input waveform", and "overlapping transitions".

An improved algorithm is described for computing the node states and delays of a subnetwork. The algorithm is based on scheduling of subnetworks which are locally evaluated based on local relaxation method.

Some MOS circuit designs depend on the relative sizes of several capacitances for their logical behavior. This is seen frequently with pre-charge buses, in which a charge is first placed on a bus, and then this bus drives its signal through a pass transistor onto a dynamic RAM cell. In this algorithm, the nodes will be set to X (unless they were previously in the same state), because the simulator does not know the relative capacitance values. This shortcoming can be circumvented by allowing different kinds of storage nodes, e.g., "Strong" and "Weak" nodes. The previously described algorithm can be extended by ranking the node strengths as: Driver > Pullup > Strong > Weak. There are other limitations of this multiple delay simulator. First, the use of X state for representing both the unknown or initial state and an error state. For more accurate design verification, the above two cases should be distinguished by having X for initially unknown state and E for an error state. Second, the simulator receives information about transistors and parasitic capacitances of nodes, but not resistances of interconnects. Thus, propagation delay in long wires is ignored.

In this multiple delay simulator, most of the limitations mentioned in [16] were addressed. It will be interesting to study the performance of this proposed simulator. The following areas for future work are prompted from this thesis:

1. The use of more logic values for more accurate logic verification.
2. The provision of more accurate delay time estimation for unknown state.
3. The inclusion of wiring delays in delay time calculation.

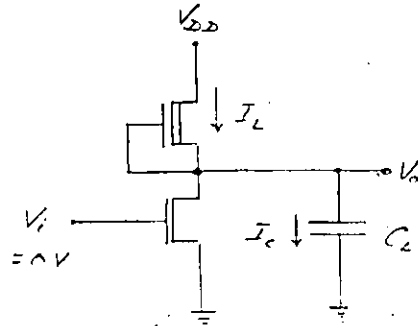
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Appendix A
DERIVATION OF RISE TIME AND RISE DELAY OF AN
NMOS INVERTER



$$V_o(0) = V_L$$

$$V_{TD} < 0, V_{TE} > 0$$

Rise Time

When $V_{GS} = 0V > V_{TD}$, $V_{DS} = V_{DD} - V_o \geq V_{GS} - V_{TD} = -V_{TD}$, the load transistor is in saturation region.

$$I_L = \frac{U_n C_o W_1}{2 L_1} (V_{GS} - V_{TD})^2$$

$$= \frac{U_n C_o W_1}{2 L_1} (-V_{TD})^2$$

$$I_c = C_L \frac{dV_o}{dt}$$

$$C_L \frac{dV_o}{dt} = \frac{U_n C_o W_1}{2 L_1} (-V_{TD})^2$$

The time in the saturation region,

$$t_{sat} = \int_{X_1}^{V_{DD} + V_{TD}} \frac{2 C_L}{U_n C_o (W_1/L_1) (-V_{TD})^2} \cdot dV_o$$

$$= \frac{2 C_L}{U_n C_o (W_1/L_1) (-V_{TD})^2} (V_{DD} + V_{TD} - X_1)$$

When $V_{GS} = OV > V_{TD}$, $V_{DS} = V_{DD} - V_o \leq -V_{TD}$, the load transistor is in linear region,

$$I_L = \frac{U_{nO}}{2} \cdot \frac{W_1}{L_1} \left[2(V_{GS} - V_{TD}) V_{DS} - V_{DS}^2 \right]$$

$$= \frac{U_{nO}}{2} \cdot \frac{W_1}{L_1} \left[2(-V_{TD})(V_{DD} - V_o) - (V_{DD} - V_o)^2 \right]$$

$$I_c = C_L \frac{dV_o}{dt}$$

$$C_L \frac{dV_o}{dt} = \frac{U_{nO}}{2} \cdot \frac{W_1}{L_1} \left[2(-V_{TD})(V_{DD} - V_o) - (V_{DD} - V_o)^2 \right]$$

The time in the linear region,

$$t_{lin} = \int_{V_{DD} + V_{TD}}^{X_2} \frac{C_L}{U_{nO} W_1 / L_1} \cdot \frac{dV_o}{2(-V_{TD})(V_{DD} - V_o) - (V_{DD} - V_o)^2}$$

$$= \frac{C_L}{U_{nO} (-V_{TD}) W_1 / L_1} \cdot \int_{V_{DD} + V_{TD}}^{X_2} \left(\frac{1}{V_{DD} - V_o} + \frac{1}{2(-V_{TD}) - (V_{DD} - V_o)} \right) \cdot dV_o$$

$$= \frac{C_L}{U_{nO} (-V_{TD}) W_1 / L_1} \cdot \left[\ln \left(\frac{2(-V_{TD}) - (V_{DD} - V_o)}{(V_{DD} - V_o)} \right) \right]_{V_{DD} + V_{TD}}^{X_2}$$

$$= \frac{C_L}{U_{nO} (-V_{TD}) W_1 / L_1} \cdot \ln \left(\frac{2(-V_{TD}) - (V_{DD} - X_2)}{(V_{DD} - X_2)} \right)$$

The total rise time t_r is

$$t_r = t_{\text{sat}} + t_{\text{lin}}$$

$$= \frac{2 C_L}{U_n C_o V_{DD} W_1/L_1} \left[\frac{V_{DD}}{(-V_{TD})^2} \cdot (V_{DD} + V_{TD} - X_1) + \frac{V_{DD}/2}{(-V_{TD})} \cdot \ln \left(\frac{2(-V_{TD}) - (V_{DD} - X_2)}{(V_{DD} - X_2)} \right) \right]$$

Rise Delay

When the load transistor is in saturation region,

$$t_{\text{pl}} = \int_{V_Z}^{V_{DD} + V_{TD}} \frac{2 C_L}{U_n C_o (-V_{TD})^2 W_1/L_1} \cdot dV_o$$

$$= \frac{2 C_L}{U_n C_o (-V_{TD})^2 W_1/L_1} \cdot (V_{DD} + V_{TD} - V_L)$$

When the load transistor is in linear region,

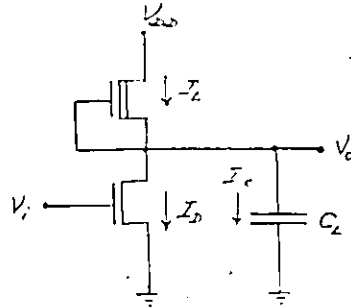
$$\begin{aligned}
 t_{p2} &= \int_{V_{DD} + V_{TD}}^{X_{.5}} \frac{2 C_L}{U_n C_o W_1 / L_1 \cdot 2(-V_{TD})(V_{DD} - V_o) - (V_{DD} - V_o)^2} dV_o \\
 &= \frac{C_L}{U_n C_o (-V_{TD}) W_1 / L_1} \cdot \left[\ln \left(\frac{2(-V_{TD}) - (V_{DD} - V_o)}{(V_{DD} - V_o)} \right) \right]_{V_{DD} + V_{TD}}^{X_{.5}} \\
 &= \frac{C_L}{U_n C_o (-V_{TD}) W_1 / L_1} \cdot \ln \left(\frac{2(-V_{TD}) - (V_{DD} - X_{.5})}{(V_{DD} - X_{.5})} \right)
 \end{aligned}$$

The total rise delay t_{pLH} is

$$t_{pLH} = t_{p1} + t_{p2}$$

$$\begin{aligned}
 &= \frac{2 C_L}{U_n C_o V_{DD} W_1 / L_1} \cdot \left[\frac{V_{DD}}{(-V_{TD})^2} (V_{DD} + V_{TD} - V_L) \right. \\
 &\quad \left. + \frac{V_{DD}/2}{(-V_{TD})} \cdot \ln \left(\frac{2(-V_{TD}) - (V_{DD} - X_{.5})}{(V_{DD} - X_{.5})} \right) \right]
 \end{aligned}$$

Appendix B
DERIVATION OF FALL TIME AND FALL DELAY OF AN
NMOS INVERTER



$$V_o(0) = V_{DD}$$

$$V_{TD} < 0, V_{TE} > 0$$

$$K = \frac{W_L/L_L}{W_D/L_D}$$

Fall Time

When $V_{DD} \geq V_o \geq V_i - V_{TE}$, load transistor is in linear region and driver transistor is in saturation region.

$$I_L = \frac{U_{n0}}{2} \cdot \frac{W_L}{L_L} \cdot \left[2(-V_{TD})(V_{DD} - V_o) - (V_{DD} - V_o)^2 \right]$$

$$I_D = \frac{U_{n0}}{2} \cdot \frac{W_D}{L_D} \cdot (V_i - V_{TE})^2$$

$$I_c = C_L \frac{dV_o}{dt}$$

$$C_L \frac{dV_o}{dt} = - \frac{U_{n0}}{2} \cdot \frac{W_L}{L_L} \cdot \left[(V_{DD} - V_o)^2 - 2(-V_{TD})(V_{DD} - V_o) + k(V_i - V_{TE})^2 \right]$$

$$t_{fl} = - \frac{2 C_L}{U_{n0} W_L / L_L} \cdot \int_{X_2}^{V_i - V_{TE}} \frac{dV_o}{(V_{DD} - V_o)^2 - 2(-V_{TD})(V_{DD} - V_o) + k(V_i - V_{TE})^2}$$

$$\text{let } V = V_{DD} - V_o, \quad dV = -dV_o$$

$$t_{fl} = \frac{2 C_L}{U_n C_{ox} W_1 / L_1} \int_{V_{DD} - X_2}^{V_{DD} - (V_i - V_{TE})} \frac{dV}{V^2 - 2(-V_{TD})V + k(V_i - V_{TE})^2}$$

$$\text{for } a = 1, \quad b = 2V_{TD}, \quad c = k(V_i - V_{TE})^2$$

$$\int \frac{dX}{aX^2 + bX + c} = \frac{2}{[4ac - b^2]^{1/2}} \cdot \tan^{-1} \left(\frac{2aX + b}{[4ac - b^2]^{1/2}} \right)$$

$$\frac{2}{[4ac - b^2]^{1/2}} = \frac{2}{[4k(V_i - V_{TE})^2 - 4V_{TD}^2]^{1/2}}$$

$$= \frac{1}{[k(V_i - V_{TE})^2 - V_{TD}^2]^{1/2}}$$

$$t_{fl} = \frac{2 C_L}{U_n C_{ox} W_1 / L_1} \cdot \frac{2}{[4ac - b^2]^{1/2}} \cdot \left[\tan^{-1} \left(\frac{2aV + 2V_{TD}}{[4ac - b^2]^{1/2}} \right) \right]_{V_{DD} - (V_i - V_{TE})}^{V_{DD} - X_2}$$

$$= \frac{V_{DD}}{[k(V_i - V_{TE})^2 - V_{TD}^2]^{1/2}} \cdot \left[\tan^{-1} \left(\frac{V_{DD} - (V_i - V_{TE}) - V_{TD}}{[k(V_i - V_{TE})^2 - V_{TD}^2]^{1/2}} \right) \right]$$

$$- \tan^{-1} \left(\frac{V_{DD} - X_2 + V_{TD}}{[k(V_i - V_{TE})^2 - V_{TD}^2]^{1/2}} \right) \cdot \frac{2 C_L}{U_n C_{ox} V_{DD} W_1 / L_1}$$

When $V_i - V_{TE} \geq V_o \geq V_{DD} + V_{TD}$, both transistors are in linear region,

$$I_L = \frac{U_{nO} C_o}{2} \cdot \frac{W_1}{L_1} \cdot \left[2(-V_{TD})(V_{DD} - V_o) - (V_{DD} - V_o)^2 \right]$$

$$I_D = \frac{U_{nO} C_o}{2} \cdot \frac{W_d}{L_d} \cdot \left[2(V_i - V_{TE})V_o - V_o^2 \right]$$

$$I_C = C_L \frac{dV_o}{dt}$$

$$C_L \frac{dV_o}{dt} = \frac{U_{nO} C_o}{2} \cdot \frac{W_1}{L_1} \cdot \left[(k-1)V_o^2 + (2V_{TD} + 2V_{DD} - 2k(V_i - V_{TE}))V_o + (-2V_{TD}V_{DD} - V_{DD}^2) \right]$$

$$t_{f2} = \left(\int_{V_i - V_{TE}}^{V_{DD} + V_{TD}} \frac{dV_o}{(k-1)V_o^2 + (2V_{TD} + 2V_{DD} - 2k(V_i - V_{TE}))V_o + (-2V_{TD}V_{DD} - V_{DD}^2)} \right) \cdot \frac{2 C_L}{U_{nO} C_o W_1 / L_1}$$

for $a = (k-1)$, $b = 2V_{TD} + 2V_{DD} - 2k(V_i - V_{TE})$, $c = -2V_{TD}V_{DD} - V_{DD}^2$

$$\int \frac{dx}{ax^2 + bx + c} = \frac{1}{[b^2 - 4ac]^{1/2}} \cdot \ln \left(\frac{2ax + b - [b^2 - 4ac]^{1/2}}{2ax + b + [b^2 - 4ac]^{1/2}} \right)$$

$$\frac{1}{[b^2 - 4ac]^{1/2}} = \frac{1}{[4(V_{TD} + V_{DD} - k(V_i - V_{TE}))^2 + 4(k-1)(2V_{TD}V_{DD} + V_{DD}^2)]^{1/2}}$$

$$t_{f2} = \frac{2 C_L}{U_{n0} W_1 / L_1} \cdot \frac{1}{[b^2 - 4ac]^{1/2}} \cdot \left[\ln \left| \frac{2aV_o + b - [b^2 - 4ac]^{1/2}}{2aV_o + b + [b^2 - 4ac]^{1/2}} \right| \right]_{V_i - V_{TE}}^{V_{DD} + V_{TD}}$$

$$= \frac{V_{DD}}{[b^2 - 4ac]^{1/2}} \cdot \left[\ln \left| \frac{2a(V_{DD} - V_{TD}) + b - [b^2 - 4ac]^{1/2}}{2a(V_{DD} - V_{TD}) + b + [b^2 - 4ac]^{1/2}} \right| \right]$$

$$- \ln \left| \frac{2a(V_i - V_{TE}) + b - [b^2 - 4ac]^{1/2}}{2a(V_i - V_{TE}) + b + [b^2 - 4ac]^{1/2}} \right| \cdot \frac{2 C_L}{U_{n0} V_{DD} W_1 / L_1}$$

When $V_{DD} + V_{TD} \geq V_o \geq X_1$, load transistor is in saturation region and driver transistor is in linear region.

$$I_L = \frac{U_{n0}}{2} \cdot \frac{W_1}{L_1} \cdot (-V_{TD})^2$$

$$I_D = \frac{U_{n0}}{2} \cdot \frac{W_d}{L_d} \cdot \left[2(V_i - V_{TE})V_o - V_o^2 \right]$$

$$I_c = C_L \frac{dV_o}{dt}$$

$$C_L \frac{dV_o}{dt} = \frac{U_{n0}}{2} \cdot \frac{W_1}{L_1} \cdot \left[kV_o^2 - 2k(V_i - V_{TE})V_o + (-V_{TD})^2 \right]$$

$$t_{f3} = \frac{2 C_L}{U_{n0} W_1 / L_1} \cdot \int_{V_{DD} + V_{TD}}^{X_1} \frac{dV_o}{kV_o^2 - 2k(V_i - V_{TE})V_o + (-V_{TD})^2}$$

for $a = k$, $b = -2k(V_i - V_{TE})$, $c = (-V_{TD})^2$

$$t_{f3} = \frac{V_{DD}}{[b^2 - 4ac]^{1/2}} \cdot \left[\ln \left| \frac{2aX_1 + b - [b^2 - 4ac]^{1/2}}{2aX_1 + b + [b^2 - 4ac]^{1/2}} \right| - \ln \left| \frac{2a(V_{DD} + V_{TD}) + b - [b^2 - 4ac]^{1/2}}{2a(V_{DD} + V_{TD}) + b + [b^2 - 4ac]^{1/2}} \right| \right] \cdot \frac{2 C_L}{U_n C_o V_{DD} W_1 / L_1}$$

The total fall time,

$$t_f = t_{f1} + t_{f2} + t_{f3}$$

Fall Delay

When load transistor is in linear region and driver transistor is in saturation region,

$$\begin{aligned} t_{pl} &= \int_{V_{DD}}^{V_i - V_{TE}} - \frac{2 C_L}{U_n C_o W_1 / L_1} \cdot \frac{dV_o}{(V_{DD} - V_o)^2 - 2(-V_{TD})(V_{DD} - V_o) + k(V_i - V_{TE})^2} \\ &= \frac{V_{DD}}{[k(V_i - V_{TE})^2 - V_{TD}^2]^{1/2}} \cdot \left[\tan^{-1} \left(\frac{V_{DD} - (V_i - V_{TE}) + V_{TD}}{[k(V_i - V_{TE})^2 - V_{TD}^2]^{1/2}} \right) - \tan^{-1} \left(\frac{V_{TD}}{[k(V_i - V_{TE})^2 - V_{TD}^2]^{1/2}} \right) \right] \cdot \frac{2 C_L}{U_n C_o V_{DD} W_1 / L_1} \end{aligned}$$

When both transistors are in linear region,

$$t_{p2} = \left(\int_{V_i - V_{TE}}^{X \cdot 5} \frac{dV_o}{(k-1)V_o^2 + (2V_{TD} + 2V_{DD} - 2k(V_i - V_{TE}))V_o + (-2V_{TD}V_{DD} - V_{DD}^2)} \right) \cdot \frac{2 C_L}{U_n C_{ox} W_1 / L_1}$$

for $a = (k - 1)$, $b = 2V_{TD} + 2V_{DD} - 2k(V_i - V_{TE})$, $c = -2V_{TD}V_{DD} - V_{DD}^2$

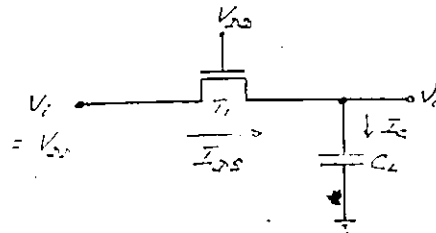
$$t_{p2} = \frac{V_{DD}}{[b^2 - 4ac]^{1/2}} \cdot \left[\ln \left| \frac{2aX \cdot 5 + b - [b^2 - 4ac]^{1/2}}{2aX \cdot 5 + b + [b^2 - 4ac]^{1/2}} \right| - \ln \left| \frac{2a(V_i - V_{TE}) + b - [b^2 - 4ac]^{1/2}}{2a(V_i - V_{TE}) + b + [b^2 - 4ac]^{1/2}} \right| \right] \cdot \frac{2 C_L}{U_n C_{ox} V_{DD} W_1 / L_1}$$

The total fall delay,

$$t_{pHL} = t_{p1} + t_{p2}$$

Appendix C

DERIVATION OF TRANSITION AND DELAY TIMES OF A PASS TRANSISTOR



$$V_{TP} > 0$$

$$V_f = V_{DD} - V_{TP}$$

Rise Time

Transistor T_1 is in saturation region.

$$I_{DS} = \frac{\mu_n C_{ox}}{2} \cdot \frac{W_p}{L_p} \cdot (V_{DD} - V_O - V_{TP})^2$$

$$= \frac{\mu_n C_{ox}}{2} \cdot \frac{W_p}{L_p} \cdot (V_f - V_O)^2$$

$$I_c = C_L \frac{dV_O}{dt}$$

$$C_L \frac{dV_O}{dt} = \frac{\mu_n C_{ox}}{2} \cdot \frac{W_p}{L_p} \cdot (V_f - V_O)^2$$

$$t_r = \int_{X_1}^{X_2} \frac{2 C_L}{\mu_n C_{ox} W_p / L_p} \cdot \frac{dV_O}{(V_f - V_O)^2}$$

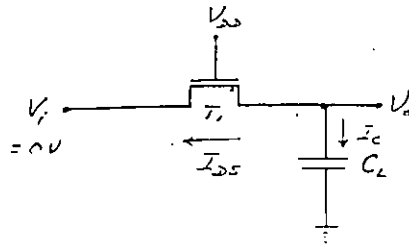
$$= \frac{2 C_L}{\mu_n C_{ox} W_p / L_p} \cdot \left[\frac{1}{V_f - V_O} \right]_{X_1}^{X_2}$$

$$t_r = \frac{2 C_L}{U_{n o p} W_p / L_p} \cdot \left(\frac{1}{V_f - X_2} - \frac{1}{V_f - X_1} \right)$$

Rise Delay

$$t_{pLH} = \int_{V_L}^{X.5} \frac{2 C_L}{U_{n o p} W_p / L_p} \cdot \frac{dV_o}{(V_f - V_o)^2}$$

$$= \frac{2 C_L}{U_{n o p} W_p / L_p} \cdot \left(\frac{1}{V_f - X.5} - \frac{1}{V_f - V_L} \right)$$



$$V_o(0) = V$$

$$V_{TP} > 0$$

Fall Time

Transistor T_1 is in linear region.

$$I_{DS} = \frac{U_{n0}}{2} \cdot \frac{C_o}{L_p} \cdot \frac{W_p}{L_p} \cdot \left[2(V_{DD} - V_{TP})V_o - V_o^2 \right]$$

$$= \frac{U_{n0}}{2} \cdot \frac{C_o}{L_p} \cdot \frac{W_p}{L_p} \cdot (2V_f V_o - V_o^2)$$

$$I_o = C_L \frac{dV_o}{dt}$$

$$C_L \frac{dV_o}{dt} = \frac{U_{n0}}{2} \cdot \frac{C_o}{L_p} \cdot \frac{W_p}{L_p} \cdot (V_o^2 - 2V_f V_o)$$

$$t_f = \int_{X_2}^{X_1} \frac{2 C_L}{U_{n0} W_p / L_p} \cdot \frac{dV_o}{(V_o^2 - 2V_f V_o)}$$

$$= - \frac{2 C_L}{U_{n0} W_p / L_p} \cdot \frac{1}{2V_f} \cdot \int_{X_2}^{X_1} \left(\frac{1}{V_o} + \frac{1}{2V_f - V_o} \right) \cdot dV_o$$

$$= \frac{C_L}{U_{n0} V_f W_p / L_p} \cdot \left[\ln \left(\frac{2V_f - V_o}{V_o} \right) \right]_{X_2}^{X_1}$$

$$t_f = \frac{C_L}{U_n C_{ov} W_p / L_1} \cdot \left[\ln\left(\frac{2V_f - X_1}{X_1} \right) - \ln\left(\frac{2V_f - X_2}{X_2} \right) \right]$$

Fall Delay

$$t_{pHL} = \int_{V_H}^{X_{.5}} \frac{2 C_L}{U_n C_{ov} W_p / L_p} \cdot \frac{dV_o}{(V_o^2 - 2V_f V_o)}$$

$$= \frac{C_L}{U_n C_{ov} W_p / L_p} \cdot \left[\ln\left(\frac{2V_f - X_{.5}}{X_{.5}} \right) - \ln\left(\frac{2V_f - V_H}{V_H} \right) \right]$$

Appendix D
PROGRAM LISTING

```

1  0680 -- PROGRAM simulation (input,output);
2  06A8 --
3  06A8 -- CONST
4  06A8 --     nodemax = 100 ;
5  06A8 --     transmax = 100 ;
6  06A8 --     Z = 50 ;
7  06A8 --     Z2 = 100 ;
8  06A8 --     UC = 2.0E-5 ;
9  06A8 --     VDD = 5 ;
10 06A8 --     VTE = 1 ;
11 06A8 --     VTD = -4 ;
12 06A8 --
13 06A8 -- TYPE
14 06A8 --     nodenumber = 1..nodemax;
15 06A8 --     transnumber = 1..transmax;
16 06A8 --     statevalue = 0..2;
17 06A8 --     strengvalue = 1..3;
18 06A8 --     ntype = 1..2;
19 06A8 --     ttype = 1..3;
20 06A8 --
21 06A8 --     inputlink = @inputnode ;
22 06A8 --     inputnode =
23 06A8 --         RECORD
24 06A8 --             fptr : inputlink ;
25 06A8 --             node : integer
26 06A8 --         END ;
27 06A8 --
28 06A8 --     pathlink = @pathnode ;
29 06A8 --     pathnode =
30 06A8 --         RECORD
31 06A8 --             fptr : pathlink ;
32 06A8 --             node : integer ;
33 06A8 --             no : integer
34 06A8 --         END ;
35 06A8 --
36 06A8 --     tilink = @timing;
37 06A8 --     timing =
38 06A8 --         RECORD
39 06A8 --             fptr, bptr : tilink;
40 06A8 --             time : integer;
41 06A8 --             newstate : statevalue;
42 06A8 --             tsi : real
43 06A8 --         END;
44 06A8 --
45 06A8 --     trlink = @transint;
46 06A8 --     transint =
47 06A8 --         RECORD
48 06A8 --             fptr : trlink;
49 06A8 --             trans : integer
50 06A8 --         END;
51 06A8 --
52 06A8 --     glink = @gate;
53 06A8 --     gate =
54 06A8 --         RECORD
55 06A8 --             node : integer;
56 06A8 --         END;
57 06A8 --
58 06A8 --     slink = @source;

```

```

59 06A8 -- source =
60 06A8 --   RECORD
61 06A8 --     node : integer
62 06A8 --   END;
63 06A8 --
64 06A8 --   dlink = @drain;
65 06A8 --   drain =
66 06A8 --     RECORD
67 06A8 --       node : integer
68 06A8 --     END;
69 06A8 --
70 06A8 --   hlink = @headernode ;
71 06A8 --   headernode =
72 06A8 --     RECORD
73 06A8 --       fptr : hlink ;
74 06A8 --       node : integer
75 06A8 --     END ;
76 06A8 --
77 06A8 --   plink = @plist ;
78 06A8 --   plist =
79 06A8 --     RECORD
80 06A8 --       fptr : plink ;
81 06A8 --       gr : integer
82 06A8 --     END ;
83 06A8 --
84 06A8 --   evlink = @evinfo ;
85 06A8 --   evinfo =
86 06A8 --     RECORD
87 06A8 --       fptr : evlink ;
88 06A8 --       node : integer ;
89 06A8 --       newsta : statevalue ;
90 06A8 --       time : integer ;
91 06A8 --       tt : real
92 06A8 --     END ;
93 06A8 --
94 06A8 --   overlink = @overflow ;
95 06A8 --   overflow =
96 06A8 --     RECORD
97 06A8 --       fptr,bptr : overlink ;
98 06A8 --       node : integer ;
99 06A8 --       newsta : statevalue ;
100 06A8 --       time : integer ;
101 06A8 --       tt : real
102 06A8 --     END ;
103 06A8 --
104 06A8 --   pendlink = @pend ;
105 06A8 --   pend =
106 06A8 --     RECORD
107 06A8 --       fptr : pendlink ;
108 06A8 --       group : integer ;
109 06A8 --     END ;
110 06A8 --
111 06A8 --   graph = ARRAY[0..nodemax] OF hlink ;
112 06A8 --   gte = ARRAY[0..10] OF statevalue ;
113 06A8 --   gth = ARRAY[0..10] OF strengvalue ;
114 06A8 --   list = ARRAY[1..22] OF evlink ;
115 06A8 --   pathline = ARRAY[1..10] OF pathlink ;
116 06A8 --

```

```

117 06A8 --      nodeinfo =
118 06A8 --      RECORD
119 06A8 --          tiptr : tilink ;
120 06A8 --          fcptr,icptr : trlink ;
121 06A8 --          trigger,visit,inev : boolean ;
122 06A8 --          state,newsta : statevalue ;
123 06A8 --          strength : strengvalue ;
124 06A8 --          nodetype : ntype ;
125 06A8 --          capvalue : real ;
126 06A8 --          fc,ic : integer ;
127 06A8 --          W,L : real ;
128 06A8 --          group : integer
129 06A8 --      END;
130 06A8 --
131 06A8 --      transinfo =
132 06A8 --      RECORD
133 06A8 --          gptra : glink ;
134 06A8 --          dptra : dlink ;
135 06A8 --          sptra : slink ;
136 06A8 --          trigger : boolean ;
137 06A8 --          state : statevalue ;
138 06A8 --          transtype : ttype ;
139 06A8 --          W,L : real
140 06A8 --      END;
141 06A8 --
142 06A8 --  VAR
143 06A8 --      node : ARRAY[nodenum] OF nodeinfo ;
144 25E8 --      trans : ARRAY[transnum] OF transinfo;
145 3588 --      network,subnet,sub,group,supergroup,h : graph ;
146 3F00 --      n,m : integer ;
147 3F08 --      TQ : list ;
148 4098 --      inpu,inp : inputlink ;
149 40A0 --      tim,pi : tilink ;
150 40A8 --      event : evlink ;
151 40AC --      MTEL,ev,newev : overlink ;
152 40B8 --      evpend : pendlink ;
153 40BC --      EVL,point : hlink ;
154 40C4 --      fp,l : trlink ;
155 40CC --      ST,MTC,evnum : integer ;
156 40D8 --      t,tm : integer ;
157 40E0 --      tt : real ;
158 40E8 --      i,j,k,v,w : integer ;
159 40FC --      sta : statevalue ;
160 4100 --      str : strengvalue ;
161 4104 --      unit : boolean ;
162 4108 --      pullup : boolean ;
163 410C --      q,ii,pn : integer ;
164 4118 --      path : pathline ;
165 4140 --
166 4140 --
167 4140 --  A  PROCEDURE search ( VAR first : hlink ;
168 0040 --      i : integer ;
169 0040 --      x0,x1,xx : statevalue ) ;
170 0054 --
171 0054 --      (* search for an adjacent node *)
172 0054 --
173 0054 --  VAR
174 0054 --      l : trlink ;

```

```

175 0058 --      base : hlink ;
176 005C --      j,k : integer ;
177 0064 --
178 0000 0- A BEGIN
179 0012 --      node[i].visit := true ;
180 0032 --      l := node[i].icptr ;
181 005C --      IF l <> NIL THEN
182 006E --          WHILE l <> NIL DO
183 0080 1-              BEGIN
184 0080 --                  j := l@.trans ;
185 0098 --                  IF (trans[j].state = X0) OR (trans[j].state = X1)
186 0114 --                      OR (trans[j].state = XX) THEN
187 015C 2-                      BEGIN
188 015C --                          IF (trans[j].dptr@.node <> i) AND
189 01A4 --                              (node[trans[j].dptr@.node].visit = false)
190 01FC --                              THEN
191 0204 3-                                  BEGIN
192 0204 --                                      k := trans[j].dptr@.node ;
193 023A --                                      new(base) ;
194 0248 --                                      base@.fptr := first ;
195 0268 --                                      base@.node := k ;
196 0280 --                                      first := base ;
197 0296 --                                      search(first,k,X0,X1,XX)
198 02E2 -3                                  END
199 02E6 --                                  ELSE
200 02EA --                                      IF (trans[j].sptr@.node <> i) AND
201 0332 --                                          (node[trans[j].sptr@.node].visit = false)
202 038A --                                          THEN
203 0392 3-                                              BEGIN
204 0392 --                                                  k := trans[j].sptr@.node ;
205 03C8 --                                                  new(base) ;
206 03D6 --                                                  base@.fptr := first ;
207 03F6 --                                                  base@.node := k ;
208 040E --                                                  first := base ;
209 0424 --                                                  search(first,k,X0,X1,XX)
210 0470 -3                                              END
211 0474 -2                                  END ;
212 0474 --                                  l := l@.fptr
213 047E -1                                  END
214 0490 -0 A END ;
215 04AC --
216 04AC -- A PROCEDURE partition ( VAR header : graph ;
217 0040 --      index : integer ;
218 0040 --      X0,X1,XX : statevalue ) ;
219 0054 --
220 0054 -- (* partition an undirected graph into its connected components *
221 0054 --
222 0054 -- VAR
223 0054 --     start,delete,hd : hlink ;
224 0060 --     i : integer ;
225 0064 --
226 0000 0- A BEGIN
227 0012 --     start := header[index] ;
228 003A --     WHILE start <> NIL DO
229 004C 1-         BEGIN
230 004C --             node[start@.node].visit := false ;
231 0074 --             start := start@.fptr
232 007E -1         END;

```

```

233 0094 --      start := header[index] ;
234 00BC --      m := 0 ;
235 00C8 --      WHILE start <> NIL DO
236 00DA 1-          BEGIN
237 00DA --              IF node[start@.node].visit = false THEN
238 010E 2-                  BEGIN
239 010E --                      m := m+1 ;
240 012C --                      new(hd) ;
241 013A --                      hd@.fptr := NIL ;
242 014A --                      hd@.node := start@.node ;
243 016C --                      i := start@.node ;
244 0184 --                      search(hd,i,X0,X1,XX) ;
245 01D4 --                      header[m] := hd ;
246 0202 -2                          END ;
247 0202 --                      start := start@.fptr
248 020C -1                          END
249 021E -0 A      END;
250 023C --
251 023C -- A      PROCEDURE appendev ( x : integer ;
252 0040 --                      nesta : statevalue ;
253 0040 --                      toccur : integer ;
254 0040 --                      tsi : real ) ;
255 0058 --
256 0058 --      (* adding an event to the TQ array *)
257 0058 --
258 0058 --      VAR
259 0058 --          event : evlink ;
260 005C --          ev,newev : overlink ;
261 0064 --          j : integer ;
262 0068 --
263 0000 0- A      BEGIN
264 0012 --          j := toccur - ( Z * MTC - 1 ) ;
265 0040 --          IF j <= Z2 THEN
266 0052 1-              BEGIN
267 0052 --                  new(event) ;
268 0060 --                  WITH event@ DO
269 006C 2-                      BEGIN
270 006C --                          fptr := TQ[j] ;
271 0096 --                          node := x ;
272 00A4 --                          newsta := nesta ;
273 00B6 --                          time := toccur ;
274 00C4 --                          tt := tsi
275 00C4 -2                              END ;
276 00D6 --                          \ TQ[j] := event
277 00E8 -1                              END
278 0100 --                      ELSE
279 0104 1-                          BEGIN
280 0104 --                              new(newev) ;
281 0112 --                              WITH newev@ DO
282 011E 2-                                  BEGIN
283 011E --                                      node := x ;
284 012C --                                      newsta := nesta ;
285 013E --                                      time := toccur ;
286 014C --                                      tt := tsi
287 014C -2                                          END ;
288 015E --                              ev := MTEL ;
289 0176 2-                                  REPEAT
290 0176 --                                      ev := ev@.bptr

```

```

291 0180 -2          UNTIL newev@.time >= ev@.time ;
292 01C0 --          newev@.fptr := ev@.fptr ;
293 01E6 --          newev@.bptr := ev ;
294 0202 --          ev@.fptr@.bptr := newev ;
295 0228 --          ev@.fptr := newev
296 0232 -1          END
297 0244 -0 A  END ;
298 0260 --
299 0260 -- A  PROCEDURE spike ( i : integer ;
300 0040 --          nesta : statevalue ;
301 0040 --          toc : integer ;
302 0040 --          ts : real ) ;
303 0058 --
304 0058 --      (* checking for spike *)
305 0058 --
306 0058 --      VAR
307 0058 --          pi,tim : tilink ;
308 0060 --          pointer : evlink ;
309 0064 --          ev : overlink ;
310 0068 --          stop : boolean ;
311 006C --          j : integer ;
312 0070 --
313 0000 0- A  BEGIN
314 0012 --      new(tim) ;
315 0020 --      WITH tim@ DO
316 002C 1-          BEGIN
317 002C --          time := toc ;
318 003A --          newstate := nesta ;
319 004C --          tsi := ts.
320 004C -1          END ;
321 005E --      stop := false ;
322 0064 --      pi := node[i].tiptr ;
323 008E 1-      REPEAT
324 008E --          pi := pi@.bptr ;
325 00AA --          IF ( tim@.time <= pi@.time ) AND ( pi <> pi@.fptr ) THEN
326 0110 2-              BEGIN
327 0110 --                  IF tim@.newstate <> pi@.newstate THEN
328 013E 3-                      BEGIN
329 013E --                          pi@.newstate := tim@.newstate ;
330 0164 --                          tim@.newstate := 2 ;
331 0176 --                          j := pi@.time - ( 2 * MTC - 1 ) ;
332 01AE --                          IF j <= 22 THEN
333 01C0 4-                              BEGIN
334 01C0 --                                  pointer := TQ[j] ;
335 01EA --                                  WHILE pointer <> NIL DO
336 01FC 5-                                      BEGIN
337 01FC --                                          IF pointer@.node = i THEN
338 0220 6-                                              BEGIN
339 0220 --                                                  pointer@.newsta := pi@.newstate
340 0246 --                                                  pointer := NIL
341 0246 -6                                              END
342 024C --                                          ELSE
343 0250 --                                              pointer := pointer@.fptr
344 025A -5                                          END
345 026C -4                                  END
346 0270 --                              ELSE
347 0274 4-                                  BEGIN
348 0274 --                                      ev := MTEL ;

```

```

349 028C 5- REPEAT
350 028C -- ev := ev@.bptr
351 0296 -5 UNTIL ev@.node = i ;
352 02CC -- ev@.newsta := pi@.newstate
353 02E0 -4 END
354 02F2 -3 END
355 02F2 -2 END
356 02F2 -- ELSE
357 02F6 2- BEGIN
358 02F6 -- tim@.fptr := pi@.fptr ;
359 031C -- tim@.bptr := pi ;
360 0338 -- pi@.fptr@.bptr := tim ;
361 035E -- pi@.fptr := tim ;
362 037A -- appendev(i,tim@.newstate,toc,ts) ;
363 03C8 -- stop := true
364 03C8 -2 END
365 03D0 -1 UNTIL stop = true
366 03DA -0 A END ;
367 0408 --
368 0408 -- A PROCEDURE readparameter ;
369 0040 --
370 0040 -- (* read simulation parameters *)
371 0040 --
372 0040 -- VAR
373 0040 -- pi : tilink ;
374 0044 -- base,p : trlink ;
375 004C -- g : glink ;
376 0050 -- d : dlink ;
377 0054 -- s : slink ;
378 0058 -- numnode,numtrans : integer ;
379 0060 -- tc,ti,i,t,num : integer ;
380 0074 -- sta : statevalue ;
381 0078 -- str : strengvalue ;
382 007C -- nty : ntype ;
383 0080 -- tty : ttype ;
384 0084 -- wid,len,cap : real ;
385 00A0 --
386 0000 A BEGIN
387 0012 -- network[0] := NIL ;
388 001E -- readln(numnode,numtrans) ;
389 0042 -- FOR num := 1 TO numnode DO
390 006E 1- BEGIN
391 006E -- readln(i,sta,str,nty,cap,tc,ti,wid,len) ;
392 0104 -- WITH node[i] DO
393 0124 2- BEGIN
394 0124 -- new(h[0]) ;
395 0138 -- h[0]@.node := i ;
396 0156 -- h[0]@.fptr := network[0] ;
397 017E -- network[0] := h[0] ;
398 019C -- appendev(i,sta,0,0) ;
399 01DC -- state := 2 ;
400 01E4 -- newsta := 2 ;
401 01EC -- strength := str ;
402 01FE -- nodetype := nty ;
403 0210 -- capvalue := cap ;
404 0222 -- fc := tc ;
405 0230 -- ic := ti ;
406 023E -- W := wid ;

```

```

407 0250 -- L := len ;
408 0262 -- ineq := false ;
409 0268 -- new(pi) ;
410 0276 -- pi@.fptr := pi ;
411 0292 -- pi@.bptr := pi ;
412 02AE -- pi@.time := 0 ;
413 02BE -- pi@.newstate := 2 ;
414 02D0 -- pi@.tsi := 0 ;
415 02F0 -- tiptr := pi ;
416 0302 -- IF fc > 0 THEN
417 0314 3- BEGIN
418 0314 -- base := NIL ;
419 031A -- FOR t := 1 TO tc DO
420 0346 4- BEGIN
421 0346 -- new(p) ;
422 0354 -- read(p@.trans) ;
423 0370 -- p@.fptr := base ;
424 038C -- base := p
425 038C -4 END ;
426 03C0 -- fcptr := p
427 03C0 -3 END
428 03D2 -- ELSE fcptr := NIL ;
429 03DC -- IF ic > 0 THEN
430 03EE 3- BEGIN
431 03EE -- base := NIL ;
432 03F4 -- FOR t := 1 TO ic DO
433 0420 4- BEGIN
434 0420 -- new(p) ;
435 042E -- read(p@.trans) ;
436 044A -- p@.fptr := base ;
437 0466 -- base := p
438 0466 -4 END ;
439 049A -- icptr := p
440 049A -3 END
441 04AC -- ELSE icptr := NIL
442 04B0 -2 END
443 04B6 -1 END ;
444 04D8 -- FOR num:=1 TO numtrans DO
445 0504 1- BEGIN
446 0504 -- readln(i,tty,wid,len) ;
447 054A -- WITH trans[i] DO
448 056A 2- BEGIN
449 056A -- state := 2 ;
450 0572 -- trigger := false ;
451 0578 -- transtype := tty ;
452 058A -- W := wid ;
453 059C -- L := len ;
454 05AE -- new(g) ;
455 05BC -- read(g@.node) ;
456 05D8 -- gptr := g ;
457 05EA -- new(d) ;
458 05F8 -- read(d@.node) ;
459 0614 -- dptr := d ;
460 0626 -- new(s) ;
461 0634 -- read(s@.node) ;
462 0650 -- sptr := s
463 0650 -2 END
464 0662 -1 END

```

```

465 0662 -0 A END ;
466 06A8 --
467 06A8 -- A PROCEDURE state ( front : graph ;
468 0040 --      ind : integer ;
469 0040 --      VAR grstate : statevalue ;
470 0040 --      VAR grstrength : strengvalue ) ;
471 01E0 --
472 01E0 --      (* compute the state and strength of the group *)
473 01E0 --
474 01E0 --      VAR
475 01E0 --          k,l : (N,W,P,D) ;
476 01E8 --          y : statevalue ;
477 01EC --          i : integer ;
478 01F0 --
479 0000 0- A BEGIN
480 0012 --      k := N ;      (* null strength *)
481 0018 --      y := 2 ;      (* X-state *)
482 0020 --      WHILE front[ind] <> NIL DO
483 0044 1-          BEGIN
484 0044 --              i := front[ind]@.node ;
485 006E --              IF node[i].strength = 1 THEN
486 0098 --                  l := W
487 0098 --              ELSE
488 00A4 --                  IF node[i].strength = 2 THEN
489 00CE --                      l := P
490 00CE --                  ELSE
491 00DA --                      IF node[i].strength = 3 THEN
492 0104 --                          l := D ;
493 010C --                      IF l > k THEN
494 0126 2-                          BEGIN
495 0126 --                              k := l ;
496 0134 --                              IF k = p THEN
497 0146 --                                  y := l
498 0146 --                              ELSE
499 0152 --                                  y := node[i].state
500 016A -2                              END
501 017C --                          ELSE
502 0180 --                              IF ( l = k ) AND ( node[i].state <> y ) THEN
503 01E0 --                                  y := 2 ;
504 01E8 --                                  front[ind] := front[ind]@.fptr
505 0216 -1                              END ;
506 022C --                          grstate := y ;
507 0242 --                          IF k = N THEN
508 0254 --                              writeln(' error in strength value ')
509 026C --                          ELSE
510 0276 --                              IF k = W THEN grstrength := 1
511 0288 --                              ELSE
512 0298 --                                  IF k = P THEN grstrength := 2
513 02AA --                                  ELSE
514 02BA --                                      IF k = D THEN grstrength := 3
515 02CC -0 A      END ;
516 0314 --
517 0314 -- A PROCEDURE poison ( VAR poillist : plink ;
518 0040 --      groups : graph ;
519 0040 --      gstr : gth ;
520 0040 --      pm : integer ) ;
521 0208 --
522 0208 --      (* poillist is expanded to include other poisoned groups *)

```

```

523 0208 --
524 0208 -- VAR
525 0208 -- pvector : ARRAY[1..3] OF plink ;
526 0214 -- pl,p2,p3,pp : plink ;
527 0224 -- l : trlink ;
528 0228 -- pq : hlink ;
529 022C -- i,j,k,q,s,t,v : integer ;
530 0248 -- found : boolean ;
531 024C --
532 0000 0- A BEGIN
533 0012 -- pp := poilist ;
534 0028 -- pvector[1] := NIL ;
535 002E -- pvector[2] := NIL ;
536 0034 -- pvector[3] := NIL ;
537 003A -- WHILE pp <> NIL DO
538 004C 1- BEGIN
539 004C -- IF gstr[pp@.gr] = 1 THEN
540 007A 2- BEGIN
541 007A -- new(pl) ;
542 0088 -- pl@.gr := pp@.gr ;
543 00AA -- pl@.fptr := pvector[1] ;
544 00C6 -- pvector[1] := pl .
545 00C6 -2 END
546 00D8 -- ELSE
547 00DC -- IF gstr[pp@.gr] = 2 THEN
548 010A 2- BEGIN
549 010A -- new(p2) ;
550 0118 -- p2@.gr := pp@.gr ;
551 013A -- p2@.fptr := pvector[2] ;
552 0156 -- pvector[2] := p2
553 0156 -2 END
554 0168 -- ELSE
555 016C 2- BEGIN
556 016C -- new(p3) ;
557 017A -- p3@.gr := pp@.gr ;
558 019C -- p3@.fptr := pvector[3] ;
559 01B8 -- pvector[3] := p3
560 01B8 -2 END ;
561 01CA -- pp := pp@.fptr
562 01D4 -1 END ;
563 01EA -- s := 1 ;
564 01F2 -- FOR t := 3 DOWNT0 s DO
565 021C -- WHILE pvector[t] <> NIL DO
566 0240 1- BEGIN
567 0240 -- v := pvector[t]@.gr ;
568 026A -- pvector[t] := pvector[t]@.fptr ;
569 02AA -- WHILE groups[v] <> NIL DO
570 02CE 2- BEGIN
571 02CE -- j := groups[v]@.node ;
572 02F8 -- l := node[j].icptr ;
573 0322 -- IF l <> NIL THEN
574 0334 -- WHILE l <> NIL DO
575 0346 3- BEGIN
576 0346 -- i := l@.trans ;
577 035E -- IF ( trans[i].state = 2 ) THEN
578 038E 4- BEGIN
579 038E -- IF ( trans[i].dptr@.node = j ) THEN
580 03D0 -- k := trans[i].sptr@.node

```

```

581 03F8 --
582 040A --
583 0440 --
584 046C 5-
585 046C --
586 0490 --
587 04A2 6-
588 04A2 --
589 04C6 7-
590 04C6 --
591 0504 8-
592 0504 --
593 0512 --
594 0524 --
595 0544 --
596 055A --
597 0590 --
598 059E --
599 05B0 --
600 05DE --
601 05F0 -8
602 0602 --
603 0606 --
604 064A --
605 0644 8-
606 0644 --
607 065A --
608 0660 --
609 0672 9-
610 0672 --
611 068E 0-
612 068E --
613 0696 --
614 0696 -0
615 069C --
616 06A0 --
617 06AA -9
618 06C0 --
619 06D2 9-
620 06D2 --
621 06E0 --
622 06F2 --
623 0712 --
624 0728 --
625 075E --
626 076C --
627 077E --
628 07AC --
629 07BE -9
630 07D0 -8
631 07D0 -7
632 07D0 --
633 07DA -6
634 07EC -5
635 07F0 -4
636 0812 --
637 081C -3
638 0832 --

ELSE
  k := trans[i].dptr@.node ;
  FOR q := 1 TO pm DO
    BEGIN
      pq := groups[q] ;
      WHILE pq <> NIL DO
        BEGIN
          IF k = pq@.node THEN
            BEGIN
              IF ( gstr[q] < gstr[v] ) THEN
                BEGIN
                  new(pp) ;
                  pp@.gr := q ;
                  pp@.fptr := poilist ;
                  poilist := pp ;
                  gstr[q] := gstr[v] ;
                  new(pp) ;
                  pp@.gr := q ;
                  pp@.fptr := pvector[t] ;
                  pvector[t] := pp
                END
              ELSE
                IF ( gstr[q] = gstr[v] )
                THEN
                  BEGIN
                    pp := poilist ;
                    found := false ;
                    WHILE pp <> NIL DO
                      BEGIN
                        IF q = pp@.gr THEN
                          BEGIN
                            found := true ;
                            pp := NIL
                          END
                        ELSE
                          pp := pp@.fptr
                        END ;
                      IF found = false THEN
                        BEGIN
                          new(pp) ;
                          pp@.gr := q ;
                          pp@.fptr := poilist ;
                          poilist := pp ;
                          gstr[q] := gstr[v] ;
                          new(pp) ;
                          pp@.gr := q ;
                          pp@.fptr := pvector[t] ;
                          pvector[t] := pp
                        END
                      END
                    END ;
                  pq := pq@.fptr
                END
              END ;
            END
          END
        END
      END ;
    END
  END ;
  l := l@.fptr
END ;
groups[v] := groups[v]@.fptr

```

```

639      0860 -2      END
640      0872 -1      END
641      0876 -0 A    END ;
642      08BC --
643      08BC -- A    PROCEDURE nodestate ( head : graph ;
644      0040 --      inx : integer ) ;
645      01D8 --
646      01D8 --      (* compute the node states of the subnetwork *)
647      01D8 --
648      01D8 --      VAR
649      01D8 --      ptr : hlink ;
650      01DC --      p,pptr : plink ;
651      01E4 --      gstate : gte ;
652      0210 --      gstrength : gth ;
653      023C --      i,r : integer ;
654      0244 --
655      0000 0- A    BEGIN
656      0012 --      state(head ,inx ,sta,str) ;
657      004A --      gstate[0] := sta ;
658      0062 --      gstrength[0] := str ;
659      007A --      partition(head,inx,1,1,1) ;
660      00AC --      IF m > 1 THEN
661      00C4 1-      BEGIN
662      00C4 --      pptr := NIL ;
663      00CA --      r := m ;
664      00DE --      WHILE r > 0 DO
665      00F0 2-      BEGIN
666      00F0 --      state(head ,r,sta,str) ;
667      0128 --      gstate[r] := sta ;
668      0152 --      gstrength[r] := str ;
669      017C --      IF gstate[r] <> gstate[0] THEN
670      01A8 3-      BEGIN
671      01A8 --      new(p) ;
672      01B6 --      p@.gr := r ;
673      01CE --      p@.fptr := pptr ;
674      01EA --      pptr := p
675      01EA -3      END ;
676      01FC --      r := r - 1
677      0206 -2      END ;
678      0212 --      poison(pptr,head ,gstrength,m) ;
679      024A --      WHILE pptr <> NIL DO
680      025C 2-      BEGIN
681      025C --      gstate[pptr@.gr] := -2 ;
682      0280 --      pptr := pptr@.fptr
683      028A -2      END ;
684      02A0 --      FOR r := 1 TO m DO
685      02D2 --      WHILE head[r] <> NIL DO
686      02F6 2-      BEGIN
687      02F6 --      i := head[r]@.node ;
688      0320 --      node[i].trigger := false ;
689      033E --      IF ( node[i].strength <> 3 ) THEN
690      0368 --      IF ( node[i].state <> gstate[r] ) THEN
691      03AC 3-      BEGIN
692      03AC --      node[i].newsta := gstate[r] ;
693      03E8 --      node[i].trigger := true
694      0400 -3      END
695      0408 --      ELSE
696      040C --      IF ( node[i].newsta <> gstate[r] ) THEN

```

```

697 0450 3-      BEGIN
698 0450 --      node[i].newsta := gstate[r] ;
699 048C --      node[i].trigger := true
700 04A4 -3      END ;
701 04AC --      head[r] := head[r]@.fptr
702 04DA -2      END
703 04EC -1      END
704 0512 --      ELSE
705 0516 --      WHILE head[inx] <> NIL DO
706 053A 1-      BEGIN
707 053A --      i := head[inx]@.node ;
708 0564 --      node[i].trigger := false ;
709 0582 --      IF ( node[i].strength <> 3 ) THEN
710 05AC --      IF ( node[i].state <> gstate[0] ) THEN
711 05DE 2-      BEGIN
712 05DE --      node[i].newsta := gstate[0] ;
713 0608 --      node[i].trigger := true ;
714 0620 -2      END
715 0628 --      ELSE
716 062C --      IF ( node[i].newsta <> gstate[0] ) THEN
717 065E 2-      BEGIN
718 065E --      node[i].newsta := gstate[0] ;
719 0688 --      node[i].trigger := true
720 06A0 -2      END ;
721 06A8 --      head[inx] := head[inx]@.fptr
722 06D6 -1      END
723 06E8 -0 A  END ;
724 0718 --
725 0718 -- A  PROCEDURE append ( VAR addl : hlink ;
726 0040 --      VAR list : graph ;
727 0040 --      x : integer ) ;
728 004C --
729 004C --      (* adding an activated group to the list EVL *)
730 004C --
731 004C --      VAR
732 004C --      ad : hlink ;
733 0050 --      evpen : pendlink ;
734 0054 --      found : boolean ;
735 0058 --
736 0000 0- A  BEGIN
737 0012 --      found := false ;
738 0018 --      evpen := evpend ;
739 0030 --      WHILE evpen <> NIL DO
740 0042 --      IF evpen@.group = x THEN
741 0066 1-      BEGIN
742 0066 --      found := true ;
743 006E --      evpen := NIL
744 006E -1      END
745 0074 --      ELSE
746 0078 --      evpen := evpen@.fptr ;
747 0098 --      IF found = false THEN
748 00AA 1-      BEGIN
749 00AA --      new(evpen) ;
750 00B8 --      evpen@.group := x ;
751 00D0 --      evpen@.fptr := evpend ;
752 00F2 --      evpend := evpen ;
753 010A --      ad := list[x] ;
754 0132 --      WHILE ad@.fptr <> NIL DO

```

```

755 014E --          ad := ad@.fptr ;
756 016E --          ad@.fptr := add1 ;
757 018E --          add1 := list[x] ;
758 01BA --          list[x] := NIL
759 01CC -1          END
760 01D6 -0 A      END ;
761 01E8 --
762 01E8 -- A      PROCEDURE delete ( VAR del : hlink ) ;
763 0044 --
764 0044 --      (* delete those used storage area *)
765 0044 --
766 0044 --      VAR
767 0044 --          dele : hlink ;
768 0048 --
769 0000 0- A      BEGIN
770 0012 --          WHILE del <> NIL DO
771 0028 1-          BEGIN
772 0028 --              dele := del ;
773 003E --              del := del@.fptr ;
774 0062 --              dispose(dele)
775 0072 -1          END
776 0072 -0 A      END ;
777 0084 --
778 0084 -- A      PROCEDURE searchpath ( VAR path : pathline ;
779 0040 --          VAR q : integer ;
780 0040 --          m : integer ) ;
781 004C --
782 004C --      (* search for direct paths between the input and
783 004C --          the output nodes *)
784 004C --
785 004C --      VAR
786 004C --          l : trlink ;
787 0050 --          tem,base : pathlink ;
788 0058 --          pass : boolean ;
789 005C --          i,j,k : integer ;
790 0068 --
791 0000 0- A      BEGIN
792 0012 --          node[m].visit := true ;
793 0032 --          l := node[m].icptr ;
794 005C --          IF node[m].ic >= 2 THEN
795 0086 1-          BEGIN
796 0086 --              new(tem) ;
797 0094 --              tem@ := path[q]@ ;
798 00CC --              pass := false ;
799 00D2 --              FOR i := 1 TO ( node[m].ic ) DO
800 0116 2-          BEGIN
801 0116 --              j := l@.trans ;
802 012E --              IF (trans[j].trigger = true) AND
803 0164 --              (node[trans[j].gp@.node].tiptr@.fptr@.time = ST) THEN
804 01E6 3-          BEGIN
805 01E6 --              ii := trans[j].gp@.node ;
806 0222 --              new(inp) ;
807 0236 --              inp@.node := ii ;
808 025A --              inp@.fptr := inpu ;
809 0282 --              inpu := inp
810 0282 -3          END ;
811 02A0 --              IF (trans[j].state = 2) OR (trans[j].state = 1) THEN
812 0314 3-          BEGIN

```

```

813 0314 -- IF (trans[j].dptr@.node <> m) AND
814 035C -- (node[trans[j].dptr@.node].visit = false) THEN
815 03BC 4- BEGIN
816 03BC -- IF pass = true THEN
817 03CE -- q := q + 1
818 03DC -- ELSE
819 03EC -- pass := true ;
820 03F4 -- new(path[q]) ;
821 0420 -- path[q]@ := tem@ ;
822 0458 -- k := trans[j].dptr@.node ;
823 048E -- new(base) ;
824 049C -- base@.fptr := path[q] ;
825 04D6 -- base@.node := k ;
826 04EE -- path[q] := base ;
827 051E -- searchpath(path,q,k)
828 053C -4 END
829 0540 -- ELSE
830 0544 -- IF (trans[j].sptr@.node <> m) AND
831 058C -- (node[trans[j].sptr@.node].visit = false) THEN
832 05EC 4- BEGIN
833 05EC -- IF pass = true THEN
834 05FE -- q := q + 1
835 060C -- ELSE
836 061C -- pass := true ;
837 0624 -- new(path[q]) ;
838 0650 -- path[q]@ := tem@ ;
839 0688 -- k := trans[j].sptr@.node ;
840 06BE -- new(base) ;
841 06CC -- base@.fptr := path[q] ;
842 0706 -- base@.node := k ;
843 071E -- path[q] := base ;
844 074E -- searchpath(path,q,k)
845 076C -4 END
846 0770 -3 END ;
847 0770 -- l := l@.fptr
848 077A -2 END
849 078C -1 END,
850 07AE -0 A END ;
851 07D8 --
852 07D8 -- A PROCEDURE paths ( head : hlink ) ;
853 0044 --
854 0044 -- (* searching for all the direct paths *)
855 0044 --
856 0044 -4 VAR
857 0044 -- base : pathlink ;
858 0048 -- point : hlink ;
859 004C -- l : trlink ;
860 0050 -- i,j,k : integer ;
861 005C --
862 0000 0- A BEGIN
863 0012 -- point := head ;
864 0024 -- pullup := false ;
865 0030 -- WHILE point <> NIL DO
866 0042 1- BEGIN
867 0042 -- i := point@.node ;
868 005A -- IF node[i].strength = 2 THEN
869 0084 2- BEGIN
870 0084 -- pn := i ;

```

```

871 0098 --          pullup := true ;
872 00A6 --          point := NIL
873 00A6 -2          END
874 00AC --          ELSE
875 00B0 --          point := point@.fptr
876 00BA -1          END ;
877 00D0 --          IF pullup = false THEN
878 00E8 1-          BEGIN
879 00E8 --          point := head ;
880 00FA --          WHILE point <> NIL DO
881 010C 2-          BEGIN
882 010C --          i := point@.node ;
883 0124 --          IF node[i].strength = 3 THEN
884 014E 3-          BEGIN
885 014E --          pn := i ;
886 0162 --          IF node[i].inev = true THEN
887 018C 4-          BEGIN
888 018C --          ii := i ;
889 01A0 --          new(inp) ;
890 01B4 --          inp@.node := ii ;
891 01D8 --          inp@.fptr := inpu ;
892 0200 --          inpu := inp
893 0200 -4          END ;
894 021E --          point := NIL
895 021E -3          END
896 0224 --          ELSE
897 0228 --          point := point@.fptr
898 0232 -2          END
899 0244 -1          END ;
900 0248 --          point := head ;
901 025A --          WHILE point <> NIL DO
902 026C 1-          BEGIN
903 026C --          node[point@.node].visit := false ;
904 0294 --          point := point@.fptr
905 029E -1          END ;
906 02B4 --          q := 0 ;
907 02C0 --          node[pn].visit := true ;
908 02E6 --          IF (node[pn].trigger = true) AND
909 031C --          (node[pn].nodetype = 2) THEN
910 035A 1-          BEGIN
911 035A --          q := q + 1 ;
912 0378 --          new(path[q]) ;
913 03A4 --          path[q]@.fptr := NIL ;
914 03D2 --          path[q]@.node := pn ;
915 040E --          path[q]@.no := 0
916 0436 -1          END ;
917 043C --          l := node[pn].icptr ;
918 046C --          FOR i := 1 TO node[pn].ic DO
919 04B6 1-          BEGIN
920 04B6 --          j := l@.trans ;
921 04CE --          IF (trans[j].trigger = true) AND
922 0504 --          (node[trans[j].gptr@.node].tiptr@.fptr@.time = ST) THEN
923 0586 2-          BEGIN
924 0586 --          ii := trans[j].gptr@.node ;
925 05C2 --          new(inp) ;
926 05D6 --          inp@.node := ii ;
927 05FA --          inp@.fptr := inpu ;
928 0622 --          inpu := inp

```

```

929 0622 -2      END ;
930 0640 --      IF trans[j].state <> 0 THEN
931 0670 2-      BEGIN
932 0670 --          q := q + 1 ;
933 068E --          new(path[q]) ;
934 06BA --          path[q].fptr := NIL ;
935 06E8 --          path[q].node := pn ;
936 0724 --          IF (trans[j].dptr@.node <> pn) AND
937 0772 --              (node[trans[j].dptr@.node].visit = false) THEN
938 07D2 3-      BEGIN
939 07D2 --          k := trans[j].dptr@.node ;
940 0808 --          new(base) ;
941 0816 --          base.fptr := path[q] ;
942 0850 --          base.node := k ;
943 0868 --          path[q] := base ;
944 0898 --          searchpath(path,q,k)
945 08BA -3      END
946 08BE --      ELSE
947 08C2 --          IF (trans[j].sptr@.node <> pn) AND
948 0910 --              (node[trans[j].sptr@.node].visit = false) THEN
949 0970 3-      BEGIN
950 0970 --          k := trans[j].sptr@.node ;
951 09A6 --          new(base) ;
952 09B4 --          base.fptr := path[q] ;
953 09EE --          base.node := k ;
954 0A06 --          path[q] := base ;
955 0A36 --          searchpath(path,q,k)
956 0A58 -3      END
957 0A5C -2      END ;
958 0A5C --      l := l@.fptr
959 0A66 -1      END
960 0A78 -0 A      END ;
961 0ACC --
962 0ACC -- A      PROCEDURE delays ( head : hlink ) ;
963 0044 --
964 0044 --      (* computing the delay for each output node which has
965 0044 --         changed state *)
966 0044 --
967 0044 --      VAR
968 0044 --          pi : tilink ;
969 0048 --          storage,base,pa,pp : pathlink ;
970 0058 --          first,point : hlink ;
971 0060 --          l : trlink ;
972 0064 --          i,j,k,r,di,beta,delay : integer ;
973 0080 --          totcap,tot,tstp,tsis,tin,ratio,dratio,tdel : real ;
974 00C0 --          occur : boolean ;
975 00C4 --
976 0000 0- A      BEGIN
977 0012 --          first := head ;
978 0024 --          WHILE first <> NIL DO
979 0036 1-      BEGIN
980 0036 --              IF (node[first@.node].trigger = true) AND
981 0070 --                  (node[first@.node].nodetype = 2) THEN
982 00B2 2-          begin
983 00B2 --              IF (node[first@.node].newsta = 2) THEN
984 00E6 3-          BEGIN
985 00E6 --              delay := 1 ;
986 00EE --              tm := ST + delay ;

```

```

987      0114  --      tt := 0 ;
988      0130  --      spike(first@.node,node[first@.node].newsta,tm,tt)
989      01A8  -3      END
990      01AC  --      ELSE
991      01B0  --      IF (node[first@.node].newsta = 1) THEN
992      01E4  3-      BEGIN      (* if the new state is 1 *)
993      01E4  --      paths(head) ;
994      01FA  --      r := 0 ;
995      0200  --      FOR i := 1 TO q DO
996      0232  --      IF (node[path[i]@.node].strength = 3 ) OR
997      0284  --      (( node[path[i]@.node].strength = 1 ) AND
998      02D6  --      (node[path[i]@.node].nodetype <> 2 )) THEN
999      0332  --      path[i] := NIL
1000     0344  --      ELSE
1001     0354  4-      BEGIN
1002     0354  --      r := r + 1 ;
1003     0366  --      path[r] := path[i] ;
1004     03A8  --      IF path[r]@.node = first@.node THEN
1005     03EE  --      di := r
1006     03EE  -4      END ;
1007     041E  --      FOR i := 1 TO r DO
1008     044A  4-      BEGIN
1009     044A  --      j := 0 ;
1010     0450  --      pa := path[i] ;
1011     047A  --      WHILE pa@.fptr <> NIL DO
1012     0496  5-      BEGIN
1013     0496  --      j := j + 1 ;
1014     04A8  --      pa := pa@.fptr
1015     04B2  -5      END ;
1016     04C8  --      pa := path[i] ;
1017     04F2  --      WHILE pa <> NIL DO
1018     0504  5-      BEGIN
1019     0504  --      pa@.no := j ;
1020     051C  --      j := j - 1 ;
1021     052E  --      pa := pa@.fptr
1022     0538  -5      END
1023     054A  -4      END ;
1024     0570  --      IF pullup = true THEN
1025     0588  4-      BEGIN
1026     0588  --      totcap := 0 ;
1027     059E  --      storage := NIL ;
1028     05A4  --      FOR i := 1 TO r DO
1029     05D0  5-      BEGIN
1030     05D0  --      pa := path[i] ;
1031     05FA  --      WHILE pa <> NIL DO
1032     060C  6-      BEGIN
1033     060C  --      pp := storage ;
1034     061E  --      occur := false ;
1035     0624  --      WHILE pp <> NIL DO
1036     0636  --      IF pa@.node <> pp@.node THEN
1037     0664  --      pp := pp@.fptr
1038     066E  --      ELSE
1039     0684  7-      BEGIN
1040     0684  --      occur := true ;
1041     068C  --      pp := NIL
1042     068C  -7      END ;
1043     0696  --      IF occur = false THEN
1044     06A8  7-      BEGIN

```

1045 06A8 --
 1046 06B6 --
 1047 06D8 --
 1048 06FA --
 1049 0716 --
 1050 0728 --
 1051 076E --
 1052 07A0 -7
 1053 07B4 --
 1054 07BE -6
 1055 07D0 -5
 1056 07F6 --
 1057 0854 --
 1058 0886 --
 1059 08C0 --
 1060 08F0 5-
 1061 08F0 --
 1062 08FA -5
 1063 0936 --
 1064 0966 --
 1065 09BC --
 1066 09BC --
 1067 09D4 --
 1068 09E6 --
 1069 09FA --
 1070 0A48 -4
 1071 0A4E --
 1072 0A52 4-
 1073 0A52 --
 1074 0A82 5-
 1075 0A82 --
 1076 0A8C -5
 1077 0AC8 --
 1078 0AE4 --
 1079 0AE4 -4
 1080 0AFA --
 1081 0B2E 4-
 1082 0B2E --
 1083 0B86 --
 1084 0B9E --
 1085 0C16 -4
 1086 0C1A --
 1087 0C1E 4-
 1088 0C1E --
 1089 0C34 --
 1090 0C46 --
 1091 0C70 --
 1092 0C82 5-
 1093 0C82 --
 1094 0C9E --
 1095 0CDA --
 1096 0D12 --
 1097 0D1C -5
 1098 0D32 --
 1099 0D5E --
 1100 0D70 5-
 1101 0D70 --
 1102 0D86 --

```

new(base) ;
base@.node := pa@.node ;
base@.no := pa@.no ;
base@.fptr := storage ;
storage := base ;
totcap := ( 1 / sqrt(pa@.no + 1) ) *
  node[pa@.node].capvalue + totcap
END ;
pa := pa@.fptr
END
END ;
ratio := node[pn].W / node[pn].L ;
tstp := 3.6976 * ( 1 / ( UC * VDD ) ) *
  ( 1 / ratio ) * totcap ;
pi := node[ii].tiptr ;
REPEAT
  pi := pi@.bptr
UNTIL pi@.time = ST ;
IF pi@.tsi <> 0 THEN
  tsis := ( 1 + 0.3 * (pi@.tsi / tstp) ** 1.5 ) *
    tstp
ELSE
  tsis := tstp ;
tdel := tsis / sqrt( sqrt(2.9) + 0.15 *
  sqrt(node[ii].capvalue / totcap) )
END
ELSE
BEGIN
  pi := node[ii].tiptr ;
  REPEAT
    pi := pi@.bptr
  UNTIL pi@.time = ST ;
  tsis := pi@.tsi ;
  tdel := 0
END ;
IF path[di]@.no = 0 THEN
BEGIN
  tm := ST + round(tdel * 1.0E9) ;
  tt := tsis ;
  spike(first@.node, node[first@.node].newsta, tm, tt)
END
ELSE
BEGIN
  totcap := 0 ;
  tin := tsis ;
  pa := path[di] ;
  WHILE pa <> NIL DO
  BEGIN
    IF pa@.no <> 0 THEN
      totcap := totcap + sqrt(pa@.no) *
        node[pa@.node].capvalue ;
    pa := pa@.fptr
  END ;
  FOR i := 1 TO r DO
    IF i <> di THEN
      BEGIN
        tot := 0 ;
        pa := path[i] ;

```

```

1103 ODB0 --
1104 ODC2 6-
1105 ODC2 --
1106 ODEC --
1107 ODF2 --
1108 OE04 --
1109 OE32 --
1110 OE3C --
1111 OE52 7-
1112 OE52 --
1113 OE5A --
1114 OE5A -7
1115 OE64 --
1116 OE76 7-
1117 OE76 --
1118 OEA6 --
1119 OEBA --
1120 OEC4 -7
1121 OED6 --
1122 OEDA 7-
1123 OEDA --
1124 OF16 --
1125 OF2A --
1126 OF2A -7
1127 OF30 -6
1128 OF30 -5
1129 OF56 --
1130 OF80 --
1131 OFB4 --
1132 1026 --
1133 105C --
1134 10C8 --
1135 10DC --
1136 1102 --
1137 114E --
1138 114E --
1139 1166 --
1140 1178 --
1141 118E --
1142 11E6 --
1143 11FE --
1144 1216 --
1145 127A -4
1146 127E -3
1147 127E --
1148 1282 3-
1149 1282 --
1150 1298 --
1151 129E --
1152 12B4 --
1153 12E6 4-
1154 12E6 --
1155 12FC --
1156 1348 5-
1157 1348 --
1158 1372 --
1159 1384 6-
1160 1384 --

```

```

WHILE pa <> NIL DO
  BEGIN
    pp := path[di] ;
    occur := false ;
    WHILE pp <> NIL DO
      IF pa@.node <> pp@.node THEN
        pp := pp@.fptr
      ELSE
        BEGIN
          occur := true ;
          pp := NIL
        END;
      IF occur = false THEN
        BEGIN
          tot := node[pa@.node].capvalue +
            tot ;
          pa := pa@.fptr
        END
      ELSE
        BEGIN
          totcap := sqrt(pa@.no) * tot +
            totcap ;
          pa := NIL
        END
      END
    END ;
    pa := path[di] ;
    l := node[pa@.node].icptr ;
    ratio := trans[l@.trans].W / trans[l@.trans].L ;
    tstp := 17.778 * ( 1 / ( UC * ( VDD - VTE ) ) ) *
      sqrt(path[di@.no) * ( 1 / ratio ) *
        totcap ;
    IF tin <> 0 THEN
      tsis := ( 1 + 0.3 * ( tin / tstp ) ** 1.5 ) *
        tstp
    ELSE
      tsis := tstp ;
      tdel := tsis / 8.9 ;
      tm := ST + round(tdel * 1.0E9) ;
      tt := tsis ;
      i := first@.node ;
      spike(i,node[i].newsta,tm,tt)
    END
  END
ELSE
  BEGIN (* if the new state is 0 *)
    paths(head) ;
    r := 0 ;
    dratio := 0 ;
    FOR i := 1 TO q DO
      BEGIN
        ratio := 0 ;
        IF (node[path[i]@.node].strength = 3) THEN
          BEGIN
            pa := path[i] ;
            WHILE pa <> NIL DO
              BEGIN
                IF pa@.node <> pn THEN

```

```

1161 13AE 7-
1162 13AE --
1163 13E2 --
1164 13F4 8-
1165 13F4 --
1166 1426 --
1167 145A --
1168 148C --
1169 14C8 --
1170 14FE --
1171 1536 --
1172 154A --
1173 1554 -8
1174 1566 -7
1175 156A --
1176 1574 -6
1177 158A --
1178 15C2 --
1179 15D4 -5
1180 15E0 --
1181 15E4 5-
1182 15E4 --
1183 1636 --
1184 1690 --
1185 16A2 --
1186 16B2 6-
1187 16B2 --
1188 16C4 --
1189 1706 --
1190 174C --
1191 174C -6
1192 175A -5
1193 175A -4
1194 177C --
1195 17A8 4-
1196 17A8 --
1197 17AE --
1198 17D8 --
1199 17F4 5-
1200 17F4 --
1201 1806 --
1202 1810 -5
1203 1826 --
1204 1850 --
1205 1862 5-
1206 1862 --
1207 187A --
1208 188C --
1209 1896 -5
1210 18A8 -4
1211 18CE --
1212 18E6 4-
1213 18E6 --
1214 18FC --
1215 1902 --
1216 192E 5-
1217 192E --
1218 1958 --

BEGIN
  l := node[pa@.node].icptr ;
  WHILE l <> NIL DO
    BEGIN
      IF (trans[l@.trans].dptr@.node
        = pa@.fptr@.node) OR
        (trans[l@.trans].sptr@.node
        = pa@.fptr@.node) THEN
        ratio := ( trans[l@.trans].L /
                    trans[l@.trans].W )
                + ratio ;
        l := l@.fptr
      END
    END ;
    pa := pa@.fptr
  END ;
  dratio := ( dratio + ( 1 / ratio ) ) ;
  path[i] := NIL
END
ELSE
  begin
    IF (node[path[i]@.node].strength = 1) AND
      (node[path[i]@.node].nodetype <> 2) THEN
      path[i] := NIL
    ELSE
      BEGIN
        r := r + 1 ;
        path[r] := path[i] ;
        IF path[r]@.node = first@.node THEN
          di := r
        END
      end
    END ;
    FOR i := 1 TO r DO
      BEGIN
        j := 0 ;
        pa := path[i] ;
        WHILE pa@.fptr <> NIL DO
          BEGIN
            j := j + 1 ;
            pa := pa@.fptr
          END ;
          pa := path[i] ;
          WHILE pa <> NIL DO
            BEGIN
              pa@.no := j ;
              j := j - 1 ;
              pa := pa@.fptr
            END
          END ;
        END ;
        If pullup = true THEN
          BEGIN
            totcap := 0 ;
            storage := NIL ;
            FOR i := 1 TO r DO
              BEGIN
                pa := path[i] ;
                WHILE pa <> NIL DO

```

1219 196A 6-
 1220 196A --
 1221 197C --
 1222 1982 --
 1223 1994 --
 1224 19C2 --
 1225 19CC --
 1226 19E2 7-
 1227 19E2 --
 1228 19EA --
 1229 19EA -7
 1230 19F4 --
 1231 1A06 7-
 1232 1A06 --
 1233 1A14 --
 1234 1A36 --
 1235 1A58 --
 1236 1A74 --
 1237 1A86 --
 1238 1ACC --
 1239 1AFE --
 1240 1AFE -7
 1241 1B12 --
 1242 1B1C -6
 1243 1B2E -5
 1244 1B54 --
 1245 1BB2 --
 1246 1BFE --
 1247 1C36 --
 1248 1C68 --
 1249 1C8E --
 1250 1CA6 --
 1251 1CDE --
 1252 1D10 --
 1253 1D36 --
 1254 1D4E --
 1255 1D96 --
 1256 1DC6 5-
 1257 1DC6 --
 1258 1DD0 -5
 1259 1E0C --
 1260 1E3C --
 1261 1E92 --
 1262 1E92 --
 1263 1EAA --
 1264 1EBC --
 1265 1ED0 --
 1266 1F1E -4
 1267 1F24 --
 1268 1F28 4-
 1269 1F28 --
 1270 1F58 5-
 1271 1F58 --
 1272 1F62 -5
 1273 1F9E --
 1274 1FBA --
 1275 1FBA -4
 1276 1FD0 --

```

BEGIN
  pp := storage ;
  occur := false ;
  WHILE pp <> NIL DO
    IF pa@.node <> pp@.node THEN
      pp := pp@.fptr
    ELSE
      BEGIN
        occur := true ;
        pp := NIL
      END;
    IF occur = false THEN
      BEGIN
        new(base) ;
        base@.node := pa@.node ;
        base@.no := pa@.no ;
        base@.fptr := storage ;
        storage := base ;
        totcap := ( 1 / sqrt(pa@.no + 1) ) *
          node[pa@.node].capvalue +
          totcap
      END ;
      pa := pa@.fptr
    END
  END ;
  ratio := node[pn].W / node[pn].L ;
  beta := round(dratio / ratio) ;
  IF ( ( beta >= 2 ) AND ( beta < 6 ) ) THEN
    tstp := 4.0624 * ( 1 / ( UC * VDD ) ) *
      ( 1 / dratio ) * totcap
  ELSE
    IF ( ( beta >= 6 ) AND ( beta < 10 ) ) THEN
      tstp := 3.8758 * ( 1 / ( UC * VDD ) ) *
        ( 1 / dratio ) * totcap
    ELSE
      writeln(' beta = ', beta, ' error ' ) ;
      pi := node[ii].tiptr ;
      REPEAT
        pi := pi@.bptr
      UNTIL pi@.time = ST ;
      IF pi@.tsi <> 0 THEN
        tsis := ( 1 + 0.25 * (pi@.tsi / tstp) ** 1.1 )
          * tstp
      ELSE
        tsis := tstp ;
        tdel := tsis / sqrt( sqr(1.9) + 0.06 *
          sqr(node[ii].capvalue / totcap) )
      END
    ELSE
      BEGIN
        pi := node[ii].tiptr ;
        REPEAT
          pi := pi@.bptr
        UNTIL pi@.time = ST ;
        tsis := pi@.tsi ;
        tdel := 0
      END ;
      IF path[di]@.no = 0 THEN

```

```

1277 2004 4- BEGIN
1278 2004 -- tm := ST + round(tdel * 1.0E9) ;
1279 205C -- tt := tsis ;
1280 2074 -- spike(first@.node,node[first@.node].newsta,tm,tt)
1281 20EC -4 END
1282 20F0 -- ELSE
1283 20F4 4- BEGIN
1284 20F4 -- totcap := 0 ;
1285 210A -- tin := tsis ;
1286 211C -- pa := path[di] ;
1287 2146 -- WHILE pa <> NIL DO
1288 2158 5- BEGIN
1289 2158 -- IF pa@.no <> 0 THEN
1290 2174 -- totcap := totcap + sqrt(pa@.no) *
1291 21B0 -- node[pa@.node].capvalue ;
1292 21E8 -- pa := pa@.fptr
1293 21F2 -5 END ;
1294 2208 -- FOR i := 1 TO r DO
1295 2234 -- IF i <> di THEN
1296 2246 5- BEGIN
1297 2246 -- tot := 0 ;
1298 225C -- pa := path[i] ;
1299 2286 -- WHILE pa <> NIL DO
1300 2298 6- BEGIN
1301 2298 -- pp := path[di] ;
1302 22C2 -- occur := false ;
1303 22C8 -- WHILE pp <> NIL DO
1304 22DA -- IF pa@.node <> pp@.node THEN
1305 2308 -- pp := pp@.fptr
1306 2312 -- ELSE
1307 2328 7- BEGIN
1308 2328 -- occur := true ;
1309 2330 -- pp := NIL
1310 2330 -7 END ;
1311 233A -- IF occur = false THEN
1312 234C 7- BEGIN
1313 234C -- tot := node[pa@.node].capvalue +
1314 237C -- tot ;
1315 2390 -- pa := pa@.fptr
1316 239A -7 END
1317 23AC -- ELSE
1318 23B0 7- BEGIN
1319 23B0 -- totcap := sqrt(pa@.no) * tot +
1320 23EC -- totcap ;
1321 2400 -- pa := NIL
1322 2400 -7 END
1323 2406 -6 END
1324 2406 -5 END ;
1325 242C -- pa := path[di] ;
1326 2456 -- l := node[pa@.node].icptr ;
1327 248A -- ratio := trans[l@.trans].W / trans[l@.trans].L ;
1328 24FC -- tstp := 2.7436 * ( 1/( UC * ( VDD - VTE ) ) ) *
1329 2532 -- sqrt(path[di]@.no) * ( 1 / ratio ) *
1330 259E -- totcap ;
1331 25B2 -- IF tin <> 0 THEN
1332 25D8 -- tsis := ( 1 + ( tin / tstp ) ** 0.7 ) *
1333 2620 -- tstp
1334 2620 -- ELSE

```

```

1335 263C --      tsis := tstp ;
1336 264E --      tdel := tsis / 2.5 ;
1337 2664 --      tm := ST + round(tdel * 1.0E9) ;
1338 26BC --      tt := tsis ;
1339 26D4 --      i := first@.node ;
1340 26EC --      spike(i,node[i].newsta,tm,tt)
1341 2750 -4      END
1342 2754 -3      END
1343 2754 -2      end ;
1344 2754 --      first := first@.fptr
1345 275E -1      END
1346 2770 -0 A    END ;
1347 286C --
1348 286C --
1349 286C --
1350 286C -- A    PROCEDURE simulate ;
1351 0040 --      (* perform the simulation process *)
1352 0040 --
1353 0040 --
1354 0040 --      VAR
1355 0040 --          TQempty,stop,optev,share : boolean ;
1356 0050 --          i,k,delay : integer ;
1357 005C --
1358 0000 0- A    BEGIN
1359 0012 1-        REPEAT
1360 0012 --          evpend := NIL ;
1361 001E --          EVL := NIL ;
1362 002A --          ST := 2 * MTC + t - 1 ;
1363 0064 --          IF TQ[t] <> NIL THEN
1364 0094 2-            BEGIN
1365 0094 --              WHILE TQ[t] <> NIL DO
1366 00C4 3-                BEGIN
1367 00C4 --                  i := TQ[t]@.node ;
1368 00FA --                  IF ( node[i].state <> TQ[t]@.newsta ) THEN
1369 0154 4-                    BEGIN
1370 0154 --                      node[i].state := TQ[t]@.newsta ;
1371 01A6 --                      IF ( node[i].strength = 3 ) AND ( node[i].ic > 0 )
1372 0206 --                      THEN,
1373 020E 5-                        BEGIN
1374 020E --                          node[i].inev := true ;
1375 022E --                          j := node[i].group ;
1376 025A --                          append(EVL,subnet,j)
1377 0282 -5                        END ;
1378 0286 --                      fp := node[i].fcptr ;
1379 02B6 --                      WHILE fp <> NIL DO
1380 02CE 5-                        BEGIN
1381 02CE --                          IF ( trans[fp@.trans].transtype = 1 ) THEN
1382 030E 6-                            BEGIN
1383 030E --                              trans[fp@.trans].trigger := true ;
1384 0344 --                              trans[fp@.trans].state := node[i].state
1385 0384 -6                            END
1386 039C --                          ELSE
1387 03A0 --                              IF ( trans[fp@.trans].transtype = 2 ) THEN
1388 03E0 6-                                BEGIN
1389 03E0 --                                  trans[fp@.trans].trigger := true ;
1390 0416 --                                  IF ( node[i].state = 0 ) THEN
1391 0440 --                                      trans[fp@.trans].state := 1
1392 0468 --                                  ELSE

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1393 047A -- IF ( node[i].state = 1 ) THEN
1394 04A4 --   trans[fp@.trans].state := 0
1395 04CC -- ELSE
1396 04DC --   trans[fp@.trans].state := 2
1397 0504 -6   END
1398 0512 --   ELSE
1399 0516 6-     BEGIN
1400 0516 --       trans[fp@.trans].trigger := true ;
1401 054C --       trans[fp@.trans].state := 1
1402 0574 -6     END ;
1403 0582 --   v := trans[fp@.trans].dptr@.node ;
1404 05CE --   w := trans[fp@.trans].sptr@.node ;
1405 061A --   IF ( node[v].group = node[w].group ) THEN
1406 0670 --     append(EVL,subnet,node[v].group)
1407 06B0 --   ELSE
1408 06B8 6-     BEGIN
1409 06B8 --       append(EVL,subnet,node[v].group) ;
1410 06FC --       append(EVL,subnet,node[w].group)
1411 073C -6     END ;
1412 0740 --   fp := fp@.fptr
1413 0750 -5   END
1414 0768 -4   END ;
1415 076C --   TQ[t] := TQ[t]@.fptr
1416 07AC -3   END ;
1417 07C8 --   sub[0] := EVL ;
1418 07E6 --   partition(sub,0,1,1,2) ;
1419 0812 --   delete(sub[0]) ;
1420 0820 --   inpu := NIL ;
1421 082C --   FOR k := 1 to m DO
1422 085E 3-     BEGIN
1423 085E --       n := n + 1 ;
1424 087C --       subnet[n] := sub[k] ;
1425 08C4 --       point := subnet[n] ;
1426 08FA --       WHILE point <> NIL DO
1427 0912 4-         BEGIN
1428 0912 --           i := point@.node ;
1429 0930 --           node[i].group := n ;
1430 095C --           point := point@.fptr
1431 096C -4         END ;
1432 0988 --       nodestate(subnet,n) ;
1433 09B4 --       point := subnet[n] ;
1434 09EA --       outev := false ;
1435 09F0 --       WHILE point <> NIL DO
1436 0A08 4-         BEGIN
1437 0A08 --           i := point@.node ;
1438 0A26 --           IF ( node[i].trigger = true ) THEN
1439 0A50 --             IF ( node[i].nodetype = 1 ) THEN
1440 0A7A --               node[i].state := node[i].newsta
1441 0AAA --             ELSE
1442 0AC0 --               IF unit = true THEN
1443 0AD8 5-                 BEGIN
1444 0AD8 --                   delay := 1 ;
1445 0AE0 --                   tm := ST + delay ;
1446 0B06 --                   tt := 0 ;
1447 0B22 --                   appendev(i,node[i].newsta,tm,tt).
1448 0B86 -5                 END
1449 0B8A --               ELSE
1450 0B8E --                 outev := true ;

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1451      0B96 --      point := point@.fptr
1452      0BA6 -4      END ;
1453      0BC2 --      share := true ;
1454      0BCA --      IF ( outev = true ) THEN
1455      0BDC 4-      BEGIN
1456      0BDC --      point := subnet[n] ;
1457      0C12 --      WHILE point <> NIL DO
1458      0C2A 5-      BEGIN
1459      0C2A --      IF (node[point@.node].strenght = 2) OR
1460      0C6A --      (node[point@.node].strenght = 3) THEN
1461      0CB2 6-      BEGIN
1462      0CB2 --      share := false ;
1463      0CB8 --      point := NIL
1464      0CB8 -6      END
1465      0CC4 --      ELSE
1466      0CC8 --      point := point@.fptr
1467      0CD8 -5      END ;
1468      0CF4 --      IF share = true THEN
1469      0D06 5-      BEGIN
1470      0D06 --      point := subnet[n] ;
1471      0D3C --      WHILE point <> NIL DO
1472      0D54 6-      BEGIN
1473      0D54 --      IF node[point@.node].nodetype = 2 THEN
1474      0D8E 7-      BEGIN
1475      0D8E --      i := point@.node ;
1476      0DAC --      tm := ST + 1 ;
1477      0DCA --      spike(i,node[i].newsta,tm,0)
1478      0E2C -7      END ;
1479      0E30 --      point := point@.fptr
1480      0E40 -6      END
1481      0E58 -5      END
1482      0E5C --      ELSE
1483      0E60 --      delays(subnet[n])
1484      0E90 -4      END
1485      0E94 -3      END ;
1486      0EB6 --      WHILE inpu <> NIL DO
1487      0ECE 3-      BEGIN
1488      0ECE --      i := inpu@.node ;
1489      0EEC --      IF node[i].inev = true THEN
1490      0F16 --      node[i].inev := false ;
1491      0F34 --      pi := node[i].tiptr@.fptr ;
1492      0F6E --      IF pi@.time = ST THEN
1493      0F9E 4-      BEGIN
1494      0F9E --      node[i].tiptr@.fptr := pi@.fptr ;
1495      0FE2 --      pi@.fptr@.bptr := node[i].tiptr
1496      1014 -4      END ;
1497      1026 --      inpu := inpu@.fptr
1498      1036 -3      END ;
1499      1052 --      FOR k := 1 TO m DO
1500      1084 3-      BEGIN
1501      1084 --      point := sub[k] ;
1502      10B4 --      WHILE point <> NIL DO
1503      10CC 4-      BEGIN
1504      10CC --      l := node[point@.node].icptr ;
1505      110C --      WHILE l <> NIL DO
1506      1124 5-      BEGIN
1507      1124 --      IF trans[l@.trans].trigger = true THEN
1508      1164 --      trans[l@.trans].trigger := false ;

```

```

1509 1198 --          1 := 1@.fptr
1510 11A8 -5          END ;
1511 11C4 --          point := point@.fptr
1512 11D4 -4          END
1513 11EC -3          END
1514 11F0 -2          END ;
1515 1212 -- IF unit = false THEN
1516 122A 2-          BEGIN
1517 122A --          write(' time ',ST,' node 1 ',node[1].state) ;
1518 128A --          writeln(' node 5 ',node[5].state,' node 6 ',node[6].state)
1519 12E4 -2          END ;
1520 12EA --          t := t + 1 ;
1521 1308 --          IF t = Z + 1 THEN
1522 1326 2-          BEGIN
1523 1326 --          FOR i := 1 TO Z DO
1524 1344 3-          BEGIN
1525 1344 --          TQ[i] := TQ[Z+i] ;
1526 138A --          TQ[Z+i] := NIL
1527 13A0 -3          END ;
1528 13CE --          MTC := MTC + 1 ;
1529 13EC --          t := 1 ;
1530 13FA --          WHILE ( MTEL@.fptr@.time <= ( Z * MTC + Z2 - 1 ) ) AND
1531 144C --          ( MTEL <> MTEL@.fptr ) DO
1532 148A 3-          BEGIN
1533 148A --          j := MTEL@.fptr@.time - ( Z * MTC - 1 ) ;
1534 14D8 --          new(event) ;
1535 14EC --          WITH event@ DO
1536 14FE 4-          BEGIN
1537 14FE --          fptr := TQ[j] ;
1538 152E --          node := MTEL@.fptr@.node ;
1539 1556 --          newsta := MTEL@.fptr@.newsta ;
1540 1582 --          time := MTEL@.fptr@.time ;
1541 15AA --          .tt := MTEL@.fptr@.tt
1542 15C4 -4          END ;
1543 15D6 --          TQ[j] := event ;
1544 160C --          ev := MTEL@.fptr ;
1545 1634 --          MTEL@.fptr := ev@.fptr ;
1546 1666 --          ev@.fptr@.bptr := MTEL
1547 1680 -3          END
1548 1698 -2          END ;
1549 169C --          i := 1 ;
1550 16A4 --          TQempty := true ;
1551 16AC --          WHILE i <= Z2 DO
1552 16BE --          IF TQ(.i.) = NIL THEN
1553 16E8 --          i := i + 1
1554 16F2 --          ELSE
1555 16FE 2-          BEGIN
1556 16FE --          i := Z2 + 1 ;
1557 170A --          TQempty := false
1558 170A -2          END ;
1559 1714 --          IF ( TQempty = true ) AND ( MTEL = MTEL@.fptr ) THEN
1560 176A --          stop := true
1561 176A --          ELSE
1562 1776 --          stop := false
1563 1776 -1          UNTIL stop = true
1564 1786 -0 A          END ;
1565 17FC --
1566 17FC --

```

```

1567 17FC -- (* start of the main program *)
1568 17FC --
1569 0000 0- BEGIN
1570 0066 -- n := 0 ;
1571 0072 -- MTC := 0 ;
1572 007E -- t := 1 ;
1573 008C -- new(MTEL) ; (* create an empty overflow event list *)
1574 00A0 -- WITH MTEL@ DO
1575 00B2 1- BEGIN
1576 00B2 -- fptr := MTEL ;
1577 00CA -- bptr := MTEL ;
1578 00E2 -- node := 0 ;
1579 00E8 -- newsta := 0 ;
1580 00EE -- time := 0 ;
1581 00F4 -1 END ;
1582 00F4 -- FOR i := 1 TO Z2 DO (* create an empty TQ array *)
1583 011E -- TQ[i] := NIL ;
1584 0176 -- readparameter ;
1585 017A -- sub[0] := network[0] ;
1586 0198 -- partition(sub,0,1,1,2) ;
1587 01C4 -- delete(sub[0]) ;
1588 01D2 -- FOR i := 1 TO m DO
1589 021C 1- BEGIN
1590 021C -- n := n + 1 ;
1591 023A -- subnet[n] := sub[i] ;
1592 0288 -- point := subnet[n] ;
1593 02BE -- WHILE point <> NIL DO
1594 02D6 2- BEGIN
1595 02D6 -- j := point@.node ;
1596 02FA -- node[j].group := n ;
1597 032C -- point := point@.fptr
1598 033C -2 END
1599 0354 -1 END ;
1600 0392 -- unit := true ;
1601 03A0 -- simulate ;
1602 03A4 -- read(evnum) ;
1603 03BC -- FOR j := 1 TO evnum DO
1604 0406 1- BEGIN
1605 0406 -- read(i,sta,tm,tt) ;
1606 045A -- new(tm) ;
1607 046E -- WITH tm@ DO
1608 0480 2- BEGIN
1609 0480 -- time := tm ;
1610 0494 -- newstate := sta ;
1611 04AC -- tsi := tt
1612 04AC -2 END ;
1613 04C4 -- pi := node[i].tptr ;
1614 04FA 2- REPEAT
1615 04FA -- pi := pi@.bptr
1616 050A -2 UNTIL tm@.time >= pi@.time ;
1617 055C -- tm@.fptr := pi@.fptr ;
1618 058E -- tm@.bptr := pi ;
1619 05B6 -- pi@.fptr@.bptr := tm ;
1620 05E8 -- pi@.fptr := tm ;
1621 0610 -- appendev(i,sta,tm,tt)
1622 0668 -1 END ;
1623 06A6 -- MTC := 0 ;
1624 06B2 -- t := 1 ;

```

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AAEC (17FEB82)

```
1625 06C0 --      unit := false ;  
1626 06CC --      simulate  
1627 06CC -0      END. (* end of main program *)
```

AAEC PASCAL 2.0B COMPILATION CONCLUDED

NO ERRORS DETECTED IN PASCAL PROGRAM